502885692 07/10/2014

PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1 Stylesheet Version v1.2 EPAS ID: PAT2932289

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

CONVEYING PARTY DATA

Name	Execution Date
NUMONYX B.V.	05/23/2012

RECEIVING PARTY DATA

Name:	Micron Technology, Inc.
Street Address:	8000 So. Federal Way
City:	Boise
State/Country:	IDAHO
Postal Code:	83716-9632

PROPERTY NUMBERS Total: 1

Property Type	Number
Application Number:	14034275

CORRESPONDENCE DATA

Fax Number: (605)791-1857

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent

using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.

Phone: 6054154394 Email: llee@slwip-rc.com

Correspondent Name: SCHWEGMAN, LUNDBERG & WOESSNER, P.A.

Address Line 1: P.O. BOX 2938

Address Line 4: MINNEAPOLIS, MINNESOTA 55402

ATTORNEY DOCKET NUMBER:	303.C60US2
NAME OF SUBMITTER:	LISA M. LEE
SIGNATURE:	/Lisa M. Lee/
DATE SIGNED:	07/10/2014

Total Attachments: 50

source=303C60US2_Assignment#page1.tif source=303C60US2_Assignment#page2.tif source=303C60US2_Assignment#page3.tif source=303C60US2_Assignment#page4.tif source=303C60US2_Assignment#page5.tif

source=303C60US2_Assignment#page6.tif source=303C60US2_Assignment#page7.tif

source=303C60US2_Assignment#page8.tif	
source=303C60US2_Assignment#page9.tif	
source=303C60US2_Assignment#page10.tif	
source=303C60US2_Assignment#page11.tif	
source=303C60US2_Assignment#page12.tif	
source=303C60US2_Assignment#page13.tif	
source=303C60US2_Assignment#page14.tif	
source=303C60US2_Assignment#page15.tif	
source=303C60US2_Assignment#page16.tif	
source=303C60US2_Assignment#page17.tif	
source=303C60US2_Assignment#page18.tif	
source=303C60US2_Assignment#page19.tif	
source=303C60US2_Assignment#page20.tif	
source=303C60US2_Assignment#page21.tif	
source=303C60US2_Assignment#page22.tif	
source=303C60US2_Assignment#page23.tif	
source=303C60US2_Assignment#page24.tif	
source=303C60US2_Assignment#page25.tif	
source=303C60US2_Assignment#page26.tif	
source=303C60US2_Assignment#page27.tif	
source=303C60US2_Assignment#page28.tif	
source=303C60US2_Assignment#page29.tif	
source=303C60US2_Assignment#page30.tif	
source=303C60US2_Assignment#page31.tif	
source=303C60US2_Assignment#page32.tif	
source=303C60US2_Assignment#page33.tif	
source=303C60US2_Assignment#page34.tif	
source=303C60US2_Assignment#page35.tif	
source=303C60US2_Assignment#page36.tif	
source=303C60US2_Assignment#page37.tif	
source=303C60US2_Assignment#page38.tif	
source=303C60US2_Assignment#page39.tif	
source=303C60US2_Assignment#page40.tif	
source=303C60US2_Assignment#page41.tif	
source=303C60US2_Assignment#page42.tif	
source=303C60US2_Assignment#page43.tif	
source=303C60US2_Assignment#page44.tif	
source=303C60US2_Assignment#page45.tif	
source=303C60US2_Assignment#page46.tif	
source=303C60US2_Assignment#page47.tif	
source=303C60US2_Assignment#page48.tif	
source=303C60US2_Assignment#page49.tif	
source=303C60US2_Assignment#page50.tif	

PATENT ASSIGNMENT AGREEMENT

WHEREAS, Numonyx B.V., a company organized under the laws of Netherlands, having a place of business at A-ONE Biz Center, Z.A. Vers la Piece, Rte. De l'Etraz, 1180 Rolle, Switzerland (hereinafter referred to as "Assignor") has rights in and to the following:

- 1. U.S. Letters Patents Listed on Exhibit A,
- 2. U.S. Patent Applications listed on Exhibit B,
- 3. Foreign patents and patent applications listed on Exhibit C.

(said patents and patent applications listed in Exhibits A, B, and C being hereinafter referred to as "SAID PATENT RIGHTS"); and

WHEREAS, Micron Technology, Inc. is a corporation having a principal place of business at 8000 S. Federal Way, Boise, Idaho 83707, United States (hereinafter referred to as "Assignee") is desirous of obtaining rights to SAID PATENT RIGHTS;

NOW, THERFORE, for and in consideration of good and valuable consideration the receipt, sufficiency and adequacy of which are hereby acknowledged, Assignor does hereby sell, convey, transfer and assign to Assignee, its successors, assigns and legal representatives, subject to prior encumbrances, all right, title and interest in and to SAID PATENT RIGHTS, together with any and all continuations, continuation-in-part, continuing prosecution applications, requests for continuing examinations, divisions, reissues, reexaminations, extensions, registrations, and foreign counterparts of any item in any of the foregoing, together with the right to sue for and be entitled to any damages, injunctive relief, and any other remedies of any kind for past, current and future infringement thereof.

Numon By:	iyx B.V	· L	Si	- J cu	_
Printed	Name:	Thoma	SL.	Laws	Jr.
Title:	NIC	ecolor			

Micron Technology, Inc.

By: fodewell Jewn

Printed Name: Roden's W. Lour's

Title: V.P. of Lague Affairs

STMicroelectronics originated

		72
	•	0
ĺ		7
ı		Þ
		٠,
Į		Ç
ı		Ū
		š
		든
		H
		3
		필
		ö
		Ξ
		G

NITE SANS			Exhibit A - US Issued Patents		Chillen		Paramy.	Compte
NMXS-0001.00/RE	Utility - REIS Expired	Expired	METHOD TO INSTALL AN ELECTRONIC COMPONENT AND FIS ELECTRICAL CONNECTIONS ON A SUPPORT, AND PRODUCT OBTAINED THEREBY	12/12/1988	08/198,208	3/20/1990		US
SN/00°1000-5XWN	Utility - ORG	Expired	METHOD TO INSTAIL AN ELECTRONIC COMPONENT AND ITS ELECTRICAL CONNECTIONS ON A SUPPORT, AND PRODUCT OBTAINEDTHEREBY	12/12/1988	07/283,214	3/20/1990	4,908,937	US
NMXS-0002.00/US	Utility - ORG	Abandoned	METHOD FOR FIXING AN ELECTRONIC COMPONENT AND ITS CONTACTS TO A SUPPORT	12/12/1988	07/283,305	7/17/1990	4,941,257	US
NMXS-0002.01/RE	Utility - REIS	Expired	METHOD FOR FIXING AN ELECTRONIC COMPONENT AND ITS CONTACTS TO A SUPPORT	11/9/1994	08/336,560	7/17/1990	RE35,385	US
NMXS-0003.00/US	Utility - ORG	Abandoned	ELECTRICALLY PROGRAMMABLE MEMORY WITH SEVERAL INFORMATION BITS PER	4/24/1989	07/342,476	10/16/1990	4,964,079	S.
NMXS-0004.00/US	Utility - ORG	Issued	INTEGRATED CIRCUIT MEMORY DEVICE WITH BALANCING CIRCUIT INCLUDING FOLLOWER AMPLIFIER COUPLED TO BIT LINE	7/23/1993	08/096,684	12/3/1996	5,581,511	LS.
NMXS-0004.01/US	Utility - CON	Issued	INTEGRATED CIRCUIT MEMORY DEVICE WITH BALANCING CIRCUIT INCLUDING FOLLOWER AMPLIFIER COUPLED TO BIT LINE	6/7/1995	08/486,363	6/10/1997	5,638,332	US
NMXS-0004.02/US	Utility - DIV	Issued	INTEGRATED CIRCUIT MEMORY DEVICE WITH BALANCING CIRCUIT INCLUDING FOLLOWER AMPLIFIER COUPLED TO BIT LINE	6/7/1995	08/478,463	8/6/1996	5,544,114	us
NMXS-0005.00/US	Utility - ORG	Issued	DEVICE FOR THE PROTECTION OF AN INTEGRATED CIRCUIT AGAINST POWER SUPPLY CUTS	8/2/1993	08/100,867	12/5/1995	5,473,496	Sn
NMXS-0006.00/US	Utility - ORG	Issued	VOLTAGE BOOSTER CIRCUIT OF THE CHARGE-PUMP TYPE WITH BOOTSTRAPPED OSCILLATOR	9/29/1993	08/128,871	12/31/1996	5,589,793	SU
Sn/10'9000-5xwn	Utility - DIV	Issued	VOLTAGE BOOSTER CIRCUIT OF THE CHARGE-PUMP TYPE WITH A BOOTSTRAPPED OSCILLATOR	6/6/1995	08/467,297	1/7/1997	5,592,115	Sn
NMXS-0007.01/US	Utility - CON	Issued	POWER-ON-RESET CIRCUIT PROVIDING PROTECTION AGAINST POWER SUPPLY INTERRUPTIONS	8/8/1997	08/908,583	9/12/2000	6,118,315	SJ
SD/00'8000-SXWN	Utility - ORG	Expired	SAFETY DEVICE FOR ELECTRICALLY PROGRAMIMABLE READ-ONLY MEMORY	5/21/1987	07/052,068	3/7/1989	4,811,291	S
Sn/00'6000-5xwn	Utility - ORG	Expired	NON-VOLATILE SHADOW STORAGE CELL WITH REDUCED TUNNEL DEVICE COUNT FOR IMPROVED RELIABILITY	8/3/1987	07/081,032	1/31/1989	4,802,124	ıs
Sn/0010100-SXIMN	Utility - ORG	Expîred	NON-VOLATILE SHADOW STORAGE CELL WITH IMPROVED LEVEL SHIFTING CIRCUIT AND REDUCED TUNNEL DEVICE COUNT FOR IMPROVED RELIABILITY	8/3/1987	07/081,037	11/22/1988	4,787,066	US
NMXS-0011.03/US	Utility - CON	issued	CONTENT ADDRESSABLE MEMORY	6/7/1995	08/478,429	4/16/2002	6,373,737	æ
NMXS-0012.00/US	Utility - ORG	Expired	REDUNDANCY FOR SERIAL MEMORY	1/12/1990	07/464,219	4/2/1991	5,005,158	SN
NMXS-0013.00/US	Utility - RES	Abandoned	POLYCRYSTALLING SILICON CONTACT STRUCTURE	9/29/1994	08/316,035	9/29/1992	RE37,769	<u> </u>
NMXS-0013.01/US	Utility - DIV	Expired	POLYCRYSTALLINE SIJICON CONTACT STRUCTURE	2/28/1992	07/843,818	1/18/1994	5,279,887	S
NMXS-0014.00/US	Utility - CIP	Expired	DIFFERENCE COMPARISON BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	12/21/1989	07/454,408	6/9/1992	5,121,346	CS
NMXS-0014.03/US	Utility - CON	Issued	DIFFERENCE COMPARISON BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	4/1/1994	08/221,986	3/26/1996	5,502,655	US.
NMXS-0015.00/US	utility - ORG	Expired	PIPELINED CIRCUITRY FOR ALLOWING THE COMPARISON OF THE RELATIVE DIFFERENCE BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	10/18/1990	07/600,201	4/27/1993	5,206,817	S
NMXS-0016.00/US	Utility - ORG	Expired	TEST CIRCUIT FOR NON-VOLATILE STORAGE CELL	9/29/1989	07/414,775	7/9/1991	5,031,152	US
NIMXS-0017.00/US	Utility - ORG	Expired	SEMICONDUCTOR MEMORY WITH A CLOCKED ACCESS CODE FOR TEST MODE ENTRY	8/17/1990	07/569,009	12/10/1991	5,072,137	SN
NMXS-0018.00/US	Utility - ORG	Expired	DUAL STATE MEMORY STORAGE CELL WITH IMPROVED DATA TRANSFER CIRCUITRY	2/26/1991	07/661,555	10/1/1991	5,053,996	Sn
NMXS-0019.00/US	Utility - ORG	Expired	SEMICONDUCTOR MEMORY WITH IMPROVED TEST MODE	7/13/1990	07/552,567	11/23/1993	5,265,100	US
NMXS-0019.01/US	Utility - DIV	Expired	SEMICONDUCTOR MEMORY WITH IMPROVED TEST MODE	6/2/1993	08/071,448	5/10/1994	5,311,473	SU
NMXS-0020.00/US	Utility - ORG	Expired	SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY	8/17/1990	07/568,968	11/3/1992	5,161,159	ıs

ı	Q.
ı	ਜ
ı	➣
ı	4
ı	C
ı	S
ı	ussi
ш	
	찚
ı	=
ı	7,
ŀ	=
ŀ	亞
	#
	ᅜ

L	SS	5,357,236	10/18/1994	616,068/70	2/29/1992	יייייייייייייייייייייייייייייייייייייי			
	Γ	5,386,377	1/31/1995	08/122,804	9/16/1993	PARALIELIZED DURKOW EUON AFIEAD SUBIKACIUK	lesued	Utility - ORG	NMXS-0052.00/US
L	8	740,041	4554116	100,010,00	TOTAL BOOK	HXED VALUE	Freed	THIETH COM	NMXS-0051 01/11S
\perp		5 210 247	6/7/1004	07/876 851	4/30/1997	PARALLELIZED MAGNITUDE COMPARATOR FOR COMPARING A BINARY NUMBER TO A	Issued	Utility - ORG	NMXS-0050.00/US
\perp		5,357,235	10/18/1994	07/876,959	4/30/1992	PARALLELIZED MAGNITUDE COMPARATOR	Issued	Utility - ORG	NMXS-0049.00/US
	T	5,311,467	5/10/1994	07/854,481	4/7/1992	SELECTIVE BULK WRITE OPERATION	Issued	Utility - ORG	NMXS-0048.00/US
	1	5 757 779	10/26/1993	07/830.314	1/31/1992	COLUMN REDUNDANCY ARCHITECTURE FOR A READ/WRITE MEMORY	Expired	Utility - ORG	NMXS-0047.00/US
1		5,471,426	11/28/1995	07/830.315	1/31/1992	REDUNDANCY DECODER	Issued	Utility - ORG	NMXS-0046.00/US
		040,040	2/15/100/	77/200725	17/17/1991	INTEGRATED CIRCUIT WITH PRECHARGED INTERNAL DATA BUS	Expired	Utility - ORG	NMXS-0045.00/US
	T	8V0 48V 5	1/73/1006	08/041371	3/31/1993	MULTIPLEXING SENSE AMPLIFIER	issued	Utility - ORG	NMXS-0044.00/US
	T	ברבו / /כנכ	1/0/1006	02/207322	9/16/199/	MULTIPLEXING SENSE AMPLIFIER	Issued	Utility - DIV	NMXS-0043.01/US
\perp	Τ	5,777,000	12/27/1994	08/040 916	3/31/1993	MULTIPLEXING SENSE AMPLIFIER HAVING LEVEL SHIFTER CIRCUITS	Issued	Utility - ORG	NMXS-0043.00/US
		2700,412	0001/3/3 4661/0/7	00777792	12/21/1006	TRISTATABLE DRIVER FOR INTERNAL DATA BUS I INFS	Issued	Utility - CON	NMXS-0042.01/US
_	Τ	5,623,438	4/22/1997	07/800 303	12/17/1991	READ/WRITE MEMORY WITH IMPROVED TEST MODE DATA COMPARE	Expired	Utility - ORG	NMXS-0041.00/US
L	T	2,74,45	OCCT/TC/C	CC-7,1CO/OO	000112010	MIBITIAL GROUND READ ONLY MEMORY CIRCUIT	ksiipd	Utility - CON	NMXS-0040_03/US
\perp	S	5,377,153	2/27/1994	886,786//0	7661/06/11	VIRTUAL GROUND READ ONLY MEMORY CIRCUIT	Issued	Utility - DIV	NMXS-0040.02/US
L		5,321,314	6/14/1994	08/109,697	8/20/1993	SIGNAL LINE PULSE ENHANCING CIRCUIT FOR INTEGRATED CIRCUITS	Expired	Utility - CUN	NMXS-0039.01/US
<u> </u>	S	5,287,322	2/15/1994	07/731,802	7/17/1991	INTEGRALED CIRCUIT DUAL-PART MEMORY DEVICE HAVING REDUCED CAPACITANCE	Expired	Utility - ORG	MWXS-0038.00/US
	T	1000	2))						און איני שכיטי שיוי אווי
	Ī	5,297,094	3/22/1994	07/731,487	7/17/1991	INTEGRATED CIRCUIT MEMORY DEVICE WITH REDUNDANT ROWS	Expired	Utility - ORG	NMXS-0037.00/US
		5.339.322	8/16/1994	07/677,313	3/29/1991	CACHE TAG PARITY DETECT CIRCUIT	Expired	Utility - ORG	NMXS-0036.00/US
	1	5,428,632	6/27/1995	07/693,670	4/30/1991	CONTROL CIRCUIT FOR DUAL PORT MEMORY	Expired	Utility - ORG	NMXS-0035.00/US
		5,319,768	6/7/1994	07/694,451	5/1/1991	CONTROL CIRCUIT FOR RESETTING A SNOOP VALID BIT IN A DUAL PORT CACHE TAG MEMORY	Expired	Utility - ORG	NMXS-0034.00/US
L	Sn	5,311,477	5/10/1994	07/731,803	7/17/1991	INTEGRATED CIRCUIT MEMORY DEVICE HAVING FLASH CLEAR	Expired	Utility - ORG	NMXS-0033.00/US
	Sn	5,355,340	10/11/1994	08/101,347	8/2/1993	SEMICONDUCTOR MEMORY WITH MULTIPLEXED REDUNDANCY	Expired	Utility - CON	NMXS-0032.01/US
	IJ	5,258,952	11/2/1993	07/627,236	12/14/1990	SEMICONDUCTOR MEMORY WITH SEPARATE TIME-OUT CONTROL FOR READ AND WRITE OPERATIONS	Expired	Utility - ORG	NMXS-0031.00/US
<u> </u>		5,297,090	3/22/1994	07/627,050	12/13/1990	SEMICONDUCTOR MEMORY WITH COLUMN DECODED BIT LINE EQUILIBRATE	Expired	Utility - ORG	NMXS-0030.00/US
		5,265,054	11/23/1993	07/827,403	12/14/1990	VEHICLE SEAT ASSEMBLY WITH INTEGRATED CHILD SEAT	Expired	Utility - ORG	NMXS-0029.00/US
	SU	5,124,584	6/23/1992	07/601,287	10/22/1990	ADDRESS BUFFER CIRCUIT WITH TRANSITION-BASED LATCHING	Expired	Utility - ORG	NMXS-0028.00/US
	ĸ	5,124,951	6/23/1992	07/588,600	9/26/1990	SEMICONDUCTOR MEMORY WITH SEQUENCED LATCHED ROW LINE REPEATERS	Expired	Utility - ORG	NMXS-0027.00/US
	Sn	5,526,318	6/11/1996	08/376,127	1/19/1995	SEMICONDUCTOR MEMORY WITH POWER-ON RESET CONTROLLED LATCHED ROW UNE REPEATERS	Issued	Utility - CON	NMXS-0026.02/US
	รก	5,121,358	6/9/1992	07/588,609	9/26/1990	SEMICONDUCTOR MEMORY WITH POWER-ON RESET CONTROLLED LATCHED ROW UNE REPEATERS	Expired	Utility - ORG	NMXS-0026.00/US
	Sn	5,099,148	3/24/1992	07/601,288	10/22/1990	INTEGRATED CIRCUIT HAVING MULTIPLE DATA OUTPUTS SHARING A RESISTOR NETWORK	Expired	Utility - ORG	NMXS-0025.00/US
.	S	5,072,138	12/10/1991	07/570,203	8/17/1990	SEMICONDUCTOR MEMORY WITH SEQUENTIAL CLOCKED ACCESS CODES FOR TEST MODE ENTRY	Expired	Utility - ORG	NMXS-0024.00/US
TEI	SN	5,128,897	7/7/1992	07/588,577	9/26/1990	SEMICONDUCTOR MEMORY HAVING IMPROVED LATCHED REPEATERS FOR MEMORY ROW LINE SELECTION	Expired	Utility - ORG	NMXS-0023.00/US
	US	5,119,340	6/2/1992	07/588,601	9/26/1990	SEMICONDUCTOR MEMORY HAVING LATCHED REPEATERS FOR MEMORY ROW LINE SELECTION	Expired	Udlity - ORG	NMXS-0022.00/US
	S	5,706,232	1/6/1998	08/424,722	4/18/1995	SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY	Issued	Utility - CON	NMXS-0021.02/US
	Sn	5,408,435	4/18/1995	07/984,233	11/20/1992	SEMICONDUCTOR MEMORY WITH INHIBITED TEST MODE ENTRY DURING POWER-UP	Issued	Utility - CON	NMXS-0021.01/US
38	Country	Patentivo Country	IssueDate	SerialNo	HieDate		MatterStatus	MatterType	MH DOMES
						Exhibit A - US Issued Patents			

bit A
•
ៜ
issued
Patents

	2		Exhibit A - US issued Patents				H448	
NWXS-0053.00/US	Utility - ORG	Issued	SERIALIZED DIFFERENCE FLAG CIRCUIT	6/22/1992	07/901,667	10/11/1994	5,355,113	Sn
NMXS-0054.00/US	Utility - ORG	issued	PROGRAMMABLE DIFFERENCE FLAG LOGIC	7/31/1992	07/923,855	1/10/1995	5,381,126	S
NMX5-0054.01/US	Utility - CON	Issued	FIFO WITH ADAPTABLE FLAGS FOR CHANGING SYSTEM SPEED REQUIREMENTS	9/8/1994	08/303,172	4/16/1996	5,508,679	US.
NMXS-0055.00/US	Utility - ORG	Expired	INTEGRATED CIRCUIT WITH SELF-BIASED DIFFERENTIAL DATA LINES	12/17/1991	07/809,733	10/26/1993	5,257,226	SS
NMX5-0056.00/US	Utility - ORG	Issued	PROCESS FOR REALIZING P-CHANNEL MOS TRANSISTORS HAVING A LOW THRESHOLD VOLTAGE IN SEMICONDUCTOR INTEGRATED CIRCUITS FOR ANALOG APPLICATIONS	7/28/1994	08/282,408	7/9/1996	5,534,448	g FNT
NMXS-0056.01/US	Alg - Ailith	Issued	PROCESS FOR REALIZING P-CHANNEL MOS TRANSISTORS HAVING A LOW THRESHOLD VOLTAGE IN SEMICONDUCTOR INTEGRATED CIRCUITS FOR ANALOG APPLICATIONS	6/7/1995	08/486,747	12/31/1996	5,589,701	۶ PAT i
NMXS-0057.02/U\$	Utility - CON	Issued	INPUT BUFFER CIRCUIT IMMUNE TO COMMON MODE POWER SUPPLY FLUCTUATIONS	6/7/1995	08/477,283	11/3/1998	5,831,457	SJ
NMXS-0058.00/US	Utility - ORG	Issued	STRUCTURE FOR USING A PORTION OF AN INTEGRATED CIRCUIT DIE	11/13/1992	07/975,628	. 10/11/1994	5,355,344	SU
NMXS-0058.01/US	Utility - CON	lssued	STRUCTURE FOR USING A PORTION OF AN INTEGRATED CIRCUIT DIE	6/21/1994	08/263,048	6/11/1996	5,526,317	SU
NMXS-0059.01/US	Utility - CON	lssued	INTEGRATED CIRCUIT OUTPUT DRIVER	12/30/1994	08/367,681	7/17/2001	6,262,617	US
NMXS-0060.00/US	Utility - ORG	Issued	OUTPUT DRIVER CIRCUIT WITH BODY BIAS CONTROL FOR MULTIPLE POWER SUPPLY OPERATION	1/3/1994	08/176,960	6/6/1995	5,422,591	SS
NMXS-0061.01/US	Utility - CON	Issued	MULTIPLE CLOCKED DYNAMIC SENSE AMPLIFIER	9/15/1994	08/306,527	1/16/1996	5,485,430	US
NMXS-0062.00/US	Utility - ORG	Issued	DUAL DYNAMIC SENSE AMPLIFIERS FOR A MEMORY ARRAY	12/22/1992	07/995,581	10/3/1995	5,455,802	ន
NMXS-0064.00/US	Otility - CIP	lssued	MULTIPLE LEVEL PARALLEL MAGNITUDE COMPARATOR	2/19/1993	08/020,045	3/21/1995	5,389,577	<u> </u>
NMXS-0065.00/US	Utility - ORG	Issued	STRESS TEST FOR MEMORY ARRAYS IN INTEGRATED CIRCUITS	9/30/1992	07/954,276	6/13/1995	5,424,988	S
NMXS-0065.01/US	Utility - CON	Issued	STRESS TEST FOR MEMORY ARRAYS IN INTEGRATED CIRCUITS	6/2/1995	08/460,409	7/1/1997	5,644,542	. SU
NWX-006-00/US	Utility - ORG	issued	SLEW RATE LIMITED OUTPUT BUFFER WITH BYPASS CIRCUITRY	8/31/1992	07/938,399	4/5/1994	5,300,828	S
NMXS-0068.00/US	Utility - ORG	issued	ADDRESS BUFFER	4/30/1993	08/056.078	8/16/1994	5.339.277	S S
Sn/00:6900-5XMN	Utility - ORG	Issued	METHOD FOR STRESS TESTING DECODERS AND PERIPHERY CIRCUITS	4/30/1993	08/056,376	8/23/1994	5,341,336	S
NMXS-0070.00/US	Utility - ORG	Issued	INPUT BUFFER WITH HYSTERESIS CHARACTERISTICS	12/21/1992	07/995,666	9/20/1994	5,349,246	LS.
NMXS-0072.00/US	Utility - ORG	Issued	REDUNDANCY ELEMENT CHECK IN IC MEMORY WITHOUT PROGRAMMING SUBSTITUTION OF REDUNDANT ELEMENTS	7/30/1993	08/099,606	4/4/1995	5,404,331	S S
NMXS-0073.00/US	Utility - ORG	Issued	TEMPERATURE-STABLE CURRENT SOURCE	5/31/1995	08/454,926	7/1/1997	5,644,216	SS
NMXS-0074-01/US	Utility - DIV	Issued	PROCESS FOR IMPROVING THE INTERFACE UNION AMONG DIELECTRIC MATERIALS IN AN INTEGRATED CIRCUIT MANUFACTURE	6/6/1995	08/473,552	5/6/1997	5,627,403	ß
NMXS-0074.02/US	Utility - CON	Issued	PROCESS FOR IMPROVING THE INTERFACE UNION AMONG DIELECTRIC MATERIALS IN AN INTEGRATED CIRCUIT MANUFACTURE	11/18/1996	08/751,244	8/18/1998	5,795,821	દ્ધ
NMXS-0075.00/US	Utility - ORG	Issued	VOLTAGE GENERATOR CIRCUIT PROVIDING POTENTIALS OF OPPOSITE POLARITY	9/26/1994	08/311,941	8/13/1996	5,546,044	ኤ
NMXS-0076.00/US	Utility - ORG	Abandoned	PROCESS FOR THE MANUFACTURE OF AN INTEGRATED VOLTAGE LIMITER AND STABILIZER IN FLASH EEPROM MEMORY DEVICES	9/7/1994	08/301,792	1/23/1996	5,486,486	ន
NMXS-0076.01/US	Utility - DIV	Issued	PROCESS FOR THE MANUFACTURE OF AN INTEGRATED VOLTAGE LIMITER AND STABILIZER IN FLASH EEPROM MEMORY DEVICES	6/7/1995	08/477,302	2/4/1997	5,600,590	Sn
NMXS-0077.00/US	Utility - ORG	Issued	MONOLITHICALLY INTEGRATED STORAGE DEVICE	11/30/1994	08/347,653	7/9/1996	5,535,157	UŞ.
NMXS-0078.00/US	Utility - ORG	Issued	CIRCUIT FOR COVERING INITIAL CONDITIONS WHEN STARTING-UP AN INTEGRATED CIRCUIT DEVICE	1/30/1995	08/380,309	3/18/1997	5,612,641	ß
NMXS-0079.00/US	Utility - ORG	Issued	METHOD AND DEVICE FOR SUPPLYING NEGATIVE PROGRAMMING VOLTAGES TO NON- VOLATILE MEMORY CELLS IN A NON-VOLATILE MEMORY DEVICE	11/23/1994	08/344,232	6/18/1996	5,528,536	ß
NMXS-0079.01/US	Utility - DIV	issued	METHOD AND DEVICE FOR SUPPLYING NEGATIVE PROGRAMMING VOLTAGES TO NON- VOLATILE MEMORY CELLS IN A NON-VOLATILE MEMORY DEVICE	4/26/1996	08/639,931	8/19/1997	5,659,501	US

bit A
•
ŝ
issued
Patents

いたのかのでは、これには、これでは、これのできる	The state of the s		The fact of the fa		THE PERSON NAMED IN COLUMN TWO IS NOT THE OWNER. WHEN			
NMXS-0079.02/US	NMXS-0079.02/US Utility - CON Issued	Issued	METHOD AND DEVICE FOR SUPPLYING NEGATIVE PROGRAMMING VOLTAGES TO NON- VOLATILE MEMORY CELLS IN A NON-VOLATILE MEMORY DEVICE	6/9/1997	08/871,226	10/6/1998	760	SS
NMXS-0080.00/US	Utility - ORG	issued	REDUNDANCY CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE	12/6/1994	08/349,783	10/15/1996	5,566,114	ຮ
NMXS-0081.01/US	Utility - CON	Issued	INTEGRATED CIRCUIT FOR THE PROGRAMMING OF A MEMORY CELL IN A NON- VOLATILE MEMORY REGISTER	4/18/1996	08/635,455	7/1/1997	5,644,529	ß
NMXS-008Z.00/US	Utility - ORG	Ssued	METHOD FOR PROGRAMMING REDUNDANCY REGISTERS IN A ROW REDUNDANCY INTEGRATED CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE, AND ROW REDUNDANCY INTEGRATED CIRCUITRY	2/16/1995	08/391,999	8/19/1997	5,659,509	US
NMXS-0083.00/US	Utility - ORG	Issued	INTEGRATED CIRCUITRY FOR CHECKING THE UTILIZATION RATE OF REDUNDANCY MEMORY ELEMENTS IN A SEMICONDUCTOR MEMORY DEVICE	12/7/1994	08/350,961	2/20/1996	5,493,531	SS
NMXS-0083.01/US	Utility - CIP	Issued	INTEGRATED CIRCUTTRY FOR CHECKING THE UTILIZATION RATE OF REDUNDANCY IMEMORY ELEMENTS IN A SEMICONDUCTOR MEMORY DEVICE	2/16/1996	08/602,237	1/13/1998	5,708,601	US
NMXS-0084.00/US	Utility - ORG	Issued	REDUNDANCY CIRCUITRY LAYOUT FOR A SEMICONDUCTOR MEMORY DEVICE	3/29/1995	08/412,550	9/24/1996	5,559,743	S
NMXS-0085.00/US	Utility - ORG	Issued	CURRENT SOURCE HAVING VOLTAGE STABILIZING ELEMENT	1/20/1995	08/377,524	8/13/1996	5,546,054	SU
NMXS-0086.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR TIMING THE LOADING OF NONVOLATILE-MEMORY OUTPUT DATA	2/21/1995	08/391,160	5/7/1996	5,515,332	US
NMXS-0087.00/US	Utility - ORG	Issued	INTERNAL TIMING METHOD AND CIRCUIT FOR PROGRAMMABLE MEMORIES	2/21/1995	08/391,159	9/2/1997	5,663,921	US
NMXS-0088.01/US	Utility - CON	issued	LOAD SIGNAL GENERATING METHOD AND CIRCUIT FOR NONVOLATILE MEMORIES	2/25/1997	08/803,915	2/10/1998	5,717,642	S
SO/10'6800-5XWN	Utility - CON	issued	COUNT UNIT FOR NONVOLATILE MEMORIES	8/20/1996	08/700,126	11/11/1997	5,687,135	ls.
NMXS-0091.01/US	Utility - CON	Issued	VOLTAGE BOOSTER WITH AN ACCELERATION CIRCUIT	5/14/1997	08/855,922	6/16/1998	5,768,115	5 5
NMXS-0092,00/US	Utility ~ ORG	Issued	BIAS CIRCUIT FOR A MEMORY LINE DECODER DRIVER OF NONVOLATILE MEMORIES	12/2/1994	08/348,461	3/12/1996	5,499,217	સ
NMXS-0093.00/US	Utility - ORG	issued	READING CIRCUIT FORAN INTEGRATED SEMICONDUCTOR MEMORY DEVICE	3/22/1995	08/408,589	5/6/1997	5,627,790	US
NMXS-0094.00/US	Utility - ORG	issued	METHOD AND APPARATUS FOR TESTING A NETWORK WITH A PROGRAMMABLE LOGIC MATRIX	11/28/1994	08/345,530	2/10/1998	5,717,698	SO
NMXS-0095.00/US	Utility - ORG	issued	METHOD FOR PROGRAMMING AND TESTING A NONVOLATILE MEMORY	1/31/1995	08/381,530	2/4/1997	5,600,600	LS
NMXS-0096.00/US	Utility - ORG	Issued	THRESHOLD VOLTAGE MEASURING DEVICE FOR MEMORY CELLS	3/31/1995	08/412,326	2/4/1997	5,600,594	US
NMXS-0097.00/US	Utility ~ ORG	lssued	CIRCUIT FOR IDENTIFYING A MEMORY CELL HAVING ERRONEOUS DATA STORED THEREIN	8/30/1995	08/521,304	11/11/1997	5,687,124	US
SO/00'8600-5XMN	Utility - ORG	Issued	DEVICE FOR DETECTING A REDUCTION IN A SUPPLY YOLTAGE	12/29/1994	08/366,211	12/10/1996	5,583,820	US
NMXS-0098.01/US	Utility - DIV	Issued	DEVICE FOR DETECTING A REDUCTION IN A SUPPLY VOLTAGE	9/9/1996	08/711,132	5/5/1998	5,748,548	LS
NMXS-0099.00/US	Utility - ORG	Issued	STABLE REFERENCE VOLTAGE GENERATOR CIRCUIT	11/30/1994	08/347,788	5/21/2002	6,392,469	LIS
Sn/00'00'00'NNX	Utility - ORG	Issued	REGULATION CIRCUIT AND METHOD FOR THE ERASING PHASE OF NON-VOLATILE MEMORY CELLS	2/21/1995	08/395,361	4/1/1997	5,617,356	US
SU/00.1010-5XWN	Utility - ORG	Issued	CIRCUIT DEVICE AND CORRESPONDING METHOD FOR RESETTING NON-VOLATILE AND ELECTRICALLY PROGRAMMABLE MEMORY DEVICES	12/29/1994	08/366,212	12/17/1996	5,586,077	S
NMXS-0102.00/US	Utility - ORG	Issued	VOLTAGE REGULATOR FOR PROGRAMMING NON-VOLATILE AND ELECTRICALLY PROGRAMMABLE MEMORY CELLS	12/29/1994	08/366,259	5/21/1996	5,519,656	US
NMXS-0103.00/US	Utility - ORG	Issued	VOLTAGE REGULATOR FOR NON-VOLATILE SEMICONDUCTOR ELECTRICALLY PROGRAMMABLE MEMORY DEVICES	1/3/1995	08/368,211	8/19/1997	5,659,516	รก
NMXS-0103.01/US	Utility - DIV	Issued	VOLTAGE REGULATOR FOR NON-VOLATILE SEMICONDUCTOR ELECTRICALLY PROGRAMMABLE MEMORY DEVICES	4/1/1997	08/831,046	5/18/1999	5,905,677	Sn
NMXS-0104.00/US	Utility - ORG	lssued	INTEGRATED PROGRAMMING CIRCUITRY FOR AN ELECTRICALLY PROGRAMMABLE SEMICONDUCTOR MEMORY DEVICE WITH REDUNDANCY	12/28/1994	08/365,154	8/20/1996	5,548,554	SS
NMXS-0105.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR SUPPRESSING DATA LOADING NOISE IN NONVOLATILE MEMORIES	2/21/1995	08/391,147	7/30/1996	5,541,884	US
SU/00:9010-SXWN	Utility - ORG	Issued	METHOD AND CIRCUIT FOR TIMING THE READING OF NONVOLATILE MEMORIES	2/21/1995	08/391,920	7/2/1996	5,532,972	US

Exhibit A -
S
Issued
Patents

Multicy DRG Issued Utility - ORG Issued	R	5,742,548	4/21/1998	08/340,940	11/17/1994	ISSUED ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY WITH WRITE CHECKING	Ottiny - ORG	NIVIX3-ULISETU-CXIVINI
Unitro-Order Manuscript M	ક		2/20/1996	08/202,830	2/28/1994			NMXS-0137.00/US
Unifier-Order Management	25		6/13/1995	08/170,612	12/20/1993			SU/00.9810-SXMN
Unitiny-ORG Laused MANISTERION ARRANGE CRUITURY FOR ALCHING STATE AND ALCHING STATE	SU		11/19/1996	08/173,197	12/22/1993		+	NMXS-0135.00/US
Unitiny-ORG Based BASH-ERFOON MEMORY ARAN CELLUT MICRON ADDRESS BASH-SAN BASH SAN	אל אל	T	2/13/1996	08/174,139	12/28/1993		_	NMXS-0134.00/US
Unitity-ORG Issaed ALCHEOTREM Issaed	3	T	8/8/1995	809'091/80	11/30/1993		_	NMX5-0133.00/US
Unitity-ORG Lissaed PLASHESTRIAN METHOD CREATING REPREVANCE SAZIASES USA	ठ		10/22/1996	08/172,853	12/22/1993			NMXS-0132.00/US
Unitity-ORG Issaed International Inter	SU		5/23/1995	08/129,763	9/30/1993			NMXS-0131.00/US
Unlithy-ORG Leaned MANOYER READANG CIRCUIT WITH COTTAL CICARRETH BEANCH A171/1995 CRE/2221831 MORPHONE CREATING CREA	22		3/7/1995	08/129,257	9/30/1993		-	NMXS-0130.00/US
Unitry-ORG Issued PASH-EERPOM MEMORY ARRAY SUD METHOD FOR FIGHER SUACH Unitry-ORG Issued PASH-EERPOM MEMORY ARRAY SUD METHOD FOR FIGHER SUACH Unitry-ORG Issued PASH-EERPOM MEMORY ARRAY SUD METHOD FOR FIGHER SUACH Unitry-ORG Issued PASH-EERPOM MEMORY ARRAY SUD METHOD FOR FIGHER SUACH Unitry-ORG Issued PASH-EERPOM MEMORY ARRAY SUD METHOD FOR FIGHER SUACH Unitry-ORG Issued PASH-EERPOM MEMORY ARRAY SUD METHOD FOR FIGHER SUACH Unitry-ORG Issued PASH-EERPOM MEMORY ARRAY SUD METHOD FOR FIGHER SUACH Unitry-ORG Issued PASH-EERPOM MEMORY ARRAY SUD METHOD FOR FIGHER SUACH Unitry-ORG Issued PASH-EERPOM MEMORY ARRAY SUD METHOD FOR FIGHER SUACH Unitry-ORG Issued PASH-EERPOM MEMORY ARRAY SUD METHOD FOR FIGHER SUACH Unitry-ORG Issued PASH-EERPOM MEMORY ARRAY SUD METHOD FOR FIGHER SUACH Unitry-ORG Issued PASH-EERPOM MEMORY ARRAY SUD METHOD FOR FIGHER SUACH Unitry-ORG Issued PASH-PASH SUACH SUCCESS VASHAN SUACH SUD MEMORY ARRAYS VASHAN SUACH SUACH SUACH SUBJECT OF FIRST SUACH SUACH SUBJECT OF FIRST SUACH SU	72		1/13/1998	08/717,139	9/20/1996			NMXS-0129.01/US
Utility-ORG Issued CHANGER REGULATOR FOR NOW-VOLATILE SEMICONDUCTOR NEWOOF DEVICE, AND COLUMN NEWOOF DEVICE DEV	Σ,		10/22/1996	08/492,219	6/19/1995		-	NMXS-0128.01/US
Utility - ORG	ટા		8/8/2000	08/172,848	12/22/1993			NMXS-0127.00/US
Unitry-ORG	ะ		11/10/1998	08/172,854	12/22/1993			NMXS-0126.00/US
Utility-ORG	S		8/8/1995	08/188,158	1/27/1994			NMXS-0125.00/US
Utility-ORG Issued MENORY MARKACELL READMO CRECIT UNITED TRACLISEER FISHANCE 4/17/1995 OR/14/2.813 OR/12/395 OR/14/2.813 OR/14/395 OR/14/3	S		6/28/2001	09/139,225	8/25/1998			MMXS-0124.03/US
Unitity-ORG Issued METHON REPORT ARRAY CELL READING CIRCUIT WITH DOTAL CHREST BRANCH 177/1995 08/422,163; 10/9/1995 08/25,252,00 US Unitity-ORG Issued METHOD FOR DRAWN CIRCUIT WITH DOTAL CHREST BRANCH 2/26/1995 08/25/25/25 US 08/27/25/25 US 08/27/	ટડ		1/11/2000	08/801,452	2/18/1997			NMXS-0124,02/US
WRITH-PURE WRITE-CHARGE Inches WRITH-PURE CAPTER CHREENT BRANCH Utility - ORG Issued MRENDO FOR ROSENAMEN AND METHOD FOR BUSING THE SAME 3/28/1995 08/421,567 05/52,533 05/52,53	ঠ		11/5/1996	08/114,747	8/31/1993			NMXS-0123.00/US
Utility - ORG	25 25		11/24/1998	08/647,222	5/9/1996			NMX5-0122.01/US
Welffry-ORG	3 2	1	11/26/1996	08/189.589	1/31/1994			NMXS-0122.00/US
WRITTNY-RES WRITTNY-RES WRITTNY-CORG Issued WRITTNY-CORG RESURED WRITTNY-CORG RESURED WRITTNY-CORG RESURED WRITTNY-CORG RESURED WRITTNY-CORG WR	7 6	T	3/28/1995	08/114.749	8/31/1993			NMXS-0121.00/US
WAITPIAPE WASTRECTION INCIDENCE IN	7 5		12/5/1995	08/298.766	8/31/1994			NMXS-0120.01/US
WHITP-ORG	7 0	1	12/27/199/	08/099 947	7/30/1993			NMXS-0120.00/US
WHIRY-ORG Issued MEMORY ARRAY CELL READING CIRCUIT WITH DOTAN CURRENT BRANCH 4/17/1995 08/472,523 10/1995 5,583,275 US US US US US US US U	ñ	T	11/21/1005	08/188 153	1/27/1994			NMXS-0119.00/US
Militry-ORG	સ		5/6/1997	08/413,789	3/30/1995			NMXS-0118.01/US
MRITERY/MPC	স		8/13/1996	08/410,383	3/27/1995			NMXS-0117.01/US
MARKENTRE MARK	S		6/27/1995	08/085,580	6/30/1993			NMXS-0116.00/US
Mathre-Water Math	75	T	9/20/1994	08/085,760	6/30/1993			NMXS-0115.00/US
Waterstade Wat	73 6	T	11/7/1995	08/069.025	5/28/1993			NMXS-0114.00/US
Mathershipe	77	T	11/7/1995	08/966.042	11/7/1997			NMXS-0114.00/RE
Utility - ORG	S		11/28/1995	08/051,184	4/22/1993			NMXS-0113.00/US
Utility - ORG			7/14/1998	08/932,930	9/18/1997		-	NMXS-0112.02/US
Utility - ORG			7/14/1998	09/616,821	7/12/2000			NMXS-0112.00/RE
WatterStatus Watt			11/19/1996	08/367,538	1/3/1995			NMXS-0111.00/US
Watterstands Watt			7/30/1996	08/411,904	3/28/1995			NMXS-0210.00/US
Writing - Org Issued MEMORY ARRAY CELL READING CIRCUIT WITH EXTRA CURRENT BRANCH 4/17/1995 08/422,813 10/8/1996 5,563,826 Utility - Org Issued FLASH-EEPROM MEMORY ARRAY AND METHOD FOR BIASING THE SAME 3/28/1995 08/412,162 6/10/1997 5,638,327			2/11/1997	08/389,599	2/16/1995			Sn/00'60to-sxwin
MatherLype Manuestatus Tible Tible September 1916 S	Š		6/10/1997	08/412,162	3/28/1995	FLASH-EEPROM MEMORY ARRAY AND METHOD FOR BIASING THE SAME		NMX5-0108.00/US
MatterLupe : Anamerolatus Serjain July Matter Matte	S		10/8/1996	08/422,813	4/17/1995	MEMORY ARRAY CELL READING CIRCUIT WITH EXTRA CURRENT BRANCH		L
	TT.			SerialNo	Hiebate	inte a second of the second of		

241
u
7
-
•
C
S
,,,,,
SS
Ë
ᇒ
Ď.
Ξ
79
m
ᄍ
-
**
Į,

	A ANGELON AND ANGELON ANGE		Exhibit A - US issued Patents		SecolNo	decipoato	skileDate PalentNo Country	Colmtw
NMXS-0139.00/US Utility - ORG Issued MANUE	Utility - ORG	Issued	DR-CAPACITOR-TRANSISTOR TYP	5/19/1994	08/246,070	7/4/1995	5,430,319	SS
NMXS-0139.01/US	Utility - CON	Issued	RELAXATION OSCILLATOR USING INTEGRATED RTC STRUCTURE	3/8/1995	08/299,900	8/26/1997	5,661,324	υş
NMXS-0140.00/US	Utility - ORG	Issued	INTEGRATED CIRCUIT CONTAINING A PROTECTED MEMORY AND SECURED SYSTEM USING SAID INTEGRATED CIRCUIT	10/27/1994	08/329,975	1/14/1997	5,594,793	ß
NMXS-0141.00/US	Utility - ORG	Issued	LINE DECODER CIRCUIT FOR A MEMORY WORKING AT LOW SUPPLY VOLTAGES	12/21/1994	08/361,313	9/10/1996	5,555,216	S US
NMXS-01.42.00/US	Utility - ORG		MEMORY IN INTEGRATED CIRCUIT FORM WITH IMPROVED READING TIME	12/21/1994	08/361,996	7/16/1996	5,537,349	5
NMXS-0143.00/US	Utility - ORG	Issued	METHOD FOR MAKING A BIPOLAR TRANSISTOR FOR THE PROTECTION OF AN INTEGRATED CIRCUIT AGAINST ELECTROSTATIC DISCHARGES	1/27/1995	08/379,337	3/23/1999	5,886,386	US
NMXS-0143.01/US	Utility - DIV	Issued	METHOD FOR MAKING A BIPOLAR TRANSISTOR FOR THE PROTECTION OF AN INTEGRATED CIRCUIT AGAINST ELECTROSTATIC DISCHARGES	12/24/1998	09/220,635	7/24/2001	6,265,277	US .
NMXS-0144.02/US	Utility - CON	issued	BIAS CIRCUIT FOR TRANSISTOR OF A STORAGE CELL	12/16/1996	08/767,521	5/4/1999	5,900,756	s
NMXS-0145.00/US	Utility - ORG	Issued	MEMORY REDUNDANCY CIRCUIT	2/27/1995	08/393,464	11/26/1996	5,5/9,265	5
NMXS-0146.00/US	Utility - ORG	issued	INTEGRATED CIRCUIT MEMORY WITH COLUMN VOLTAGE HOLDING CIRCUIT	3/10/1995	08/402,519	3/11/199/	048,0T9'5	ī 8
NMXS-0146.01/US	Utility - DIV	Issued	INTEGRATED CIRCUIT MEMORY WITH COLUMN VOLTAGE HOLDING CIRCUIT	3/4/199/	08/811.558	966T//T/C	201,527,5	8
NMXS-0147.00/US	Utility - ORG	issued	STATE FOR MEMORY REDUNDANCY CIRCUIT	1/30/1995	08/380,737	2/25/1997	5,606,523	us
NMXS-0148.00/US	Utility - ORG	Issued	NON-VOLATILE-PROGRAMMABLE BISTABLE MULTIVIBRATOR, PROGRAMMABLE BY THE SOURCE, FOR MEMORY REDUNDANCY CIRCUIT	1/30/1995	08/380,738	1/7/1997	5,592,417	US
NMXS-0148.01/US	Utility - DIV	Issued	NON-VOLATILE-PROGRAMMABLE BISTABLE MULTIVIBRATOR, PROGRAMMABLE BY THE SOURCE, FOR MEMORY REDUNDANCY CIRCUIT	11/21/1996	08/752,814	10/14/1997	5,677,870	S
NMXS-0148.02/US	Utility ~ DIV	Issued	NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR, PROGRAMMABLE BY THE SOURCE, FOR MEMORY REDUNDANCY CIRCUIT	11/21/1996	08/754,432	2/24/1998	5,721,706	ង
NMXS-0149.00/US	Utility - ORG	lssued	NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR WITH REDUCED PARASITICS IN READING MODE NOTABLY FOR MEMORY REDUNDANCY CIRCUIT	1/31/1995	08/381,529	10/1/1996	5,561,621	SS
Sn/00'0510-5XWN	Utility ~ ORG	bsued	SWITCHING REGULATOR WITH DYSSYMETRICAL DIFFERENTIAL INPUT STAGE	4/19/1995	08/423,398	3/18/1997	5,612,611	S
NMXS-0151.00/US	Utility - ORG	Issued	VOLTAGE BOOSTER CIRCUIT	4/19/1995	08/423,396	6/3/1997	5,636,115	55
NMXS-0152.00/US	Utility - ORG	Abandoned	METHOD FOR THE ERASURE OF A MEMORY, AND CIRCUITS FOR THE IMPLEMENTATION THEREOF	4/12/1995	08/421,671	4/8/1997	5,619,451	ĸ
Sn/00'8510-5xwn	Utility - ORG	Issued	CIRCUIT FOR THE SELECTION OF REDUNDANT MEMORY ELEMENTS AND FLASH EEPROM MEMORY COMPRISING SAID CIRCUIT	2/22/1995	08/394,314	8/18/1998	5,796,653	S
NMXS-0154.00/US	Utility - ORG	Issued	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY INCORPORATING TEST FUNCTIONS	4/7/1995	08/418,636	7/1/1997	5,644,530	ĸ
NMXS-0155.00/US	Utility - ORG	lssued	PROGRAMMABLE INTEGRATED CIRCUIT MEMORY COMPRISING EMULATION MEANS	6/7/1995	08/484,873	7/22/1997	5,651,128	SU
NMXS-0156.00/US	Utility - ORG	Issued	MATRIX DEVICE WITH REDUNDANCY FUSES FOR INTEGRATED MEMORY	3/21/1995	08/408,016	1/14/1997	5,594,693	cs
NMXS-0157.00/US	Utility - ORG	lssued	METHOD FOR TESTING AN ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY DEVICE	6/7/1995	08/479,081	12/31/1996	5,590,075	SS
NMXS-0158.01/US	Utility - CON	Issued	PROGRAMMABLE MEMORY ELEMENT	2/4/1997	08/794,965	12/9/1997	5,696,716	US.
NMXS-0159.00/US	Utility - ORG	Issued	SENSE AMPLIFIER WITH HYSTERESIS	5/2/1995	08/432,838	2/3/1998	5,715,204	SS
NMXS-0160.01/US	Utility - DIV	tssued	HIGHLY-PLANAR INTERLAYER DIELECTRIC THIN FILMS IN INTEGRATED CIRCUITS	6/6/1995	08/468,282	1/28/1997	5,598,028	US
NMXS-0161.00/US	Utility - ORG	Issued	PROCESS FOR THE PRODUCTION OF A SEMICONDUCTOR DEVICE HAVING BETTER INTERFACE ADHESION BETWEEN DIELECTRIC LAYERS	12/22/1995	08/577,125	11/28/2000	6,153,537	US
NWXS-0161.01/US	Utility - DIV	lssued	PROCESS FOR THE PRODUCTION OF A SEMICONDUCTOR DEVICE HAVING BETTER INTERFACE ADHESION BETWEEN DIELECTRIC LAYERS	12/14/1998	09/211,065	3/11/2003	6,531,714	SI
NMXS-0162.00/US	Utility - ORG	Issued	FAILURE TOLERANT MEMORY DEVICE, IN PARTICULAR OF THE FLASH EEPROM TYPE	5/31/1995	08/454,650	10/28/1997	5,682,349	SN

~
~
≖.
5
·
4
➣
٠
-
C
S
_
v
(A)
-
-
n
12
Œ
.,

₩.
7
m.
~
-
~
v.

	Su 8	5,841,728	11/24/1998	08/724,495	9/30/1996	ed HIERARCHIC MEMORY DEVICE HAVING AUXILIARY LINES CONNECTED TO WORD LINES	Utility - ORG Issued	Utility	NMXS-0187.00/US
	Sn 0	5,764,570	6/9/1998	08/691,796	8/2/1996	ECURRENT DETECTING CIRCUIT	Utility - URG Issued	Aginan	CO/OO'98TO-CYIMIN
	7 US	5,914,867	6/22/1999	08/631,574	4/12/1996			Utility	NIMXS-0185.00/US
	7 115	5,812,017	9/22/1998	08/567,328	12/5/1995		Utility - ORG Issued	Utility	NMX5-0184,00/US
	S US	6,104,058	8/15/2000	08/898,155	7/22/1997	METHOD FOR IMPROVING THE INTERMEDIATE DIELECTRIC PROFILE, PARTICULARLY FOR NON-VOLATILE MEMORIES	Utility - DIV Issued	Utility	NMXS-0183.01/US
	S US	5,894,065	4/13/1999	08/802,619	2/19/1997		- ORG Issued	Utility - ORG	NMXS-0183.00/US
	S US	6,114,203	9/5/2000	08/644,892	5/10/1996		- ORG Issued	Utility - ORG	NMXS-0182.00/US
	ı S	5,856,221	1/5/1999	08/670,179	6/20/1996	PROCESS FOR FORMING AN INTEGRATED CIRCUIT COMPRISING NON-VOLATILE MEMORY CELLS AND SIDE TRANSISTORS OF AT LEAST TWO DIFFERENT TYPES, AND CORRESPONDING IC	Utility - ORG Issued	Utility	NWIXS-0181.00/US
	Su o	6,248,630	6/19/2001	09/300,029	4/27/1999	PROCESS FOR FORMING AN INTEGRATED CIRCUIT COMPRISING NON-VOLATILE MEMORY CELLS AND SIDE TRANSISTORS AND CORRESPONDING IC	- CON Issued	Utility - CON	NMXS-0180.01/US
	7 US	6,004,847	12/21/1999	08/667,097	6/20/1996		- ORG Issued	Utility - ORG	SD/00'08'00-5XWN
	3 US	5,949,713	9/7/1999	09/094,916	6/15/1998	NONVOLATILE MEMORY DEVICE HAVING SECTORS OF SELECTABLE SIZE AND NUMBER	- CON Issued	Utility - CON	NMXS-0179.01/US
	S B	5,793,676	8/11/1998	08/649,857	5/3/1996	NONVOLATILE MEMORY DEVICE HAVING SECTORS OF SELECTABLE SIZE AND NUMBER	- ORG Issued	Utility - ORG	NMXS-0179.00/US
	1 US	5,696,461	12/9/1997	08/521,666	8/31/1995	ed POWER-ON RESET CIRCUIT	Utility - ORG Issued	Utility	NMXS-0178.00/US
		5,612,913	3/18/1997	08/533,631	9/25/1995		- ORG Issued	Utility - ORG	NMXS-0177.00/US
	Sn 9	5,717,636	2/10/1998	08/642,325	5/3/1996		ORG Issued	Utility - ORG	NMXS-0176.00/US
	S I	5,731,716	3/24/1998	08/592,122	1/26/1996	PROGRAMMABLE MULTIBIT REGISTER FOR COINCIDENCE AND JUMP OPERATIONS AND COINCIDENCE FUSE CELL	- ORG Issued	Utility - ORG	NMXS-0174.00/US
		5,657,276	8/12/1997	08/649,468	5/17/1996	OUTPUT STAGE FOR INTEGRATED CIRCUITS, PARTICULARLY FOR ELECTRONIC MEMORIES	-ORG Issued	Utility - ORG	NMXS-0173.00/US
	7 US	5,742,187	4/21/1998	08/560,090	11/17/1995		-ORG Issued	Utility - ORG	NMXS-0172.00/US
		5,850,361	12/15/1998	08/628,587	4/4/1996	ED PROGRAMMABLE MEMORY WITH SINGLE BIT ENCODING	- ORG Issued	Utility - ORG	NMXS-0171.00/US
		5,633,834	5/27/1997	08/560,324	11/17/1995		- ORG Issued	Utility - ORG	NMXS-0170.00/US
	S	5,710,739	1/20/1998	08/476,547	6/6/1995		- ORG Issued	Utility - ORG	NMXS-0169.00/US
	ક ક્ર	5,644,526	7/1/1997	08/538,302	10/2/1995	INTEGRATED CIRCUIT WITH IMPROVED IMMUNITY TO LARGE METALLIZATION DEFECTS	- ORG ssued	Utility - ORG	NMXS-0168.00/US
	5	5,850,360	12/15/1998	08/607,779	2/27/1996	HIGH-VOLTAGE N-CHANNEL MOS TRANSISTOR AND ASSOCIATED MANUFACTURING PROCESS	- ORG Issued	Utility - ORG	NMXS-0167.00/US
TZ		6,144,588	11/7/2000	09/150,802	9/10/1998	MONOLITHICALLY INTEGRATED GENERATOR OF A PLURALITY OF VOLTAGE VALUES	-CON Issued	utility - CON	NMXS-0166.01/US
	US	5,982,666	11/9/1999	09/013,141	1/26/1998		- CON Issued	Utility - CON	NWXS-0165.01/US
	2 US	5,729,492	3/17/1998	08/639,192	4/26/1996		- ORG Issued	Utility - ORG	NWXS-0165.00/US
:		5,761,222		08/538,161	10/2/1995	MEMORY DEVICE HAVING ERROR DETECTION AND CORRECTION FUNCTION, AND METHODS FOR READING, WRITING AND ERASING THE MEMORY DEVICE	- ORG Issued	Utility - ORG	NMXS-0164.00/US
	SU	5,920,776		08/712,373	9/11/1996		- DIV Issued	Utility - DIV	NMXS-0163.01/US
	S	5,712,814	1/27/1998	08/503,303	7/18/1999	NONVOLATILE MEMORY CELL AND A METHOD FOR FORMING THE SAME	- ORG Issued	Utility - ORG	NMXS-0163.00/us
	Comm	PatentNo	2	SenalNo	FileDate	Spirit and the spirit	MIFDERNO Mattestype Mattessaus	Matte	WIT-DEGNo

Exhibit
À
S
Issued
Patents

I									
1	SS	5,699,295	12/16/1997	08/649,282	5/17/1996	CURRENT DETECTION CIRCUIT FOR READING A MEMORY IN INTEGRATED CIRCUIT FORM	Issued	Utility - ORG	NMXS-0218.00/US
i	SJ	5,742,546	4/21/1998	08/526,500	9/11/1995	METHOD AND DEVICE FOR ADDRESS DECODING IN AN INTEGRATED CIRCUIT MEMORY	Issued	Utility - ORG	NMXS-0217.00/US
	SS	5,675,539	10/7/1997	08/575,953	12/21/1995	METHOD AND CIRCUIT FOR TESTING MEMORIES IN INTEGRATED CIRCUIT FORM	Issued	Utility - ORG	NMXS-0216.00/US
<u></u> l	US	5,734,608	3/31/1998	08/580,549	12/29/1995	RESIDUAL CHARGE ELIMINATION FOR A MEMORY DEVICE	Issued	Utility - ORG	NMXS-0215.00/US
	Sn	6,052,806	4/18/2000	08/519,192	8/25/1995	METHOD AND APPARATUS FOR TESTING AN INTEGRATED CIRCUIT DEVICE	Issued	Utility - ORG	NMXS-0214.00/US
I	SS	5,572,470	11/5/1996	08/438,349	5/10/1995	APPARATUS AND METHOD FOR MAPPING A REDUNDANT MEMORY COLUMN TO A DEFECTIVE MEMORY COLUMN	Issued	Utility - ORG	NNXS-0213.00/US
	US	5,917,353	6/29/1999	08/848,342	4/30/1997	CLOCK PULSE EXTENDER MODE FOR CLOCKED MEMORY DEVICES HAVING PRECHARGED DATA PATHS	Issued	Utility - CON	NMXS-0212.01/US
Iİ	S	5,589,794	12/31/1996	08/360,227	12/20/1994	DYNAMICALLY CONTROLLED VOLTAGE REFERENCE CIRCUIT	Issued	Utility - ORG	NMXS-0211.00/US
1	S	5,598,122	1/28/1997	08/359,926	12/20/1994	VOLTAGE REFERENCE CIRCUIT HAVING A THRESHOLD VOLTAGE SHIFT	Issued	Utility - ORG	NMXS-0210.00/US
1	s	5,581,209	12/3/1996	08/359,927	12/20/1994	ADJUSTABLE CURRENT SOURCE	Issued	Utility - ORG	NMXS-0209.00/US
1	SS	5,594,373	1/14/1997	08/359,397	12/20/1994	OUTPUT DRIVER CIRCUITRY WITH SELECTIVE LIMITED OUTPUT HIGH VOLTAGE	Issued	Utility - ORG	NMXS-0208.00/US
	S	5,548,241	8/20/1996	08/360,229	12/20/1994	VOLTAGE REFERENCE CIRCUIT USING AN OFFSET COMPENSATING CURRENT SOURCE	Issued	Utility - ORG	NMXS-0207.00/US
<u> </u>	SS	5,596,297	1/21/1997	08/360,228	12/20/1994	OUTPUT DRIVER CIRCUITRY WITH LIMITED OUTPUT HIGH VOLTAGE	Issued	Utility - ORG	NMXS-0206.00/US
L	SS	5,654,663	8/5/1997	08/631,063	4/12/1996	CIRCUIT FOR PROVIDING A COMPENSATED BIAS VOLTAGE	Issued	Utility - CON	NMXS-0205.01/US
لـــا	ક્ક	5,568,084	10/22/1996	08/357,664	12/16/1994	CIRCUIT FOR PROVIDING A COMPENSATED BIAS VOLTAGE	Issued	Utility - ORG	NMXS-0205.00/US
	8	5,579,263	11/26/1996	08/362,187	12/22/1994	POST-FABRICATION SELECTABLE REGISTERED AND NON-REGISTERED MEMORY	Issued	បឋម៉ាស្ម - ORG	NMXS-0204.00/US
L	US	5,574,688	11/12/1996	08/438,903	5/10/1995	APPARATUS AND METHOD FOR MAPPING A REDUNDANT MEMORY COLUMN TO A DEFECTIVE MEMORY COLUMN	Issued	Utility - ORG	NMXS-0203.00/US
	US	5,610,866	3/11/1997	08/331,699	10/31/1994	CIRCUIT STRUCTURE AND METHOD FOR STRESS TESTING OF BIT LINES	Issued	Utility - ORG	NMXS-0202.00/US
L	IJ	5,517,148	5/14/1996	08/331,892	10/31/1994	LOW CURRENT DIFFERENTIAL LEVEL SHIFTER	Issued	Utility - ORG	NMXS-0201.00/US
اا	IJS	5,502,678	3/26/1996	08/315,337	9/30/1994	FULL MEMORY CHIP LONG WRITE TEST MODE	Issued	Utility - ORG	NMXS-0200.00/US
	Sn	5,495,446	2/27/1996	08/316,087	9/30/1994	PRE-CHARGED EXCLUSIONARY WIRED-CONNECTED PROGRAMMED REDUNDANT SELECT	Issued	Utility - ORG	NMXS-0199.00/US
	Sn	5,570,316	10/29/1996	08/438,276	5/10/1995	APPARATUS AND METHOD FOR ENABLING A BUS DRIVER WHEN A DATA SIGNAL IS VALID	Issued	Utility - DIV	Sn/10'8610-5XWN
	S	5,566,112	10/15/1996	08/288,334	8/10/1994	APPARATUS AND METHOD FOR ENABLING A BUS DRIVER WHEN A DATA SIGNAL IS VALID	lssued	Utility - ORG	Sn/00'8610-5XWN
	US	5,982,188	11/9/1999	08/282,047	7/29/1994	TEST MODE CONTROL CIRCUIT OF AN INTEGRATED CIRCUIT DEVICE	Issued	- Utility - ORG	Sn/00'26to-sxwn
	SS	5,589,783	12/31/1996	08/282,177	7/29/1994	VARIABLE INPUT THRESHOLD ADJUSTMENT	issued	Utility - ORG	SD/00'96TO-SXWN
	æ	5,493,532	2/20/1996	08/251,337	5/31/1994	INTEGRATED CIRCUIT MEMORY WITH DISABLED EDGE TRANSITION PULSE GENERATION DURING SPECIAL TEST MODE	Issued	Utility - ORG	NMXS-0195.00/US
	ß	5,521,880	5/28/1996	08/251,718	5/31/1994	INTEGRATED CIRCUIT MEMORY HAVING CONTROL CIRCUITRY FOR SHARED DATA BUS	issued	Utility - ORG	NMXS-0194.00/US
	ıs	5,455,799	10/3/1995	08/267,666	6/29/1994	CIRCUIT WHICH PROVIDES POWER ON RESET DISABLE DURING A TEST MODE	Issued	Utility - ORG	NMXS-0193.00/US
	ß	5,583,816	12/10/1996	08/267,667	6/29/1994	LONG WRITE TEST	lssued	Utility - ORG	NMXS-0192.00/US
TENT	US	5,530,674	6/25/1996	08/235,161	4/29/1994	STRUCTURE CAPABLE OF SIMULTANEOUSLY TESTING REDUNDANT AND NON- REDUNDANT MEMORY ELEMENTS DURING STRESS TESTING OF AN INTEGRATED CIRCUIT MEMORY DEVICE	Issued	Utility - ORG	NMXS-0191.00/US
	S	5,471,157	11/28/1995	08/220,834	3/31/1994	INTEGRATED CIRCUIT WITH CENTRALIZED CONTROL OF EDGE TRANSITION DETECTION PULSE GENERATION	Issued	Utility - ORG	NMXS-0190.00/US
	S	5,517,455	5/14/1996	08/220,976	3/31/1994	INTEGRATED CIRCUIT WITH FUSE CIRCUITRY SIMULATING FUSE BLOWING	Issued	Utility ~ ORG	NMXS-0189.00/US
	SN	5,905,683	5/18/1999		5/15/1997	METHOD AND STRUCTURE FOR RECOVERING SMALLER DENSITY MEMORIES FROM LARGER DENSITY MEMORIES			NMXS-0188.04/US
	Country	PatentNo	IssueDate PatentNo Country		Ellebate LSempiNo		WatterStatus	MatterType	MTFDdtNo

Page 8 of 40

Ł	_
	=
	ϵ
	ለነ
	_

NMXS-0243.00/US	MMX5-0242.00/US	NMXS-0241.00/US	CO/OO'0#20-CYIAIN	MWX2-0230.00/02	NMX\$-0238.00/US	NMXS-0237.00/US	NMXS-0236.02/US	NMXS-0236.01/US	NWXS-0236.00/US	NMXS-0235.00/US	NMXS-0234.00/US	NMXS-0233.00/US	NMXS-0232.01/US	NMXS-0232.00/US	NMXS-0231.00/US	NMX5-0230.00/US	NMXS-0229.00/US	NMXS-0228.00/US	NMXS-0227.00/US	NMXS-0226.00/US	NMXS-0226.00/RE	NMXS-0225.00/US	NMXS-0224.01/US	NMXS-0223.00/US	NMXS-0222.00/US	NMXS-0221.00/US	NMXS-0220.00/US	NMXS-0219.00/US	Matterstype Matterstype Matterstatus
Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - DIV	Utility - DIV	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - CON	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	บซ์โล่y - ORG	Utility - ORG	Utility - ORG	Utility - REIS	Utility - ORG	Utility - CON	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	MatterType
Issued	Issued	Issued	Issued	Issued	issued	Issued	Issued	Issued	Issued	Issued	Issued	issued	Issued	Issued	Issued	Issued	Issued	Issued	Issued	Abandoned	Issued	Issued	issued	Issued	Issued	Issued	Issued	Issued	MatterStatus
PARALLEL-DICHOTOMIC SERIAL SENSING METHOD FOR SENSING MULTIPLE-LEVEL NON-VOLATILE MEMORY CELLS, AND SENSING CIRCUIT FOR ACTUATING SUCH METHOD	TIMESHARING INTERNAL BUS, PARTICULARLY FOR NON-VOLATILE MEMORIES	REFERENCE WORD LINE AND DATA PROPAGATION REPRODUCTION CIRCUIT FOR MEMORIES PROVIDED WITH HIERARCHICAL DECODERS	UNBALANCED LATCH AND FUSE CIRCUIT INCLUDING THE SAME	BOOST REGULATOR	SYSTEM FOR DETERMINING THE PROGRAMMED/NON PROGRAMMED STATUS OF A MEMORY CELL	DEVICE FOR GENERATING AND REGULATING A GATE VOLTAGE IN A NON-VOLATILE MEMORY	ROW DECODING CIRCUIT FOR A SEMICONDUCTOR NON VOLATILE ELECTRICALLY PROGRAMMABLE MEMORY AND CORRESPONDING METHOD	PROGRAMMABLE MEMORY AND CORRESPONDING METHOD	PROGRAMMABLE MEMORY AND CORRESPONDING METHOD	VOLTAGE REGULATOR FOR SEMICONDUCTOR NON-VOLATILE ELECTRICALLY PROGRAMMABLE MEMORY DEVICE	METHOD FOR SETTING THE THRESHOLD VOLTAGE OF A REFERENCE MEMORY CELL	PARALLEL PROGRAMMING METHOD OF MEMORY WORDS AND CORRESPONDING CIRCUIT	NEGATIVE WORD LINE VOLTAGE REGULATION CIRCUIT FOR ELECTRICALLY ERASABLE SEMICONDUCTOR MEMORY DEVICES	NEGATIVE WORD LINE VOLTAGE REGULATION CIRCUIT FOR ELECTRICALLY ERASABLE SEMICONDUCTOR MEMORY DEVICES	PLASH EEPROM WITH INTEGRATED DEVICE FOR LIMITING THE ERASE SOURCE VOLTAGE	CHARGE PUMP CIRCUIT WITH MULTIPLE BOOST STAGES	THRESHOLD DETECTING DEVICE	MODULATED SLOPE SIGNAL GENERATION CIRCUIT, PARTICULARLY FOR LATCH DATA SENSING ARRANGEMENTS	READING CIRCUIT FOR MEMORY CELL DEVICES HAVING A LOW SUPPLY VOLTAGE	SENSE CIRCUIT FOR SERIES BINARY SENSING OF MULTILEVEL NONVOLATILE STORAGE ELEMENT.	CIRCUIT AND METHOD FOR READING A MEMORY CELL THAT CAN STORE MULTIPLE BITS OF DATA	CIRCUIT FOR READING NON-VOLATILE MEMORIES	READING CIRCUIT FOR MULTILEVEL NON VOLATILE MEMORY CELL DEVICES	SERIAL DICHOTOMIC METHOD FOR SENSING MULTIPLE-LEVEL NON-VOLATILE MEMORY CELLS, AND SENSING CIRCUIT IMPLEMENTING SUCH METHOD	DIGITAL RAMP GENERATOR	RESISTANCE REFERENCE CIRCUIT	CHARGE PUMP TYPE OF NEGATIVE VOLTAGE GENERATOR CIRCUIT AND METHOD	AN ELECTRICALLY PROGRAMMABLE MEMORY WITH IMPROVED RETENTION OF DATA AND A METHOD OF WRITING DATA IN SAID MEMORY	Article Co O3 issuer raterits
7/31/1996	3/7/1997	3/27/1997	7/19/1996	1/21/1997	3/27/1997	12/30/1996	8/7/2000	12/2/1998	3/27/1997	9/30/1996	7/12/1996	9/30/1996	6/23/1997	6/19/1996	7/31/1996	7/19/1996	7/31/1996	7/19/1996	4/25/1996	1/29/1996	9/30/1999	7/31/1996	6/4/1997	1/29/1996	5/30/1996	12/21/1995	6/13/1996	12/18/1995	[Roate
08/690,059	08/813,687	08/835,033	08/684,406	08/787,494	08/827,409	08/775,111	09/633,334	09/203,937	08/824,616	08/720,491	08/679,656	08/722,378	08/881,713	08/665,862	08/692,936	08/684,192	08/688,956	08/684,431	08/638,976	08/592,939	09/410,164	08/690,530	08/869,072	08/593,650	08/652,710	08/576,881	08/663,524	08/573,897	SerialNa IssueDate
3/17/1998	8/20/2002	5/19/1998	8/19/1997	10/13/1998	1/26/1999	10/13/1998	11/20/2001	10/24/2000	12/8/1998	12/1/1998	7/21/1998	7/14/1998	7/6/1999	8/19/1997	1/14/2003	6/2/1998	12/8/1998	4/7/1998	12/2/1997	9/30/1997	9/30/1997	3/31/1998	11/17/1998	12/23/1997	6/30/1998	2/10/1998	11/24/1998	7/29/1997	IssueDate
5,729,490	6,438,669	5,754,483	5.659,498	5.821.806	5,864,513	5,822,247	6,320,792	6,137,725	5,848,013	5,844,404	5,784,314	5,781,474	5,920,505	5,659,502	6,507,067	5,760,497	5.847.584	5,737,268	5,694,363	5,673,221	RE38,166	5,734,610	5,838,612	5,701,265	5,774,390	5,717,323	5,841,314	5,652,720	PateriiNo L Country
SU	SU	Sn	US (S	5	SS	S	S	ĸ	ક્ક	SS	US.	ଞ	S	ន	us	SS	S	ଞ	US	SS	rs.	ઝ	SS	SJ	S	SS	US.	US.	Country

	US US		2/27/2001	09/407,135	9/27/1999	METHOD OF AVOIDING DISTURBANCE DURING THE STEP OF PROGRAMMING AND ERASING AN ELECTRICALLY PROGRAMMABLE, SEMICONDUCTOR NON-VOLATILE STORAGE DEVICE	issued	Utility - DIV	NMXS-0270.01/US
<u></u>			3/23/1999	08/978,665	11/26/1997	IMETHOD AND CIRCUIT FOR GENERATING A SYNCHRONIZING ATD SIGNAL	Issued	Utility - URG	CO/00'6970-CXMN
		5,818,763	10/6/1998	08/774,860	12/24/1996	ERASING METHOD FOR A NON-VOLATILE MEMORY	Issued	Utility - ORG	NMXS-0268.00/US
L	7 US	6,055,187	4/25/2000	09/209,319	12/9/1998	SENSING CIRCUITRY FOR READING AND VERIFYING THE CONTENTS OF ELECTRICALLY PROGRAMMABLE/ERASABLE NON-VOLATILE MEMORY CELLS	lssued	Utility - CON	NMXS-0267.01/US
	3 US	5,917,753	6/29/1999	08/845,916	4/29/1997	SENSING CIRCUITRY FOR READING AND VERIFYING THE CONTENTS OF ELECTRICALLY PROGRAMMABLE/ERASABLE NON-VOLATILE MEMORY CELLS	Issued	Utility - ORG	NMXS-0267.00/US
	o US	5,999,450	12/7/1999	08/853,756	5/8/1997	ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY DEVICE WITH TESTABLE REDUNDANCY CIRCUITS	Íssued	Utility - ORG	NMXS-0266.00/US
	us		12/29/1998	08/821,804	3/21/1997	SECTORIZED ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY DEVICE WITH REDUNDANCY	Issued	Utility - ORG	NMXS-0265.00/US
	SUS	6,097,628	8/1/2000	09/202,656	10/30/1996	MULTI-LEVEL MEMORY CIRCUIT WITH REGULATED WRITING VOLTAGE	issued	Utility - NSPCT	NMXS-0264.00/US
	8	5,986,921	11/16/1999	08/883,822	6/27/1997	CLOCK CIRCUIT FOR READING A MUTILEVEL NON VOLATILE MEMORY CELLS DEVICE	tssued	Utility - ORG	NMXS-0263.00/US
	US	6,101,121	8/8/2000	09/202,657	10/30/1996	MULTI-LEVEL MEMORY CIRCUIT WITH REGULATED READING VOLTAGE	Issued	Utility - NSPCT	NMXS-0262.00/US
	SU S	5,859,795	1/12/1999	08/791,348	1/30/1997	MULTI-LEVEL MEMORY CIRCUITS AND CORRESPONDING READING AND WRITING METHODS	issued	Utility - ORG	NMXS-0261.00/US
	S	5,923,975	7/13/1999	08/784,967	1/16/1997	FABRICATION OF NATURAL TRANSISTORS IN A NONVOLATILE MEMORY PROCESS	Issued	Utility - ORG	NMXS-0260.00/US
Ш	7 US	5,817,557	10/6/1998	08/792,893	1/31/1997	PROCESS OF FABRICATING TUNNEL-OXIDE NONVOLATILE MEMORY DEVICES	Issued	Utility - ORG	NMXS-0259.00/US
	US	5,926,416	7/20/1999	08/807,574	2/27/1997	ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY CELLS DEVICE FOR A REDUCED NUMBER OF PROGRAMMAING CYCLES	Issued	Utility - ORG	NWXS-0258.00/US
	SU	6,222,245	4/24/2001	08/739,997	10/30/1996	HIGH CAPACITY CAPACITOR AND CORRESPONDING MANUFACTURING PROCESS	Issued	Utility - ORG	NIWXS-0257.00/US
<u> </u>	us S	6,448,138	9/10/2002	09/548,782	4/13/2000	NONVOLATILE FLOATING-GATE MEMORY DEVICES, AND PROCESS OF FABRICATION	Issued	Utility - CON	NMXS-0256.01/US
<u></u>	US	5,977,591	11/2/1999	08/824,888	3/18/1997	HIGH-VOLTAGE-RESISTANT MOS TRANSISTOR, AND CORRESPONDING MANUFACTURING PROCESS	Issued	Utility - ORG	NMXS-0255.00/US
l	US	6,000,980	12/14/1999	08/807,113	12/13/1996	PROCESS FOR FABRICATING A MICROTIP CATHODE ASSEMBLY FOR A FIELD EMISSION DISPLAY PANEL	lssued	Utility - ORG	NMXS-0254.00/US
<u></u>	US.	5,838,619	11/17/1998	08/828,039	3/27/1997	METHOD AND APPARATUS FOR REDUNDANCY MANAGEMENT OF NON-VOLATILE MEMORIES	Issued	Utility - ORG	NMXS-0253.00/US
Ш	US	5,821,788	10/13/1998	08/790,832	1/30/1997	ZERO CONSUMPTION POWER-ON-RESET	Issued	Utility - ORG	NMXS-0252.00/US
		5,801,988	9/1/1998	08/835,031	3/27/1997	CIRCUIT FOR THE GENERATION OF A VOLTAGE AS A FUNCTION OF THE CONDUCTIVITY OF AN ELEMENTARY CELL OF A NON-VOLATILE MEMORY	Issued	Utility - ORG	NMXS-0251.00/US
<u></u> 1	SU	5,778,012	7/7/1998	08/671,848	6/28/1996	MEMORY DEVICE WITH IMPROYED YIELD AND RELIABILITY	Issued	Utility - ORG	NMXS-0250.00/US
Ш		5,905,387	5/18/1999	08/742,978	11/1/1996	ANALOG VOLTAGE-SIGNAL SELECTOR DEVICE	Issued	Utility - ORG	NMXS-0249.00/US
D /	ĸ	5,754,476	5/19/1998	08/751,299	10/31/1996	NEGATIVE CHARGE PUMP CIRCUIT FOR ELECTRICALLY ERASABLE SEMICONDUCTOR MEMORY DEVICES	Issued	Utility - ORG	NMXS-0248.00/US
<u> </u>	S	6,483,750	11/19/2002	09/768,744	1/23/2001	FLASH EEPROM WITH ON-CHIP ERASE SOURCE VOLTAGE GENERATOR	Issued	Utility - DIV	NMXS-0247.01/US
<u> </u>	۱	6,195,291	2/27/2001	08/687,145	7/24/1996	FLASH EEPROM WITH ON-CHIP ERASE SOURCE VOLTAGE GENERATOR	Issued	Utility - ORG	NMXS-0247.00/EIS
NT	Sn	6,157,054	12/5/2000	09/032,179	2/27/1998	VOLTAGE GENERATOR FOR ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY	Issued	Utility ~ DIV	NMXS-0246.01/US
	US.	5,793,679	8/11/1998	08/735,709	10/23/1996	VOLTAGE GENERATOR FOR ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY CELLS	lssued	Utility - ORG	NMXS-0246.00/US
	R	5,724,290	3/3/1998	08/774,110	12/24/1996	METHOD AND PROGRAMMING DEVICE FOR DETECTING AN ERROR IN A MEMORY	Abandoned	Utility - ORG	NMXS-0245.00/US
لــــــــــــــــــــــــــــــــــــــ	Sti	6,040,734	3/21/2000	7/2/1998 09/109,630 3/21/2000 6,040,734 US	7/2/1998	SUPPLY VOLTAGES SWITCHES CIRCUIT	Issued	Utility - CON	NMXS-0244.01/US
95	Country	PatentNo	IssueDate	SeraiNo	FileDate		To see the see that the see	Marror Type	

PATENT

SO	5,619,462	4/8/1997	08/509,158	7/31/1995	FAOLI DETECTION FOR ENTIRE WAFER STRESS TEST	noncei	Contra	
55	5,592,422	1/7/1997	U8/4/6,658	CEET // /o			Utility - ORG	NMXS-0293.00/US
	5,700,200	7 7 7000	OS/ATE EES	6/7/1005		RG Issued	Utility - ORG	NMXS-0292.00/US
1	300 896 3	6/16/1998	08/484.491	6/7/1995		RG Issued	Othley - ORG	SO/00'TE20-CYIMIN
5	7/7 900	5/5/1000	08/464.082	6/5/1995	L	A	Utility - ORG	SO/0070570NN
	250 5530	5/5/1000	10C 897/6U	10000/5/5	POWER SUPPLY SWITCH REFERENCE CIRCUITRY	EIS Issued	Utility - REIS	NMXS-0290.00/RE
SS	5,576,656	11/19/1996	08/414,103	3/31/1995	YOLTAGE REGULATOR FOR AN OUTPUT DRIVER WITH REDUCED OUTPUT IMPEDANCE	RG Issued	Utility - ORG	NMXS-0289.00/US
ĸ	5,640,122	6/17/1997	08/464,551	6/5/1995	CIRCUIT FOR PROVIDING A BIAS VOLTAGE COMPENSATED FOR P-CHANNEL TRANSISTOR VARIATIONS	RG Issued	Utility - ORG	NMXS-0288.00/US
ន	5,793,247	8/11/1998	08/667,481	6/24/1996		ON Issued	Utility - CON	NMXS-0287.01/US
US	5,625,603	4/29/1997	08/477,244	6/7/1995		RG Issued	Utility - ORG	NMXS-0286.00/US
ક્ર	5,859,810	1/12/1999	08/826,009	3/27/1997		RG Issued	Utility - ORG	NMXS-0285.00/US
SS	5,831,891	11/3/1998	08/812,595	3/7/1997		RG Issued	Utility - ORG	NMXS-0284.00/US
8	6,212,096	4/3/2001	09/351,603	7/12/1999		ilV Issued	Utility - DIV	NMXS-0283.01/US
SJ	5,946,237	8/31/1999	08/826,489	3/27/1997		RG Issued	Utility - ORG	NMXS-0283.00/US
ន	5,854,770	12/29/1998	08/791,746	1/30/1997		RG Issued	Utility - ORG	NMXS-0282.00/US
S	6,148,413	11/14/2000	08/835,030	3/28/1997	A MEMORY UNDER TEST PROGRAMMING AND READING DEVICE	RG Issued	Utility - ORG	NMXS-0281.00/US
ß	5,751,654	5/12/1998	08/826,223	3/27/1997	DRIVER DEVICE FOR SELECTION LINES FOR A MULTIPLEXER, TO BE USED IN A WIDE RANGE OF SUPPLY VOLTAGES, PARTICULARLY FOR NON-VOLATILE MEMORIES	RG Issued	Utility - ORG	NMXS-0280.00/US
S	5,777,941	7/7/1998	08/853,732	5/9/1997	L	RG Issued	Utility - ORG	NMXS-0279.00/US
SS	5,878,049	3/2/1999	08/840,056	4/24/1997	CIRCUITS AND METHODS FOR READ-ENABLING MEMORY DEVICES SYNCHRONOUSLY WITHTHE REACHING OF THE MINIMUM FUNCTIONALITY CONDITIONS OF THE MEMORY CELLS AND READING CIRCUITS, PARTICULARLY FOR NON-VOLATILE MEMORIES	RG Issued	Utility - ORG	NMXS-0278.00/US
SU	5,917,768	6/29/1999	08/847,385	4/24/1997	MEMORY ARCHITECTURE FOR FLEXIBLE READING MANAGEMENT, PARTICULARLY FOR NON-VOLATILE MEMORIES, HAVING NOISE-IMMUNITY FEATURES, MATCHING DEVICE PERFORMANCE, AND HAVING OPTIMIZED THROUGHOUT	RG Issued	Utility - ORG	NMX5-0277.00/US
ଜ	6,210,994	4/3/2001	09/534,675	3/24/2000	PROCESS FOR FORMING AN EDGE STRUCTURE TO SEAL INTEGRATED ELECTRONIC DEVICES	IV Issued	Utility - DIV	NMXS-0276.01/US
US	6,057,591	5/2/2000	09/014,437	1/27/1998		RG Issued	Utility - ORG	NMXS-0276.00/US
ន	5,796,275	8/18/1998	08/791,700	1/30/1997			Utility - ORG	NMXS-0275.00/US
5	5.757.719	5/26/1998	08/869,208	6/5/1997	PAGE-MODE MEMORY DEVICE WITH MULTIPLE-LEVEL MEMORY CELLS	RG Issued	Utility - ORG	NMXS-0274.00/US
ଞ	6,005,411	12/21/1999	08/777,296	12/27/1996	MONOLITHICALLY INTEGRATED PROGRAMMABLE DEVICE HAVING ELEMENTARY MODULES CONNECTED ELECTRICALLY BY MEANS OF MEMORY CELLS OF THE FLASH TYPE	RG Issued	Utility - ORG	NMXS-0273.00/US
ଞ	5,784,319	7/21/1998	08/788,530	1/24/1997		RG Issued	Utility - ORG	NMXS-0272.00/US
US	5,721,707	2/24/1998	08/787,907	1/23/1997	ERASE VOLTAGE CONTROL CIRCUIT FOR AN ELECTRICALLY ERASABLE NON-VOLATILE MEMORY CELL	RG Issued	Utility - ORG	NMXS-0271.00/US
Country	PatentNo	SeraNo TsueDate Parentio Country	SerialNo :	FileDate		MILDORNO MatterType MatterStatus	Матеглу	MUJDOMNO

PATENT

	₫
	-
	Ç
и	
9	ē
	issued
	ä
	E
ı	

S	5,886,549	3/23/1999	08/792,962	1/24/1997	Issued DEVICE TO NEUTRALIZE AN ELECTRONIC CIRCUIT WHEN IT IS BEING POWERED OR DISCONNECTED	Utility - ORG	NMXS-0322.00/US
ß	5,950,224	9/7/1999	08/797,948	2/12/1997	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	Utility - ORG	NMX5-0321.00/US
SS	5,737,266	4/7/1998	08/738,231	10/25/1996	Issued METHODS AND APPARATUS FOR PROGRAMING CONTENT-ADDRESSABLE MEMORIES USING FLOATING-GATE MEMORY CELLS	Utility - ORG	NMXS-0320.00/US
SJ	5,801,577	9/1/1998	08/762,677	12/11/1996	Issued HIGH VOLTAGE GENERATOR	Utility - ORG	NMXS-0319.00/US
SU	6,034,895	3/7/2000	09/198,431	11/24/1998	Issued METHOD AND CIRCUIT FOR THE PROGRAMMING AND ERASURE OF A MEMORY	Utility - DIV	NMXS-0318.01/US
ᅜ	5,883,833	3/16/1999	08/703,811	8/27/1996	Issued METHOD AND CIRCUIT FOR THE PROGRAMMING AND ERASURE OF A MEMORY	Utility - ORG	NMXS-0318.00/US
SS	5,760,638	6/2/1998	08/664,083	6/13/1996	ISSUED PHASE GENERATOR CIRCUIT FOR CHARGE PUMP TYPE OF NEGATIVE SUPPLY CIRCUIT	Utility - ORG	NMXS-0317.00/US
SS	5,812,446	9/22/1998	08/623,044	3/28/1996	ISSUED METHOD AND APPARATUS FOR THE PROTECTION OF NON-VOLATILE MEMORY ZONES	Utility - ORG	NMXS-0316.00/US
S	5,557,573	9/17/1996	08/484,609	8/21/1995	Issued ENTIRE WAFER STRESS TEST METHOD FOR INTEGRATED MEMORY DEVICES AND CIRCUIT THEREFOR	Utility - ORG	NMXS-0315.00/US
rs.	5,633,828	5/27/1997	08/519,075	8/24/1995	Issued CIRCUITRY AND METHODOLOGY TO TEST SINGLE BIT FAILURES OF INTEGRATED CIRCUIT MEMORY DEVICES	Utility - ORG	NMXS-0314.00/US
ςŞ	5,896,336	4/20/1999	08/974,747	11/19/1997		Utility - CON	NMXS-0313.02/US
S	5,883,838	3/16/1999	08/929,987	9/15/1997	ISSUED DEVICE AND METHOD FOR DRIVING A CONDUCTIVE PATH WITH A SIGNAL	Utility - DIV	NMXS-0313.01/US
æ	5,619,466	4/8/1997	08/589,024	1/19/1996	ISSUED LOW-POWER READ CIRCUIT AND METHOD FOR CONTROLLING A SENSE AMPLIFIER	Utility - ORG	N/00/21ED-SXIVIN
SS	6,006,339	12/21/1999	09/020,430	2/9/1998	CIRCUIT AND METHOD FOR SETTING THE TIME DURATION OF A WRITE TO A MEMORY CELL	Utility - DIV	SO/10'11E0-SXWN
SS	5,864,696	1/26/1999	08/587,711	1/19/1996	Issued CIRCUIT AND METHOD FOR SETTING THE TIME DURATION OF A WRITE TO A MEMORY CELL	Utility - ORG	NMXS-0311.00/US
SS	5,848,018	12/8/1998	08/926,833	9/10/1997		Utility - CON	NMXS-0310.01/US
S S	5.828.622	10/27/1998	08/944,649	10/6/1997		Utility - DIV	NMXS-0309.01/US
¥ &	5,825,691	10/20/1998	08/858,788	5/19/1997	ISSUED CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL ISSUED CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL ISSUED CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL ISSUED CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL ISSUED CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL ISSUED CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL ISSUED CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL ISSUED CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL ISSUED CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL ISSUED CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL ISSUED CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL ISSUED CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL ISSUED CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL ISSUED CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL ISSUED CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL ISSUED CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL ISSUED CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL ISSUED CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL ISSUED CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL ISSUED CIRCUIT AND METHOD FOR THE PROPERTY OF THE	Utility - CON	NMXS-0309.001/US
ß	5,808,960	9/15/1998	08/858,295	5/19/1997	ISSUED CIRCUIT AND METHOD FOR TRACKING THE START OF A WRITE TO A MEMORY CELL	Utility - CON	NMXS-0307.01/US
ន	5,745,432	4/28/1998	08/589,141	1/19/1996	Issued WRITE DRIVER HAVING A TEST FUNCTION	Utility - ORG	SO/00'90E0-SXWN
US.	5,845,059	12/1/1998	08/588,762	1/19/1996	DATA-INPUT DEVICE FOR GENERATING TEST SIGNALS ON BIT AND BIT-COMPLEMENT LINES	Utility - ORG	NMXS-0305.00/US
S	5,657,292	8/12/1997	08/588,662	1/19/1996	Issued WRITE PASS THROUGH CIRCUIT	Utility - ORG	NMXS-0304.00/US
ន	5,790,462	8/4/1998	08/580,827	12/29/1995		Utility - ORG	NMXS-0303.00/US
\perp	5,801,563	9/1/1998	08/588,988	1/19/1996		Utility - ORG	NMXS-0302.00/US
5 8	5,798,980	8/25/1998	08/878.612	6/19/1997	ISSUED PIPELINED CHIP ENABLE CONTROL CIRCUITRY AND METHODOLOGY	Utility - DIV	NMXS-0301.01/US
	6,297,996	10/2/2001	09/457,558	12/9/1999		Utility - CON	NMXS-0300.02/US
S.	6,144,594	11/7/2000	08/587,709	1/19/1996	ISSUED TEST MODE ACTIVATION AND DATA OVERRIDE	Utility - ORG	NMXS-0300.00/US
S		3/18/1997	08/582,424	12/29/1995		Utility - ORG	NMXS-0299.00/US
	5,629,895	5/13/1997	08/521,800	8/31/1995		Utility - ORG	NMXS-0298.00/US
<u>ج</u> ا	١	7/15/1997	08/509,211	7/31/1995	Issued STRUCTURE FOR DESELECTING BROKEN SELECT LINES IN MEMORY ARRAYS	Utility - CIP	NMXS-0297.00/US
8	5,608,678	3/4/1997	08/509,351	7/31/1995	Issued COLUMN REDUNDANCY OF A MULTIPLE BLOCK MEMORY ARCHITECTURE	Utility - ORG	NMXS-0296.00/US
3 8	5,745,420	4/28/1998	08/833,582	4/7/1997		Otility - CON	NMXS-0294.01/US
Anune	ParentNo Co	Issuebate Parentno Country		Hiel	Martes areas and the same and t		
	The state of the s					ı	

	-					1 SALLI TERM ON ON OR SALL			
	us Us	5,838,623	11/17/1998	08/841,904	4/17/1997	METHOD FOR DETECTING REDUNDED DEFECTIVE ADDRESSES IN A MEMORY DEVICE WITH REDUNDANCY	ORG Issued	Utility - ORG	NMXS-0354.00/US
ļ,	7 us	5,959,917	9/28/1999	08/819,519	3/17/1997		ORG Issued	Utility - ORG	NWXS-0353.00/US
<u> </u>	ı us	6,175,521	1/16/2001	08/833,336	4/4/1997		ORG issued	Utility - ORG	NMXS-0352.00/US
<u></u>	US.	5,864,500	1/26/1999	08/835,296	4/7/1997	AUTO-SAVING CIRCUIT FOR PROGRAMMING CONFIGURATION ELEMENTS IN NON- VOLATILE MEMORY DEVICES	ORG Issued	Utility - ORG	Sn/001550-5XWN
<u></u>	US	5,754,473	5/19/1998	08/835,294	4/7/1997		ORG Issued	Utility - ORG	NMXS-0350.00/US
L	Γ	5,805,435	9/8/1998	08/824,958	3/27/1997			Utility - ORG	NMXS-0349.00/US
L	Γ	5,889,723	3/30/1999	08/826,008	3/27/1997			Utility - ORG	NMXS-0348.00/US
		5,886,945	3/23/1999	08/825,138	3/28/1997			Utility - ORG	NMXS-0347.00/US
L		6,078,523	6/20/2000	09/048,941	3/26/1998		-	Utility - DIV	NMXS-0346.01/US
	7 US	5,901,087	5/4/1999	08/828,790	3/27/1997		-	Utility - ORG	NMXS-0346.00/US
		5,959,476	9/28/1999	08/828,791	3/27/1997			Utility - ORG	NMX5-0345.00/US
		6,055,665	4/25/2000	08/816,766	3/18/1997			Utility - ORG	NMXS-0344.00/US
		5,815,464	9/29/1998	08/811,869	3/5/1997		-	Utility - ORG	NMXS-0343.00/US
L.		6,130,572	10/10/2000	09/012,331	1/23/1998			Utility - ORG	NMXS-0342.00/US
L		5,923,076	7/13/1999	08/811,577	3/5/1997		ORG Issued	Utility - ORG	NMXS-0341.00/US
<u></u>	ß	5,946,238	8/31/1999	08/877,066	6/17/1997	SINGLE-CELL REFERENCE SIGNAL GENERATING CIRCUIT FOR READING NONVOLATILE MEMORY		Utility - CON	NMXS-0340.00/US
		6,150,844	11/21/2000	08/898,811	7/23/1997		DRG Issued	Utility - ORG	NMXS-0339.00/US
L	us	6,060,753	5/9/2000	08/889,653	7/8/1997	LOW NOISE OUTPUT BUFFER FOR SEMICONDUCTOR ELECTRONIC CIRCUITS	-	Utility - ORG	NMXS-0338.00/US
<u> </u>	Su	6,215,329	4/10/2001	08/899,228	7/23/1997	OUTPUT STAGE FOR A MEMORY DEVICE AND FOR LOW VOLTAGE APPLICATIONS		Utility - ORG	NMXS-0337.00/US
	Γ	6,075,402	6/13/2000	08/946,727	10/8/1997			Utility - ORG	NMXS-0336.00/US
	US	6,016,073	1/18/2000	08/965,068	11/5/1997)RG Issued	Utility - ORG	SD/00'5EE0-5XWN
<u> </u>		6,184,741	2/6/2001	08/900,165	7/28/1997	ed BIDIRECTIONAL CHARGE PUMP GENERATING EITHER A POSITIVE OR NEGATIVE VOLTAGE		Utility - ORG	NMXS-0334.00/US
	SS	6,590,247	7/8/2003	09/916,954	7/27/2001		ON Issued	Utility - CON	NMXS-0333.01/US
	ક્ર	5,805,500	9/8/1998	08/877,921	6/18/1997	ed CIRCUIT AND METHOD FOR GENERATING A READ REFERENCE SIGNAL FOR NONVOLATILE MEMORY CELLS)RG Issued	Utility - ORG	NMXS-0332.00/US
<u> </u>	SS.	5,903,498	5/11/1999	08/877,927	6/18/1997	ed LOW-SUPPLY-VOLTAGE NONVOLATILE MEMORY DEVICE WITH VOLTAGE BOOSTING	RG Issued	Utility - ORG	NMXS-0331.00/US
ــــــــــــــــــــــــــــــــــــــ	Sn	6,128,225	10/3/2000	08/879,017	6/18/1997			Utility - ORG	Sn/00'02:09-5XWN
	US	6,094,073	7/25/2000	09/432,642	11/2/1999		1	Utility - DIV	NMXS-0329 01/US
L	US	6,018,255	1/25/2000	08/862,563	5/23/1997		-	Utility - ORG	NMXS-0329.00/US
L	SD	5,859,797	1/12/1999	08/846,753	4/30/1997	BIASING CIRCUIT FOR UPROM CELLS WITH LOW VOLTAGE SUPPLY	RG Issued	Utility - ORG	NMXS-0327-00/US
	SS	5,822,259	10/13/1998	08/846.755	4/30/1997		-	Utility - ORG	NMXS-0326.00/US
_L -\	5 2	5,939,933	7/77/1999	08/805,/48	5/30/1997			Utility - ORG	NMXS-0325.00/US
⊥_ IT	S S	5,881,001	3/9/1999	08/825,098	3/27/1997	DATA SENSING TIMING MODULATING CIRCUIT, PARTICULARLY FOR NON-VOLATILE MEMORIES	RG Issued	Utility - ORG	NMXS-0324.00/US
1	SO	6,074,916	6/13/2000	09/164,761	10/1/1998			Utility - DIV	NMXS-03Z3.01/US
1	CS	5,850,092	12/15/1998	08/833,925	4/10/1997		RG Issued	Utility - ORG	NMXS-0323.00/US
L	SS	6,125,022	9/26/2000		11/17/1998	DEVICE TO NEUTRALIZE AN ELECTRONIC CIRCUIT WHEN IT IS BEING POWERED OR DISCONNECTED	1	Utility - CON	NMXS-0322.01/US
	Country	PatentNo	SqueDate PatentNo Country	SeraiNo	TileDate	The state of the s		Matterilarie	NITERAN

ı	
l	×.
	Ħ
ŀ	Ħ.
ŀ	➣
ı	
l	S
	issued
l	₹
	atents

S		6,081,911	6/27/2000	08/865,642	5/30/1997	Issued DEVICE METHOD AND CIRCUIT ARCHITECTURE FOR TESTING A NON-VOLATILE MEMORY DEVICE	Utility - ORG Iss	Utility	NMXS-0374.00/US
S		5,949,666	9/7/1999	09/032,282	2/26/1998	ISSUED STAIRCASE ADAPTIVE VOLTAGE GENERATOR CIRCUIT	Utility - ORG Iss	Utility	NMXS-0373.00/US
Ş	SU OS	5,973,966	10/26/1999	09/203,798	12/1/1998	READING CIRCUIT FOR SEMICONDUCTOR MEMORY CELLS		Utility	NMXS-0372.01/US
Ş		5,883,837	3/16/1999	08/940,115	9/29/1997	Issued NEADING CIRCUIT FOR SEMICONDUCTOR MEMORY CELLS		Utility	NMXS-0372.00/US
S	Sn 6	6,630,739	10/7/2003	09/687,217	10/13/2000	Abandoned PLANARIZATION STRUCTURE AND METHOD FOR DIELECTRIC LAYERS		Utility	NMXS-0371.01/US
V.	7 US	6,156,637	12/5/2000	08/997,403	12/23/1997	Abandoned PLY STRUCTURE METHOD OF PLANARIZING A SEMICONDUCTOR DEVICE BY DEPOSITING A DIELECTRIC	Utility - ORG Aban	Utility	NMXS-0371.00/US
S	ı us	5,994,231	11/30/1999	08/996,920	12/23/1997	PROCESS FOR DEPOSITING A STRATIFIED DIELECTRIC STRUCTURE FOR ENHANCING THE PLANARITY OF SEMICONDUCTOR ELECTRONIC DEVICES	Utility - ORG Iss	Utility	NMXS-0370.00/US
<i>V</i> 1	s us	6,841,445	1/11/2005	10/792,308	3/3/2004	Issued METHOD OF MAKING FLOATING GATE NON-VOLATILE MEMORY CELL WITH LOW ERASING VOLTAGE HAVING DOUBLE LAYER GATE DIELECTRIC	Utility - DIV	Utility	NMXS-0369.04/US
<i>01</i>	us t	6,710,394	3/23/2004	10/158,706	5/30/2002	Issued PRASING VOLTAGE HAVING DOUBLE LAYER GATE DIELECTRIC	Utility - DIV	Utility	NWXS-0369.03/US
, , , , , , , , , , , , , , , , , , ,	4 us	6,399,444	6/4/2002	09/521,876	3/8/2000	Issued METHOD OF MAKING FLOATING GATE NON-VOLATILE MEMORY CELL WITH LOW ERASING VOLTAGE	Utility - DIV lss	Utility	NMXS-0369.02/US
J,	o us	6,147,380	11/14/2000	09/521,867	3/8/2000	Issued Floating gate non-volatile memory cell with low erasing voltage and having different potential barriers	Utility - DIV lss	Utility	SO/10.69E0-5XMN
	ı us	6,054,731	4/25/2000	08/940,856	9/29/1997	ISSUED FLOATING GATE NON-VOLATILE MEMORY CELL WITH LOW ERASING VOLTAGE AND MANUFACTURING METHOD	Utility - ORG lssi	Utility	SU/00.69E0-5XWN
	o us	6,472,750	10/29/2002	09/645,711	8/24/2000	PROCESS FOR REALIZING AN INTERMEDIATE DIELECTRIC LAYER FOR ENHANCING THE PLANARITY IN SEMICONDUCTOR ELECTRONIC DEVICES	Utility - DIV	Utility	NMXS-0368.01/US
	2 US	6,239,042	5/29/2001	08/987,454	12/9/1997	PROCESS FOR REALIZING AN INTERMEDIATE DIELECTRIC LAYER FOR ENHANCING THE PLANARITY IN SEMICONDUCTOR ELECTRONIC DEVICES		Utility - ORG	Sn/00'89E0-5XWN
	S.	5,854,762	12/29/1998	08/961,368	10/30/1997	ISSUED PROTECTION CIRCUIT FOR REDUNDANCY REGISTER SET-UP CELLS OF ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY DEVICES	Utility - ORG . Issu	Utility	NMXS-0367.00/US
		5,905,678	5/18/1999	08/934,499	9/19/1997	ISSUED CONTROL CIRCUIT OF AN OUTPUT BUFFER	Utility - ORG Issi	Utility	NMXS-0366.00/US
	Sn (6,046,619	4/4/2000	08/900,424	7/25/1997	ISSUED ASYMMETRICAL PULSIVE DELAY NETWORK		Utility - ORG	NMXS-0365.00/US
	2 US	6,252,802	6/26/2001	09/636,397	8/9/2000	ISSUED PLOATING GATE MOS TRANSISTOR CHARGE INJECTION CIRCUIT AND COMPUTATION DEVICES INCORPORATING IT		Utility - CON	NMXS-0364.02/US
	Sn i	6,236,592	5/22/2001	09/373,813	8/13/1999	ISSUED FLOATING GATE MOS TRANSISTOR CHARGE INJECTION CIRCUIT AND COMPUTATION DEVICES INCORPORATING IT		Utility - CON	NMXS-0364.01/US
		5,946,235	8/31/1999	08/940,278	9/30/1997			Utility - ORG	NMXS-0364.00/US
Ш	SO	5,999,445	12/7/1999	08/916,874	8/22/1997	ISSUED MULTILEVEL NON VOLATILE MEMORY DEVICE		Utility - ORG	NMXS-0363.00/US
	Sn	5,886,925	3/23/1999	08/877,922	6/18/1997	READ CIRCUIT AND METHOD FOR NONVOLATILE MEMORY CELLS WITH AN EQUALIZING STRUCTURE		Utility - ORG	NMXS-0362.00/US
	US	6,061,273	5/9/2000	08/835,347	4/7/1997		- ORG Issued	Utility - ORG	Sn/00°1980-5XMN
	US	5,831,915	11/3/1998	08/868,213	6/3/1997	Issued MEMORY DEVICE WITH CLOCKED COLUMN REDUNDANCY		Utility - ORG	NMX5-0360.00/US
		5,968,183	10/19/1999	08/868,214	6/3/1997	SEMICONDUCTOR MEMORY DEVICE WITH CLOCKED COLUMN REDUNDANCY AND TIME-SHARED REDUNDANCY DATA TRANSFER APPROACH	- ORG Issued	Utility - ORG	รก/00'6580-รมพุพ
[FN	SS	5,867,504	2/2/1999	08/869,367	6/5/1997		- ORG Issued	utility - ORG	Sn/00'85E0-5XWN
<u> </u>	SJ	5,864,562	1/26/1999	08/869,859	6/5/1997			Utility - ORG	NMXS-0357.00/US
	Sn	5,812,467	9/22/1998	08/841,903	4/17/1997			Utility - ORG	NMXS-0356.00/US
Ц.		5,889,710	3/30/1999	08/842,835	4/17/1997		- ORG Issued	Utility - ORG	NMXS-0355.00/US
	ಜ	5,936,907	8/10/1999	09/183,469	10/30/1998	METHOD FOR DETECTING REDUNDED		Utility - CON	NMXS-0354.01/US
2	Count	PatentNo	Screen Patenting Country	SerialNo	Hiebare SerialNo	Shins	type MatterStatus	Мане	MITEDADO ManerType

ı	
	Edibit
l	➣
١	'n
	S
	ङ
	Ē
	œ.
	~
	79
	Ħ
	Œ
	⊒.
	ĸ

US	6,063,663	5/16/2000	09/139,909	8/26/1998	PROCESS FOR MANUFACTURING NON-VOLATILE MEMORIES	Issued	Utility - ORG	NMX5-0392.00/US
SS	5,959,902	9/28/1999	09/030,604	2/25/1998	VOLTAGE LEVEL SHIFTER DEVICE, PARTICULARY FOR A NONVOLATILE MEMORY	Issued	Utility - ORG	NMXS-0391.00/US
US.	5,888,836	3/30/1999	08/990,328	12/15/1997	PROCESS FOR THE REPAIR OF FLOATING-GATE NON-VOLATILE MEMORIES DAMAGED BY PLASMA TREATIMENT	Issued	Utility - ORG	NMXS-0390.00/US
SU	6,115,313	9/5/2000	09/302,231	4/29/1999	METHOD FOR SAVING DATA IN THE EVENT OF UNWANTED INTERRUPTIONS IN THE PROGRAMMING CYCLE OF A NONVOLATILE MEMORY, AND A NONVOLATILE MEMORY	Issued	Utility - ORG	NMXS-0389.00/US
ક્ર	5,915,185	6/22/1999	09/062,859	4/20/1998	METHOD OF PRODUCING MOSFET TRANSISTORS BY MEANS OF TILTED IMPLANTS	Abandoned	Utility - ORG	NMXS-0388.00/US
S	5,880,993	3/9/1999	08/941,882	9/30/1997	GATE NONVOLATILE MEMORY CELLS PARTICULARLY FLASH CELLS	Issued	Utility - ORG	NMXS-0387.00/US
띯	6,115,801	9/5/2000	09/049,858	3/27/1998	DEVICE USING MULTIFUNCTIONAL TERMINALS OF THE ORDER OF THE TOP OF THE ORDER OF THE	Issued	Utility - ORG	NMXS-0386.00/US
ß	6,353,243	3/5/2002	09/356,080	7/16/1999	MEMORY CELLS OF THE PROPERTY	Issued	Utility - DIV	NMXS-0385.01/US
æ	5,976,933	11/2/1999	08/897,799	7/21/1997	PROCESS FOR MANUFACTURING AN INTEGRATED CIRCUIT COMPRISING AN ARRAY OF MEMORY CELLS	Issued	Utility - ORG	NMXS-0385.00/US
ន	6,284,585	9/4/2001	09/387,103	8/13/1999	ELECTRONIC MEMORY DEVICE HAVING BIT LINES WITH BLOCK SELECTOR SWITCHES	Issued	Utility - DIV	NMXS-0384.02/US
SS	6,101,124	8/8/2000	09/327,111	6/7/1999	MEMORY BLOCK FOR REALIZING SEMICONDUCTOR MEMORY DEVICES AND CORRESPONDING MANUFACTURING PROCESS	Issued	Utility - CON	NMXS-0384.01/US
ĸ	5,969,977	10/19/1999	08/998,854	12/29/1997	ELECTRONIC MEMORY DEVICE HAVING BIT LINES WITH BLOCK SELECTOR SWITCHES	Issued	Utility - ORG	NMXS-0384.00/US
S	6,380,582	4/30/2002	09/528,406	3/17/2000	AUTOALIGNED ETCHING PROCESS FOR REALIZING WORD LINES IN MEMORY DEVICES INTEGRATED SEMICONDUCTOR SUBSTRATES	ssued	Utility - DIV	NMXS-0383.01/US
S	6,130,165	10/10/2000	08/997,499	12/23/1997	AUTOALIGNED ETCHING PROCESS FOR REALIZING WORD LINES IN MEMORY DEVICES INTEGRATED SEMICONDUCTOR SUBSTRATES	Issued	Utility - ORG	NMXS-0383.00/US
S	5,864,503	1/26/1999	08/866,531	5/30/1997	METHOD FOR VERIFYING ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY CELLS OF AN ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY DEVICE AFTER PROGRAMMING	Issued	Utility - ORG	NMXS-0382.00/US
55	6,320,440	11/20/2001	09/611,258	7/6/2000	METHOD FOR SELECTIVELY ENABLING ALTERNATIVE CIRCUITS	Issued	Utility - DIV	NWX2-0381.02/US
SS	6,525,591	2/25/2003	09/558,956	4/25/2000	CIRCUIT FOR SELECTIVELY ENABLING ONE AMONG A PLURALITY OF CIRCUIT ALTERNATIVES OF AN INTEGRATED CIRCUIT	Issued	Utility - CON	SU/10.18E0-SXWN
ន	6,100,740	8/8/2000	08/957,685	10/24/1997	CIRCUIT FOR SELECTIVELY ENABLING ONE AMONG A PLURALITY OF CIRCUIT ALTERNATIVES OF AN INTEGRATED CIRCUIT	Issued	Utility - ORG	NWXS-0381.00/US
	5,793,699	8/11/1998	08/811,386	3/4/1997	CIRCUIT FOR THE GENERATION AND RESET OF TIMING SIGNAL USED FOR READING A MEMORY DEVICE	Issued	Utility - ORG	NWXS-0380.00/US
5	6,188,121	2/13/2001	09/119,115	7/20/1998	HIGH VOLTAGE CAPACITOR	Issued	Utility - ORG	NMXS-0379.00/US
S	6,071,778	6/6/2000	09/389,955	9/3/1999	MEMORY DEVICE WITH A MEMORY CELL ARRAY IN TRIPLE WELL, AND RELATED MANUFACTURING PROCESS	Issued	Utility - DIV	NMXS-0378.01/US
S.	5,990,526	11/23/1999	09/027,343	2/20/1998	MEMORY DEVICE WITH A MEMORY CELL ARRAY IN TRIPLE WELL, AND RELATED MANUFACTURING PROCESS	Issued	Utility - ORG	NMXS-0378.00/US
S	5,903,166	5/11/1999	08/811,548	3/4/1997	CIRCUIT FOR IMMUNIZING AN INTEGRATED CIRCUIT FROM NOISE AFFECTING ENABLE SIGNALS OF THE INTEGRATED CIRCUIT	Issued	Utility - ORG	NMXS-0377.00/US
S	5,914,901	6/22/1999	08/866,283	5/30/1997	INTEGRATED CIRCUIT FOR GENERATING INITIALIZATION SIGNALS FOR MEMORY CELL SENSING CIRCUITS	Issued	Utility - ORG	NMXS-0376.00/US
US US	劉文	11/16/1999	08/960,926	10/30/1997	\perp		Utility - ORG	NMXS-0375.00/US
Section Control	8	Terror and the second s	SemalNo		is a state of the	MatterStatus	MatterType	ONDOCTIM

Page 16 of 40

ı	=
ı	
ı	~
ı	-
ı	
ı	>
ı	
ı	- 1
ı	
	10
	-
	72
	v
	œ
	≖
	召
	2
	=
	7
	411
	===
	×
	40
	3
	₮
	ы

NMXS-0425.00/US Utility - ORG	odity one	+	NMYS-0422.00/US UBIRY- ORG	+	+	-	-	+	NMXS-0417.00/US Utility - ORG	NMX-0416 00/18 11/18/2- ORG		NMXS-0414.00/US Utility - ORG	NMXS-0413.00/US Utility - ORG	MINIAS-U412.00/US Utility - URG	+	+	+	-	NMXS-0407.00/US Utility - ORG	NMXS-0405.00/US Utility - ORG	╁	NMXS-0404.00/US Utility - CIP	NMXS-0403.00/US Utility - ORG	NMXS-0403.00/RE Utility - REIS	NMXS-0402.00/US Utility - CIP	_		NMXS-0399.02/US Utility - DIV	NMXS-0399.01/US Utility - DIV	NMXS-0399.00/US Utility - ORG	<u> </u>		-	\vdash	<u> </u>	MIT-DektNor Manemype
Issued	Issued	-	1	1	1		135000	+	+	+		Issued	issued	sued		1	-	Issued	Issued	Issued		Issued	Issued	Issued	Issued	Issued	issued	Issued	Issued	issued	issued	Issued		Issued	Issued	Matternype
WORD ADDRESSABLE FLOATING-GATE MEMORY COMPRISING A REFERENCE VOLTAGE GENERATOR CIRCUIT FOR THE VERIFICATION OF THE CONTENTS OF A WORD	PAGE-WRITE INDICATOR FOR NON-VOLATILE MEMORY	KING USCILLATOR USING CMOS TECHNOLOGY	METHOD AND DEVICE FOR THE FILTERING OF A PULSE SIGNAL	DIFFERENTIAL AMPLIFIER IN A MOS TRANSISTORS STRUCTURE	LOAD PUMP TYPE OF VOLTAGE GENERATOR CIRCUIT	CURRENTS	A SEAD CIBOLITI SOO MEMORY ADAPTED TO THE SEASON OF THE SE	MEMORY WITH BEAD DROTTECTED TOWER AL KEADING OF A MEMORY	MATTER AND DEVICE FOR THE PREDICTIVE READING OF A MEMORY	ELECTRICALLY ERASABLE FLOATING-GATE MEMORY ORGANIZED IN WORDS	OSCILLATOR AND SWITCH-OVER CONTROL CIRCUIT FOR A HIGH-VOLTAGE GENERATOR.	OSCILLATOR AND SWITCH-OVER CONTROL CIRCUIT FOR A HIGH-VOLTAGE GENERATOR	DEVICE AND METHOD FOR POWER-ON/POWER-OFF CHECKING OF AN INTEGRATED CIRCUIT	MEMORY WITH IMPROVED READING TIME	DEVICE FOR THE PROTECTION OF STORED DATA USING A TIME DELAY CIRCUIT	CURRENT REFERENCE DEVICE IN INTEGRATED CIRCUIT FORM	DEVICE FOR THE PROTECTION OF STORED DATA	READ CIRCUIT FOR NON-VOLATILE MEMORY WORKING WITH A LOW SUPPLY VOLTAGE	ELECTRICALLY MODIFIABLE MULTILEVEL NON-VOLATILE MEMORY COMPRISING INTERNAL REFRESH MEANS	PARALLEL-ACCESS MEMORY AND METHOD	DEVICE FOR READING CELLS OF A MEMORY	INTEGRATED CIRCUIT THAT SUPPORTS AND METHOD FOR WAFER-LEVEL TESTING	EDGE TRANSITION DETECTION CIRCUITRY FOR USE WITH TEST MODE OPERATION OF AN INTEGRATED CIRCUIT MEMORY DEVICE	EDGE TRANSITION DETECTION CIRCUITRY FOR USE WITH TEST MIDDE OPERATION OF AN INTEGRATED CIRCUIT MEMORY DEVICE	CIRCUIT AND METHOD FOR SELECTING A SIGNAL	SENSE AMPLIFIER CONTROL OF A MEMORY DEVICE	INPUT DELAY CONTROL	INTEGRATED CIRCUIT DEVICE HAVING A BURN-IN MODE FOR WHICH ENTRY INTO AND EXIT FROM CAN BE CONTROLLED	INTEGRATED CIRCUIT DEVICE HAVING A BURN-IN MODE FOR WHICH ENTRY INTO AND EXIT FROM CAN BE CONTROLLED	BURN-IN STRESS TEST MODE	EXTERNAL WRITE PULSE CONTROL METHOD AND STRUCTURE	LOW CURRENT CRYSTAL OSCILLATOR WITH FAST START-UP TIME	MULTIPLE ACCESS MEMORY DEVICE	SWITCHING MASTER SLAVE CIRCUIT	METHOD OF MANUFACTURING AN EPROM MEMORY DEVICE HAVING MEMORY CELLS ORGANIZED IN A TABLECLOTH MATRIX	Hile The Source Calcula
3/6/1998	1/20/1998	1/12/1998	5/29/1998	11/6/1998	4/13/1998	2/27/1998	12/19/1997	12/16/1997	12/16/1997	3/24/1999	5/25/2000	12/22/1997	12/18/1997	10/24/1997	8/21/1997	1/30/1997	8/21/1997	9/22/1997	10/24/1997	5/9/1997	6/12/1997	9/17/1996	12/21/1996	5/9/2002	11/27/1996	4/25/1997	12/23/1996	8/17/2001	1/27/2000	12/21/1996	12/21/1996	5/3/1996	12/31/1996	1/19/1996	8/27/1998	Hebate
09/035,654	880,600/60	09/005,722	09/087,478	09/188,071	09/059,088	09/031,748	08/994,889	08/991,428	08/991,693	09/275,327	09/578,778	08/995,667	08/993,071	08/957,666	08/915,855	08/791,383	08/916,054	08/934,696	08/957,715	08/853,526	08/873,502	08/710,357	08/771,643	10/145,606	08/758,587	08/844,696	08/780,053	09/931,820	09/491,664	08/771,645	08/771,642	08/642,271	08/775,664	08/588,648	09/141,849	SerialNo
9/14/1999	9/28/1999	10/3/2000	10/12/1999	10/31/2000	10/19/1999	3/30/1999	12/14/1999	1/23/2001	10/24/2000	8/1/2000	4/16/2002	11/14/2000	8/28/2001	2/9/1999	9/12/2000	5/11/1999	7/28/1998	1/12/1999	4/11/2000	7/4/2000	7/13/1999	9/15/1998	5/9/2000	5/9/2000	3/14/2000	9/28/1999	2/17/1998	2/11/2003	10/30/2001	3/14/2000	6/9/1998	9/8/1998	7/21/1998	7/21/1998	12/4/2001	Biedate Seralivo Issuebate Batenno Commo
5,953,253	5.959.886	6.127.898	5,966,034	6 140 876	5,969,961	5,889,702	6,002,619	6,178,490	6,138,220	6,097,631	6,373,311	6,147,566	6,281,723	5,870,336	6,119,210	5,903,141	5,787,040	5,859,798	6,049,497	6,085,280	5,923,590	5,808,947	6,059,450	RE40,282	6,037,799	5,959,910	5,719,445	6,518,746	6,310,485	6,037,792	5,764,592	5,805,027	5,784,331	5.783.958	6,326,266	PatentNo
US	55	5	5 3	<u> </u>	S	SN	US	SU	US	ß	SU	ß	S	S.	SS	ß	S	SU	US	SS	ន	Sn	ß	SS	ક્ર	SS	3	S	ડ	S	SS	SS	S	S	US.	Country

PATENT

L	US.	6,197,606	3/6/2001	09/108,439	7/1/1998	DETERMINATION OF THE THICKNESS OF A DENUDED ZONE IN A SILICON WAFER	Abandoned	Utility - ORG	CO/00454-00/05
	US	5,994,948	11/30/1999	08/921,930	8/27/1997	CWOS IWIN-10B NEGATIVE VOLIAGE SWITCHING ARCHITECTURE	133460	2000	מומטר מבדע ממחומ
	SS	5,926,059	7/20/1999	08/927,391	8/27/1997	CMOS TANIA THE NECKTHAS CONTROL CONTROL OF THE CONT	locales.	Utility - ORG	NMXS-0453.00/US
I	æ	6,401,164	6/4/2002	09/159,322	9/23/1998	SECTOR ADDRESSES SECTOR ADDRESSES	Issued	Utility - ORG	NMXS-0451.00/US
	ឆ	6,233,046	5/15/2001	09/343,207	6/29/1999	METHOD OF MEASURING THE THICKNESS OF A LAYER OF SILICON DAMAGED BY PLASMA ETCHING	Issued	Utility - ORG	NMXS-0450.00/US
]	æ	6,069,822	5/30/2000	09/181,230	10/27/1998	PARTICULAR FLASH MEMORIES AND EEPROMS	Issued	Utility - ORG	NMXS-0449.00/US
	Su	6,362,658	3/26/2002	09/716,747	11/20/2000	DECODER FOR MEMORIES HAVING OPTIMIZED CONFIGURATION	Issued	Utility - ORG	NVIX3-0448.00/US
1	SU	5,973,959	10/26/1999	09/121,024	7/22/1998	CIRCUIT AND METHOD OF READING CELLS OF AN ANALOG MEMORY ARRAY, IN PARTICULAR OF THE FLASH TYPE	Issued	Utility - ORG	NMXS-0447.00/US
	S	6,122,200	9/19/2000	09/200,002	11/25/1998	SELECTIVE ERASING OF A SUB-GROUP OF ROWS OF A SECTOR	Issued	Utility - ORG	NMXS-0446.00/US
L	S	6,330,188	12/11/2001	09/413,383	10/6/1999	DATA READ CIRCUIT FOR NON YOLATILE MEMORY CELLS	Issued	Utility - URG	MMX2-0445.00/05
1	S	6,369,406	4/9/2002	09/311,258	5/13/1999	METHOD FOR LOCALIZING POINT DEFECTS CAUSING LEAKAGE CURRENTS IN A NON- VOLATILE MEMORY DEVICE	Abandoned	utillty - ORG	NMXS-0444.00/US
	Sn	6,081,448	6/27/2000	09/162,639	9/28/1998	CELLS WITH AUTOVERIFY	issued	Utility - ORG	NMXS-0443.00/US
LL	SU	6,195,286	2/27/2001	09/353,756	7/14/1999	CIRCUIT AND METHOD FOR READING A NON-VOLATILE MEMORY	Issued	Utility - ORG	NMX5-0442.00/US
	Sn	6,376,306	4/23/2002	09/459,754	12/10/1999	METHOD FOR FORMING NON VOLATILE MEMORY STRUCTURES ON A SEMICONDUCTOR SUBSTRATE	Issued	Utility - ORG	NMXS-0441.00/US
	S	6,598,190	7/22/2003	09/175,220	10/19/1998	MEMORY DEVICE GENERATOR FOR GENERATING MEMORY DEVICES WITH REDUNDANCY	Issued	Utility - ORG	NMXS-0440.00/US
	St	6,195,283	2/27/2001	09/076,013	5/11/1998	METHOD AND DEVICE FOR ANALOG PROGRAMMING OF NON-VOLATILE MEMORY CELLS	Issued	Utility - ORG	NMXS-0439.00/US
	S	6,187,683	2/13/2001	09/059,740	4/14/1998	METHOD FOR FINAL PASSIVATION OF INTEGRATED CIRCUIT	issued	Utility - ORG	NMX5-0438,00/US
1	Sn	6,437,395	8/20/2002	09/776,105	2/1/2001	PROCESS FOR THE MANUFACTURING OF AN ELECTRICALLY PROGRAMMABLE NON- VOLATILE MEMORY DEVICE	Issued	Utility - DIV	NMXS-0437.01/US
	SII	6,194,270	2/27/2001	09/130,720	8/6/1998	PROCESS FOR THE MANUFACTURING OF AN ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY DEVICE	Issued	Utility - ORG	NMXS-0437.00/US
	Sn	6,016,271	1/18/2000	09/141,250	8/27/1998	METHOD AND CIRCUIT FOR GENERATING A GATE VOLTAGE IN NON-VOLATILE MEMORY DEVICES	Issued	Utility - ORG	NMXS-0436.00/US
L	ES 8	6,212,128	4/3/2001	09/093,382	10/6/1999	SEMICONDUCTOR INTEGRATED CIRCUIT	Issued	Utility - ORG	NMXS-0435.00/US
_L -	Z 2	6.075.718	6/13/2000	09/039.588	3/16/1998	METHOD AND DEVICE FOR READING A NON-ERASABLE MEMORY CELL	Issued	Utility - ORG	NMX5-0434.00/US
	5	6,888,225	5/3/2005	10/525,501	4/1/1998	MEMORY DEVICE WITH REDUCED POWER DISSIPATION	Issued	Utility - ORG	NMXS-0433.00/US
	SI	6,060,932	5/9/2000	09/118,953	7/17/1998	PROCESS OF FINAL PASSIVATION OF AN INTEGRATED CIRCUIT DEVICE	Issued	Utility - CON	NMXS-0432.02/US
	US	6,141,254	10/31/2000	09/355,064	1/22/1998	METHOD FOR PROGRAMMING AN EPROM-FLASH TYPE MEMORY	Issued	Utility - NSPCT	NMXS-0430.02/US
	SS	5,991,199	11/23/1999	09/012,938	1/22/1998	DEVICE AND METHOD FOR THE PROGRAMMING OF A MEMORY	Issued	Utility - ORG	NMXS-0430.00/US
		6,279,058	8/21/2001	09/746,472	12/21/2000	SET OF TWO MEMORIES ON THE SAME MONOLITHIC INTEGRATED CIRCUIT	Abandoned	Utility - DIV	NMXS-0429 02/US
N	- S	6,205,512	1002/02/2	09/056,921	12/21/2000	SET OF TWO MEMORIES ON THE SAME MONOLITHIC INTEGRATED CIRCUIT	Abandoned	Utility - DIV	NMXS-0429.01/US
		6,104,644	8/15/2000	09/013,966	1/27/1998	CIRCUIT FOR THE DETECTION OF CHANGES OF ADDRESS	Abandanad	Utility - ORG	NMXS-0428.00/US
NA E	SU	5,862,075	1/19/1999	08/970,445	11/14/1997	DEVICE FOR PROTECTION AFTER A PAGE-WRITE OPERATION IN AN ELECTRICALLY PROGRAMMABLE MEMORY	Issued	Utility - ORG	NMXS-0427.00/US
	us	6,011,724	1/4/2000	08/980,195	11/26/1997	CIRCUIT AND METHOD FOR THE ERASURE OF A NON-VOLATILE AND ELECTRICALLY ERASABLE MEMORY	Issued	Utility - ORG	NMXS-0426.00/US
	Country	PatentNo	Espedate	Triedate SerialNo ssuedate parentno Gomtry	Tiebate	The state of the s	WatterStatus	Matterlype Matterstatus	MILEDEMNO

ı	=
ı	O
l	=
ı	
	7
	ŀ
	G,
	SS
	5
	ă

	αĭ
	7
	æ
	=
	a
	bi

SS	6,307,396	10/23/2001	09/231,130	12/30/1998	TIME THE PROPERTY OF THE PARTY			
SS	6,313,480	11/6/2001	09/209,049	12/9/1998	LOW CONSTINDITION THE CONTROL OF CAMERICAN THE STATE OF CONTROL OF CAMERICAN THE CAMERICAN THE CONTROL OF CAMERICAN THE CONTROL OF CAMERICAN THE CAMERICAN THE CONTROL OF CAMERICAN THE CONTROL OF CAMERICAN THE CAMERICAN T	Issued	Utility - ORG	NMXS-0480.00/US
US	6,009,041	12/28/1999	09/032,272	2/26/1998	STRUCTURE AND METHOD EOD STATUTE CONTROL STRUCTURE OF THE CONTROL STRUC	Issued	Utility - ORG	NMXS-0479.00/US
g	6,031,761	0007/67/7	CC7'C17 /cn	2 (2) (2)	METHOD AND CIRCUIT FOR TRIMMING THE INTERNAL TIMING CONDITIONS OF A	Issued	Utility - ORG	NMXS-0478.00/US
		10000	08/37F 3FC	3/24/1999	SWITCHING CIRCUIT HAVING AN OUTPUT VOLTAGE VARYING BETWEEN A REFERENCE VOLTAGE AND A NEGATIVE YOUT OC	Issued	Utility - ORG	NMXS-0477.00/US
3	6,304,490	10/16/2001	09/675,985	9/29/2000	MEMORY CELL INTEGRATED STRUCTURE WITH CORRESPONDING BIASING DEVICE	Abandoned	Utility - DIV	NMXS-0476.01/US
ន	6,151,251	11/21/2000	09/295,667	4/21/1999	MEMORY CELL INTEGRATED STRUCTURE AND CORRESPONDING BIASING DEVICE	Abandoned	Utility - ORG	NIVIXS-U4/6.U0/US
ଞ	6,157,225	12/5/2000	09/234,016	1/19/1999	DKIVING CIRCUIT WITH THREE OUTPUT LEVELS, ONE OUTPUT LEVEL BEING A BOOSTED LEVEL	Issued	Utility - ORG	NMXS-0475.00/US
su	6,237,104	5/22/2001	09/222,070	12/29/1998	SYNCHRONIZATION SIGNAL ATD FOR TIMING THE ACCESS TO A NON-VOLATILE MEMORY	Issued	Utility - ORG	NMXS-0474.00/US
æ	6,069,837	5/30/2000	09/222,022	12/29/1998	ROW DECODER CIRCUIT FOR AN ELECTRONIC MEMORY DEVICE, PARTICULARLY FOR LOW VOLTAGE APPLICATIONS	issued	Utility - ORG	NMXS-0473.00/US
ß	5,204,722	3/20/2001	09/218,796	12/21/1998	ELECTRONIC CIRCUIT FOR GENERATING A STABLE VOLTAGE SIGNAL FOR POLARIZING DURING A READING STEP UPROM MEMORY CELLS OPERATING AT LOW FEED VOLTAGE	issued	Utility - ORG	NMXS-0472.00/US
SS	6,285,614	9/4/2001	09/602,669	6/26/2000	VOLTAGE REGULATOR FOR SINGLE FEED VOLTAGE MEMORY CIRCUITS, AND FLASH TYPE MEMORIES IN PARTICULAR	Issued	Utility - DIV	NMXS-0471.01/US
ន	6,101,118	8/8/2000	09/196,204	11/20/1998	VOLTAGE REGULATOR FOR SINGLE FEED VOLTAGE MEMORY CIRCUITS, AND FLASH TYPE MEMORY IN PARTICULAR	Issued	Utility - ORG	NMXS-0471.00/US
us I	6,286,086	9/4/2001	09/220,127	12/23/1998	CORRESPONDING PROTECTED MEMORY DEVICE	Issued	Utility - ORG	NMXS-04/0.00/US
US	6,064,598	5/16/2000	09/275,694	3/24/1999	SWITCHING CIRCUIT	Issued	Othry - URG	11WA-0409.00/US
ន ខ	6,249,172	6/19/2001	09/275,200	3/24/1999	CIRCUIT FOR DISCHARGING A NEGATIVE POTENTIAL NODE TO GROUND, INCLUDING CONTROL OF THE DISCHARGE CURRENT	Issued	Utility - ORG	NMXS-0468.00/US
5	000 375 3	8/14/2001	09/239.908	1/29/1999	HIGH-VOLTAGE PUMP ARCHITECTURE FOR INTEGRATED ELECTRONIC DEVICES	Issued	Utility - ORG	NMXS-0467.00/US
s s	6,184,670	2/6/2001	09/186,498	11/4/1998	MEMORY CELL VOLTAGE REGULATOR WITH TEMPERATURE CORRELATED VOLTAGE GENERATOR CIRCUIT	Issued	Utility - ORG	NMXS-0465.00/US
SS	6,144,589	11/7/2000	09/186,758	10/13/1998	IMPROVED OUTPUT CIRCUIT FOR INTEGRATED CIRCUITS	İssued	Utility - ORG	NMXS-0464.00/US
SU	6,169,423	1/2/2001	09/186,496	11/4/1998	BOOSTING CIRCUIT PARTICI II ARY FOR A MEMORY DEVICE	Issued	Utility - ORG	NMXS-0463,00/US
8	067,670,8	0/15/2000	107,00x fco		METHOD AND CIRCUIT FOR REGILIATING THE LENGTH OF AN ATTO BLUCE SCOUN	Issued	Utility - ORG	NMXS-0462,00/US
	2075	0000/21/3	09/185 497	11/4/1998	METHOD AND CIRCUIT FOR GENERATING AN ATD SIGNAL TO REGULATE THE ACCESS	Issued	Utility - ORG	NMXS-0461.00/US
SO.	6,011,715	1/4/2000	09/185,906	11/3/1998	MULTILEVEL NONVOLATILE MEMORY MULTILEVEL NONVOLATILE MEMORY	issued	Utility - ORG	NMXS-0460.00/US
5	5.982.677	11/9/1999	09/163,755	9/30/1998	COMPENSATED VOLTAGE REGULATOR	Issued	Utility - ORG	NMXS-0459.00/US
SS	6,275,960	8/14/2001	09/212,896	12/16/1998	SELF-TEST AND CORRECTION OF LOSS OF CHARGE ERRORS IN A FLASH MEMORY, ERASABLE AND PROGRAMMABLE BY SECTORS THEREOF	Issued	Utility - ORG	NMXS-0458.00/US
SS	6,172,908	1/9/2001	09/169,239	10/8/1998	CONTROLLED HOT-ELECTRON WRITING METHOD FOR NON-VOLATILE MEMORY CELLS	Issued	Utility - ORG	NMXS-0457.00/US
us	6,242,971	6/5/2001	09/321,961	5/28/1999	MONOLITHICALLY INTEGRATED SELECTOR FOR ELECTRICALLY PROGRAMMABLE MEMORY CELL DEVICES	issued	Utility - ORG	NMXS-0456.00/US
US	6,028,793 US	2/22/2000	09/224,330	12/31/1998	HIGH VOLTAGE DRIVER CIRCUIT FOR A DECODING CIRCUIT IN MULTILEVEL NON-VOLATILE MEMORY DEVICES	issued	Utility - ORG	NMXS-0455.00/US
	Patentina	IssueDate	HEDate Senalvo Assuepare	Flebate.		MatterType - MatterStatus	MatterType	MTI-DOM:No

1	
1	
ı	-
	140
1	×
ı	
•	-3
ı	
	~
	Ψ.
ı	=-
	•
ı	_
,	ь
ı	-
F	1
ı	•
ı	,
ı	·
	"
	•
1	_
ı	<i>T</i>
н	74
ı	
ŀ	_
ı	둤
ŀ	æ
F	Ö.
н	***
ı	
ŀ	773
г	-7
ı	•
F	-
1	-
ı	150
ŀ	~
	=
	~
	U)

L	US	6,152,373	11/28/2000	09/157,060	8661/81/6	The second second second on contractices cut CANDS			
Ш		5,999,447	12/7/1999	09/199,671	11/25/1998		penssi	Utility - ORG	NMXS-0510.00/US
i	S	6,128,222	10/3/2000	09/173,136	10/15/1998		Issued	Utility - ORG	NWXS-0508.00/US
	Sn	5,995,416	11/30/1999	09/156,945	9/18/1998	VOLTAGE IN A NON-VOLATILE MEMORY NON YOLATILE ACADORIC TROCORDAY NON YOLATIC TROCORDAY NON YO	Issued	Utility - ORG	NMXS-0507.00/US
	S	6,040,994	3/21/2000	09/179,621	10/27/1998	METHOD FOR WRITING IN AN ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY	Issued	Utility - ORG	NMXS-0506.00/US
	S	6,034,889	3/7/2000	09/177,899	10/23/1998	ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY HAVING A PROTECTABLE ZONE AND AN ELECTRONIC SYSTEM INCLUDING THE MEMORY	Issued	Utility - ORG	NMXS-0505.00/US
		6,519,682	2/11/2003	09/205,598	12/4/1998	PIPELINED NON-BLOCKING LEVEL TWO CACHE SYSTEM WITH INHERENT TRANSACTION COLLISION-AVOIDANCE	Issued	Utility - ORG	NMXS-0504.00/US
	T	6,198,672	3/6/2001	09/257,684	2/26/1999		Issued	Utility - ORG	NMXS-0503.00/US
	7 8	6.064.594	5/16/2000	09/258,224	2/26/1999		Issued	Utility - ORG	NMXS-0502.00/US
\perp		6 130 844	10/10/2000	09/257.682	2/26/1999		issued	Utility - ORG	NMXS-0501.00/US
	1	6 465 050	10/15/2002	09/249.834	2/12/1999	SENSE AMPLIFER FOR LOW VOLTAGE MEMORIES	Issued	Utility ~ ORG	NMXS-0500.00/US
		6,271,571	8/7/2001	09/276,263	3/25/1999	UPROM MEMORY CELLS FOR NON-VOLATILE MEMORY DEVICES INTEGRATED ON SEMICONDUCTORS	issued	Utility - ORG	NN4XS-0499.00/US
		6.094.394	7/25/2000	09/256,603	2/23/1999		Issued	utility - ORG	NMXS-0498.00/US
	ž E	6,049,491	4/11/2000	09/256.648	2/23/1999		tssued	Utility - ORG	NMXS-0497.00/US
	T	6 122 719	10/17/2000	09/745 029	2/5/1999		Issued	Utility - ORG	NMXS-0496.00/US
		6,867,113	3/15/2005	09/191,743	8661/51/11	IN-SIT'U DEPOSITION AND DOPING PROCESS FOR POLYCRYSTALLINE SILICON LAYERS AND THE RESULTING DEVICE	Issued	Utility - ORG	NMXS-0495.00/US
	SS I	6,097,633	8/1/2000	09/182,843	10/29/1998	READ CIRCUIT FOR NON VOLATILE MEMORIES	Issued	Utility - ORG	NMXS-0494.00/US
		5.995.471	11/30/1999	09/087,399	5/29/1998	CIRCUIT AND METHOD FOR READING A MEMORY CELL	issued	Utility - ORG	NMXS-0493.00/US
		6,107,865	8/22/2000	09/429,964	10/29/1999	NSS SWITCHING SCHEME FOR BATTERY BACKED-UP SEMICONDUCTOR DEVICES	Abandoned	Utility - CON	NMXS-0492.01/US
	SS	5,995,444	11/30/1999	08/000,547	12/30/1997	EDGE TRANSITION DETECTION CONTROL OF A MEMORY DEVICE	Issued	Utility - ORG	NMXS-0491.00/US
	ĸ	6,208,705	3/27/2001	09/262,500	3/4/1999	SEMICONDUCTOR SEMICONDUCTOR	Issued	Utility - ORG	NMXS-0490.00/US
l	US	6,111,791	8/29/2000	09/322,644	5/28/1999	CIRCUIT DEVICE AND CORRESPONDING METHOD FOR PROGRAMMING A NONVOLATILE MEMORY CELL HAVING A SINGLE VOLTAGE SUPPLY	Issued	Utility - ORG	NMXS-0489.00/US
	υs	6,218,265	4/17/2001	09/336,089	6/18/1999	PROCESS FOR FABRICATING A SEMICONDUCTOR NON-VOLATILE MEMORY DEVICE WITH SHALLOW TRENCH ISOLATION (STI)	Issued	Utility - ORG	NMXS-0488.00/US
	SS	6,147,902	11/14/2000	09/320,315	5/26/1999	HIGH STORAGE CAPACITY NON-VOLATILE MEMORY	Issued	Utility - ORG	NMXS-0487.00/US
	SJ	6,372,597	4/16/2002	09/837,137	4/17/2001	METHOD FOR IMPROVING THE EFFECTIVENESS OF ESD PROTECTION IN CIRCUIT STRUCTURES FORMED IN A SEMICONDUCTOR SUBSTRATE	Issued	Utility - DIV	NMXS-0486.01/US
	S.	6,242,793	6/5/2001	09/231,129	12/30/1998	METHOD AND A CIRCUIT FOR IMPROVING THE EFFECTIVENESS OF ESD PROTECTION IN CIRCUIT STRUCTURES FORMED IN A SEMICONDUCTOR	Issued	Utility - ORG	NMXS-0486.00/US
ΡΔ	Ų.	6,266,222	7/24/2001	09/223,621	12/30/1998	ESD PROTECTION NETWORK FOR CIRCUIT STRUCTURES FORMED IN A SEMICONDUCTOR	Issued	Utility - ORG	NMXS-0485.00/US
TEI	S	6,091,642	7/18/2000	09/234,942	1/21/1999	METHOD FOR CONTROLLED ERASING MEMORY DEVICES, IN PARTICULAR ANALOG AND MULTI-LEVEL FLASH-EEPROM DEVICES	issued	Utility - ORG	NMXS-0484.00/US
JT	S	6,101,127	8/8/2000	09/229,474	1/13/1999	OPERATING VOLTAGE SELECTION CIRCUIT FOR NON-VOLATILE SEMICONDUCTOR MEMORIES	lssued	Utility-ORG	NMXS-0483.00/US
	SJ	6,587,914	7/1/2003	09/349,702	7/8/1999	NON-VOLATILE MEMORY CAPABLE OF AUTONOMOUSLY EXECUTING A PROGRAM	Issued	Utility - ORG	NMXS-0482.00/US
		42	9/11/2001	- 1	6/30/1999	MONOLITHICALLY INTEGRATED SELECTOR FOR ELECTRICALLY PROGRAMMABLE MEMORY CELLS DEVICES	issued	Utility - NSPCT	NMXS-0481.00/US
	Country	PatentNo	IssueDate	SeralNo IssueDate	FileDate 1	us day	WatterStatu	MatterType MatterStatus	MILDONNO

ı	9
ı	==
ı	•••
ı	ъ
ı	_
ı	1
ı	_
	€,
	L/A
	π
	7.
	**
	<u>-</u>
	æ
	Ω.
	70
	۸Ŧ
	₩.
	T.
	ıμ
	_
	-
	v

6,301,152 US				47 00 100	הכספריאווע פרא ווכד ואי איסיי			
Ī		10/9/2001	09/570,332	5/12/2000	METHOD FOR FORMING CONTACTLESS MOS TRANSISTORS AND REST IT TIME DEVICES	Issued	Utility - ORG	NMXS-0534.00/US
6,444,526 US		9/3/2002	09/419,403	10/14/1999	NON-VOLATILE MEMORY DEVICE WITH ROW REPLANDANCY	Issued	Utility - ORG	SU/00'EE50-5XWN
6,180,460 US		E007/05/T	Tenineten		SIMPLIFIED PROCESS FOR DEFINING THE TUNNEL AREA IN NON-ALIGNED, NON-	Issued	Utility - ORG	NMXS-0532.00/US
		1000	00/227 051	6/21/1999	PROCESS FOR MANUFACTURING OF A NON VOLATILE MEMORY WITH REDUCED RESISTANCE OF THE COMMON SOLIBLE HINES	Issued	Utility - ORG	NMXS-0531.00/US
		1/9/2001	09/344,425	6/25/1999	METHOD FOR FAST PROGRAMMING FLOATING GATE MEMORIES BY TUNNEL EFFECT	Issued	Utility - ORG	NMXS-0530.00/US
6,284,607 US		9/4/2001	09/411,134	10/1/1999	METHOD OF MAKING HIGH-VOLTAGE HV TRANSISTORS WITH DRAIN EXTENSION IN A CMOS PROCESS OF THE DUAL GATE TYPE WITH SILICIDE	Issued	Utility - ORG	NMXS-0529.00/US
6,255,163 US		7/3/2001	09/330,540	6/11/1999	FIX-CESS FOR MANUFACTURING SELECTION TRANSISTORS FOR NONVOLATILE SERIAL- FLASH, EPROM, EEPROM AND FLASH-EEPROM MEMORIES IN STANDARD OR AMG CONFIGURATION	ksued	Utility - ORG	NMXS-0528.00/US
6,495,455 US		12/17/2002	09/836,937	4/17/2001	METHOD FOR ENHANCING SELECTIVITY BETWEEN A FILM OF A LIGHT-SENSITIVE MATERIAL AND A LAYER TO BE ETCHED IN ELECTRONIC SEMICONDUCTOR DEVICE FABRICATION PROCESSES	lssued	Utility - DIV	NMXS-0527.01/US
6,461,922 US		10/8/2002	09/464,066	12/15/1999	TRANSISTORS IN AN INTEGRATED DEVICE WITH A MEMORY MATRIX MANUFACTURED BY MEANS OF A PROCESS FEATURING SELF-ALIGNED SOURCE (5AS) FORMATION AND JUNCTION SALICIDATION	Issued	Utility - ORG	NMXS-0526.00/US
6,300,181 US		10/9/2001	09/358,075	7/21/1999	TRANSISTORS WITH SALICIDED JUNCTIONS AND NON-SALICIDED RESISTORS METHOD FOR THE INTEGRATION OF RESISTORS	nssued	ounty - Ond	
6,420,769 US		7/16/2002	09/861,404	5/18/2001	LV TRANSISTORS WITH SALIGIBED JUNCTIONS PROCESS FOR MANUFACTURING AN ELECTRONIC DESIGNATIONS PROCESS FOR MANUFACTURING AN ELECTRONIC DESIGNATIONS	Issued	Ounty-Div	NMXS-052k 00/1 k
6,251,728 US		6/26/2001	09/359,923	7/22/1999	LV TRANSISTORS WITH SALICIDED JUNCTIONS DEVICES HAVING HY TRANSISTORS AND METHOD FOR MANUE ACTUBING ELECTRONIC DEVICES HAVING HY TRANSISTORS AND	Issued	Otsaty - ORG	MMXCDE24.00/03
		2/4/2003	09/894,975	6/27/2001	SEMICONDUCTOR MEMORY DEVICES	issued	ounty COM	אואאיר חבים המחור
T		7/4/2000	09/276,214	3/25/1999	CIRCUIT STRUCTURE FOR PROVIDING A HIFRARCHICAL DECONDER IN	100000	I triliby - CON	NMXS-0523.01/HS
		10/13/2009	11/033,776	1/12/2005	METHOD FOR BEADING A SHIPTING METHOD	Issued	Utility - ORG	NMXS-0522.00/US
SI 965 658 9		2/8/2005	09/779,956	2/9/2001	ELECTRONIC MEMORY CIRCUIT AND RELATED MANUFACTURING METHOD	Issued	Utility - DIV	NMXS-0521.02/US
		A/10/2	09/364 766	7/30/1999	ELECTRONIC MEMORY CIRCUIT AND RELATED MANUFACTURING METHOD	Issued	Utility - ORG	NMXS-0521.00/US
6,551,892 US		4/22/2003	09/891,438	6/25/2001	PROCESS FOR THE MANUFACTURE OF INTEGRATED DEVICES WITH GATE OXIDE PROTECTION FROM MANUFACTURING PROCESS DAMAGE, AND PROTECTION STRUCTURE THEREFOR	Issued	Utility - DIV	NMXS-0520.01/US
6,278,159 US		8/21/2001	09/344,426	6/25/1999	PROCESS FOR THE MANUFACTURE OF INTEGRATED DEVICES WITH GATE OXIDE PROTECTION FROM MANUFACTURING PROCESS DAMAGE, AND PROTECTION STRUCTURE THEREFOR	Issued	Utility - ORG	NMXS-0520.00/US
		8/1/2000	09/275,691	3/24/1999	VALUES OCCUPATION OF THE AIM OUTPUT VOLTAGE CHANGING AMONG FOUR POSSIBLE OCCUPATIONS OCCUPATI	Issued	Utility - ORG	MWIXS-OSTS:00/US
6.157.579 115		12/5/2000	09/295,263	4/20/1999	CIRCUIT FOR PROVIDING A READING PHASE AFTER POWER-ON-RESET	issued	Othey - Ong	100000000000000000000000000000000000000
T		1/30/2/000	09/322,460	5/28/1999	DEVICE AND METHOD FOR READING NONVOLATILE MEMORY CELLS	Issued	Utility - ORG	NMX5-0517-00/US
6,219,277 US		4/17/2001	09/300,527	6/1/1/999 6661/17/ 1		Issued	Utility - ORG	NMXS-0515.00/US
6,091,641 US		7/18/2000	09/195,276	11/18/1998		Abandoned	Utility - ORG	NMXS-0514.00/US
6,140,869 US		10/31/2000	09/234,194	1/20/1999	NON-VOLATILE MEMORY DEVICE AND METHOD FOR THE PROGRAMMING OF THE	Issued	Utility - ORG	NMXS-0513.00/US
	1999 5,	11/2/1999	09/179,635	10/27/1998	A MEMORY THAT USES FLOATING-GATE TRANSISTORS DEVICE FOR DEMONSH ATTING A RINARY STRANSISTORS	Issued	Utility - ORG	NMXS-0512.00/03
No Country	IssueDate PateniNo	IssueDate	SerialNo	FileDate SerialNo		NWAXCOZII ODZIG	I Killing Coop	NIMYC OF 11 OD/I IS

	s	6,222,775	4/24/2001	09/599,356	6/21/2000				
	æ	6,294,431	9/25/2001	09/547,520	4/12/2000	FLASH COMPATIBLE EEPROM	Issued	Utility - ORG	NMXS-0557.00/US
<u></u>	Sn	6,392,931	5/21/2002	09/449,168	11/24/1999	PROCESS OF MANUFACTURE OF A NON VOLATILE MEMORY WITH ELECTRIC	Issued	Utility - ORG	NMXS-0556.00/US
<u></u>					44 / 74 / 4600	METHOD FOR HIGH PRECISION PROGRAMMING NONVOLATILE MEMORY CELLS, WITH	Issued	Utility - ORG	NMXS-0555.00/US
	S	6,274,411	8/14/2001	09/469,849	12/21/1999	METHOD FOR MANUFACTURING ELECTRONIC DEVICES, COMPRISING NON-SALICIDED NON-VOLATILE MEMORY CELLS, NON-SALICIDED HV TRANSISTORS, AND LV TRANSISTORS WITH SALICIDED JUNCTIONS WITH FEW MASKS	Issued	Utility - ORG	NMXS-0554.00/US
	SS	6,232,753	5/15/2001	09/467,726	12/20/1999	LOADS BEING DRIVEN	Issued	Utility - ORG	May 20,000,00
	ᅜ	6,737,715	5/18/2004	10/090,978	3/4/2002	FIELD-EFFECT TRANSISTOR AND CORRESPONDING MANUFACTURING METHOD VOLTAGE REGILLATOR FOR CORRESPONDING MANUFACTURING METHOD	Issued	Onliny - DIV	NIVAXE DEED OUT IL
	US.	6,387,763	5/14/2002	09/442,834	11/18/1999	METHOD	issued	ounty - Ond	SIL TO CESO SAIMIN
	S	6,462,400	10/8/2002	09/483,656	1/14/2000	IMPROVED FIELD-EFFECT TRANSISTOR AND CORRESPONDING MAINTENANCE TO THE PROPERTY OF THE PROPERTY			NWXS-0550 ON/I IS
	S.	6,259,632	7/10/2001	09/491,475	1/19/2000	READING VOLTAGE IN NON-VOLATILE MEMORIES CHIP OI TI INE BAND (COB) STBI (CTIL) COBABETO COB TO THE WORD LINE CHIP OI TI INE BAND (COB) STBI (CTIL) COBABETO COB TO THE WORD LINE CHIP OI TI INE BAND (COB) STBI (CTIL) COBABTO COB TO THE WORD LINE CHIP OI TI INE BAND (COB) STBI (CTIL) COB TO THE WORD LINE COB TO THE WORD LINE COB TO THE	Issued	Utility - ORG	NMXS-0551.00/US
	S.	6,259,635	7/10/2001	09/491,476	1/19/2000	VOLTAGE IN NON-VOLATILE MEMORIES CAPACITYS COMPENSATION CIGATITY FOR THE RECEIN THE WORD LINE READING CAPACITYS COMPENSATION CIGATITY FOR THE RECEIN THE WORD LINE READING	Issued	Utility - ORG	NMXCDEED OUT IS
		6,195,289	2/27/2001	09/425,446	10/22/1999	CERTS CONTRACTOR OF THE PROPERTY CONTRACTOR OF	issued	Contract Circ	NAME OF AD DOUG
\perp	æ	6,350,637	2/26/2002	09/543,400	4/5/2000	DEVICE FOR READING ANALOIS NONVOLVELLO MUST RANGISTOR		I Hillay, Cin	NMXS-0548 00/11S
	LIS	6,169,691	1/2/2001	09/397,387	9/15/1999	METHOD OF EXPRICATION OF A MODIFIED MENIOR	issued	Utility - ORG	NMXS-0547.00/US
	SU	6,713,347	3/30/2004	10/158,424	5/29/2002	PERFORMANCE LOGIC CIRCUITRY METHOD FOR MAINTAINING THE MEMORY CONTENT OF NOW YOU ATTIC MEMORY		Itiliav - ORG	NMXS-0546.00/US
<u>L</u>	5	/00,01+,0	of the feet			PROCESS FOR INTEGRATING IN A SAME CHIP A NON-VOLATILE MEMORY AND A HIGH-	issued	Utility - DIV	NMXS-0545.01/US
		6 410 297	6/25/2002	09/449.044	11/24/1999	PROCESS FOR INTEGRATING IN A SAME CHIP A NON-VOLATILE MEMORY AND A HIGH- PERFORMANCE LOGIC CIRCUITRY	Issued	Utility - ORG	NMXS-0545.00/US
	us	6,128,228	10/3/2000	09/438,823	11/12/1999	CIRCUIT FOR HIGH-PRECISION ANALOG READING OF NONVOLATILE MEMORY CELLS, IN PARTICULAR ANALOG OR MULTILEVEL FLASH OR EEPROM MEMORY CELLS	Issued	Utility - ORG	NMXS-0544.00/US
	ន	6,163,483	12/19/2000	09/447,531	11/23/1999	CIRCUIT FOR PARALLEL PROGRAMMING NONVOLATILE MEMORY CELLS, WITH ADJUSTABLE PROGRAMMING SPEED	Issued	Utility - ORG	NMXS-0543,00/US
	SS	6,456,481	10/15/2002	09/438,232	11/12/1999	DEVICE AND METHOD FOR PROGRAMMING NONVOLATILE MEMORY CELLS WITH AUTOMATIC GENERATION OF PROGRAMMING VOLTAGE	Issued	Utility - ORG	NMXS-0542.00/US
		6,323,799	11/27/2001	09/421,616	10/19/1999	DEVICE FOR READING NON-VOLATILE MEMORY CELLS, IN PARTICULAR ANALOG FLASH MEMORY CELLS	Issued	Utility - ORG	NMXS-0541.00/US
		6,301,157	10/9/2001	09/415,024	10/7/1999	DEVICE	issued	Utility - ORG	NMXS-0540.00/US
丄		6.456.527	9/24/2002	09/501,131	2/9/2000	NONVOLATILE MULTILEVEL MEMORY AND READING METHOD THEREFORE	Issued	Utility - ORG	MMX>-0539.00/US
 AT	<u>ه</u>	6,530,058	3/4/2003	09/513,286	2/24/2000	MEMORY CELLS, NOT REQUIRING ADDITIONAL CELLS	Issued	Utility - ORG	NMXS-0538.00/US
	r.	6,602,774	8/5/2003	09/473,367	12/28/1999	SEMICONDUCTOR SUBSTRATE ASTRUCTURE STRATE ASTRUCT	Issued	Utility - ORG	NMXS-0537.00/US
	S	6,396,101	5/28/2002	09/836,590	4/16/2001	MEIHOU FOR MANUFACTURING ELECTRONIC DEVICES COMPRISING NON-VOLATILE MEMORY CELLS AND LY TRANSISTORS WITH SALICIDED JUNCTIONS GET SCHOOL SALICIDATION	Issued	Utility - DIV	NMXS-0536.01/US
	5 E	6,281,077	8/28/2001		9/9//9	MEMORY CELLS AND LY TRANSISTORS WITH SALICIDED JUNCTIONS	Issued	Utility - ORG	NMXS-0536.00/US
1	Animon	6,313,040	09/406,903 11/6/2001	18	9/28/1999		Abandoned	Otility - ORG	WWX-0535.00/US
				捌		S. P. S.	WatterStatus	Mattertype Mattessiatus	MIT DOMNO

S S S S	5,434,189 6,425,066	8/13/2002 7/23/2002	09/335,024 09/313,926	6/17/1999 5/18/1999		Issued	Utility - ORG	NMXS-0585.00/US
8 8 8	5,434,189	8/13/2002	09/335,024	6/17/1999			11:13: 000	NMXS-0585 OO/IIS
8 8				- /2 - /		Issued	Utility - ORG	NMXS-0584.00/US
SO	5,410,404	6/25/2002	09/561,272	4/28/2000		issued	Utility - ORG	NMXS-0583-00/US
	5,243,310	6/5/2001	09/546,975	4/11/2000		Issued	Utility - ORG	NMXS-0582.00/US
æ	6,324,098	11/27/2001	09/546,957	4/11/2000		Issued	Utility - ORG	Sn/00'1850-5X/WN
SS SS	6,310,801	10/30/2001	09/548,783	4/13/2000		Issued	Utility - ORG	NMXS-0580.00/US
ñ	5 2/10 002	1000/00/2	09/561.271	4/28/2000		issued	Utility - ORG	S0/00/6/50-5xMM
ĸ	6,511,874	1/28/2003	09/912,638	7/24/2001		Issued	Utility - DIV	NMXS-0578.01/US
US	6,294,798	9/25/2001	09/415,992	10/12/1999		Issued	Utility - ORG	NIVIXS-05/8.00/US
S	6,041,000	3/21/2000	09/183,840	10/30/1998		isoned.	Out of City	*** OF 50 (2)
S	6,081,466	6/27/2000	09/183,451	10/30/1998		Issued	OSC - Valled	NMXS-0577.00/1/S
US.	6,034,917	3/7/2000	09/183,589	10/30/1998		Issued	Utility - ORG	NMXS-0575.00/US
S	5,946,264	8/31/1999	09/183,231	10/30/1998		Issued	Utility - ORG	NMXS-0574.00/US
ß	6,084,390	7/4/2000	09/217,323	12/21/1998		Issued	Utility - ORG	NMXS-0573.00/US
S	6,118,188	9/12/2000	09/217,321	12/21/1998		Issued	Utility - ORG	NIVIXS-05/2.00/US
SS	6,249,112	6/19/2001	09/608,445	6/29/2000	APPARATING AND METUDO FOR CHATCHING POPULATION AND POPULATION AND METUDO FOR CHATCHING POPULATION AND METUDO FOR CHATCHING POPULATION AND METUDO FOR CHATCHING POPULATION AND METUDO FOR CHATCHING POPULATION AND METUDO FOR CHATCHING POPULATION AND POPULATION AND POPULATION AND POPULATION AND POPULATION AND POPULATION AND POPULATION AND POPULATION AND POPULATION AND POPULATION AND POPULATION AND POPULATION AND POPULATION AND POPULATION AND POPULATION AND POPULATION AND POPULATION AND POPULATION A	nancei	County - Olyo	2007 2007 2007
su	6,301,149	10/9/2001	09/513,598	2/25/2000		Issued	Utility - ORG	NMXS-0570.00/US
æ	6,396,132	5/28/2002	09/502,070	2/10/2000		lssued	Utility - ORG	NMXS-0569.00/US
æ	6,249,463	6/19/2001	09/457,500	12/8/1999		Issued	Utility - ORG	NMXS-0567.00/US
su	6,803,630	10/12/2004	10/350,745	1/24/2003	MEI HOD OF ADJUSTING PROGRAM VOLTAGE IN NON-VOLATILE MEMORIES, AND PROCESS FOR FABRICATING A NON-VOLATILE MEMORY DEVICE	Issued	Utility - DIV	NMXS-0566.01/US
æ	6,535,431	3/18/2003	09/552,933	4/20/2000		Issued	Utility - ORG	NMXS-0566.00/US
US	6,350,671	2/26/2002	09/579,778	5/26/2000	METHOD FOR AUTOALIGNING OVERLAPPED LINES OF A CONDUCTIVE MATERIAL PROVIDED IN INTEGRATED ELECTRONIC CIRCUITS	Issued	Utility - ORG	NWXS-0565.00/US
S	6,373,781	4/16/2002	09/499,799	2/8/2000		Issued	Utility - ORG	NMX5-0564.00/US
<u></u> 8	6,775,416	8/14/2001	09/472,496	12/27/1999		Issued	Utility - ORG	NMXS-0563.00/US
	ספר ארכ ש	11/27/2001	09/464 631	12/15/1999	,	Abandoned	Utility - ORG	NMXS-0562.00/US
SS	6,300,195	10/9/2001	09/512,900	2/25/2000	PROCESS FOR MANUFACTURING SEMICONDUCTOR INTEGRATED MEMORY DEVICES WITH CELLS MATRIX HAVING VIRTUAL GROUND	Issued	Utility - ORG	NWXS-0561.00/US
SS	6,365,456	4/2/2002	09/507,777	2/18/2000	PROCESS FOR MANUFACTURING SEMICONDUCTOR INTEGRATED MEMORY DEVICES WITH CELLS MATRIX HAVING VIRTUAL GROUND	Issued	Utility - ORG	NMXS-0560.00/US
US	6,424,575	7/23/2002	09/716,759	11/20/2000	SYNCHRONOUS OUTPUT BUFFER, PARTICULARLY FOR NON-VOLATILE MEMORIES	Issued	Utility - ORG	NMXS-0559.00/US
US	6,477,625	12	09/474,932	12/29/1999	METHOD FOR READING A MEMORY, PARTICULARLY A NON-VOLATILE MEMORY	Issued	Utility - ORG	NMXS-0558.00/US
	Espedate Parentine Commercial	1861 1862	SerialNo	FileDate	Exhibit A - US issued Patents	MatterStatus	MatterType	MII-Dokavo Marteriype

Page 22 of 40

NMXS-0612.00/US	NMXS-0611.00/US	NMXS-0610.00/US	NMXS-0608.01/US	NMXS-0607.00/US	NMXS-0606.00/US	NMXS-0605.00/US	NMXS-0604.00/US	NMXS-0603.00/US	NMXS-0602.00/US	NMXS-0601.00/US	NWX5-0600.00/US	NMXS-0599.00/US	NMXS-0598.00/US	NMXS-0597.00/US	NMXS-0596,00/US	NWXS-0595.00/US	NMXS-0594.00/US	NMX5-0593.00/US	NMXS-0592.00/US	NMXS-0591.00/US	NMXS-0590.00/US	NWXS-0589.00/US	NMXS-0588.00/US	NMXS-0587.00/US		MII-Dektwo
Utility - ORG	Utility - ORG	Utility - ORG	Utility - DIV	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG	Utility - ORG		MatterType
Issued	Issued	Issued	Issued	Issued	Issued	Abandoned	Issued	Issued	Issued	Issued	Issued	Issued	Issued	Issued	Issued	lssued	Issued	Issued	Issued	Issued	Issued	Issued	Abandoned	Issued		Matte Status
NON-VOLATILE MEMORY WITH FUNCTIONAL CAPABILITY OF BURST MODE READ AND PAGE MODE READ DURING SUSPENSION OF AN OPERATION OF ELECTRICAL ALTERATION	NON-VOLATILE MEMORY WITH FUNCTIONAL CAPABILITY OF SIMULTANEOUS MODIFICATION OF THE CONTENT AND BURST MODE READ OR PAGE MODE READ	BUFFER DEVICE WITH DUAL SUPPLY VOLTAGE FOR LOW SUPPLY VOLTAGE APPLICATIONS	BIPOLAR TRANSISTOR PRODUCED USING PROCESSES COMPATIBLE WITH THOSE EMPLOYED IN THE MANUFACTURE OF MOS DEVICES	SOFT PROGRAMMING METHOD FOR NON-VOLATILE MEMORY CELLS	METHOD FOR READING DATA FROM A NON-VOLATILE MEMORY DEVICE WITH AUTODETECT BURST MODE READING AND CORRESPONDING READING CIRCUIT	ROW DECODER FOR SELECTIVELY BIASING A WORDLINE TO A POSITIVE OR NEGATIVE VOLTAGE	CMOS SWITCH CIRCUIT FOR TRANSFERRING HIGH VOLTAGES, IN PARTICULAR FOR LINE	METHOD FOR PROGRAMMING MULTI-LEVEL NON-VOLATILE MEMORIES BY CONTROLLING THE GATE VOLTAGE	NON-VOLATILE MEMORY DEVICE WITH LOW POWER CONSUMPTION AND AND RELATIVE WRITING, READING AND ERASING METHODS	METHOD AND APPARATUS FOR GENERATING FROM A SINGLE SUPPLY LINE VOLTAGES INTERNAL TO A FLASH MEMORY WITH REDUCED SETTLING TIMES	METHOD AND A DEVICE FOR MEASURING AN ANALOG VOLTAGE IN A NON-VOLATILE MEMORY	BIASING STAGE FOR BIASING THE DRAIN TERMINAL OF A NONVOLATILE MEMORY CELL DURING THE READ PHASE	CIRCUIT FOR READING A SEMICONDUCTOR MEMORY	SYNCHRONOUS MULTILEVEL NON-VOLATILE MEMORY AND RELATED READING METHOD	NONVOLATILE MEMORY DEVICE WITH HIERARCHICAL SECTOR DECODING	METHOD FOR THE IN-WRITING VERIFICATION OF THE THRESHOLD VALUE IN NON- VOLATILE MEMORIES	NONVOLATILE MEMORY DEVICE, IN PARTICULAR A FLASH-EEPROM	ERASING AND PARALLEL REWRITING CIRCUIT FOR MEMORY CELL BLOCKS, PARTICULARLY FOR ANALOG FLASH CELLS, AND RELATED OPERATING METHOD	READING METHOD FOR NON-VOLATILE MEMORIES WITH SENSING RATIO VARIABLE WITH THE READING VOLTAGE, AND DEVICE TO REALIZE SAID METHOD	METHOD FOR ERASING AND REWRITING NON VOLATILE MEMORY CELLS AND PARTICULARLY FLASH CELLS	METHOD AND DEVICE FOR THE PROGRAMMING OF AN ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY FOR IMPROVING RELIABILITY	SECURED EEPROM MEMORY COMPRISING MEANS FOR THE DETECTION OF ERASURE BY ULTRAVIOLET RADIATION	METHOD FOR VERIFYING THE MEMORY CIRCUIT INTEGRITY	DEVICE AND METHOD FOR GENERATING A HIGH VOLTAGE	MULTIPLE LEVEL FLOATING-GATE MEMORY	The state of the s
7/19/2000	7/28/2000	12/13/2000	2/15/2002	12/14/2000	11/20/2000	6/16/2000	6/2/2000	8/2/2000	7/21/2000	6/30/2000	6/29/2000	6/2/2000	6/26/2000	5/17/2000	6/26/2000	5/11/2000	4/20/2000	6/13/2000	6/8/2000	4/20/2000	4/21/2000	11/24/1999	12/2/1999	8/10/1999	12/2/1999	FileDate
09/619,589	09/627,703	09/736,984	10/077,288	09/738,253	09/716,746	09/595,054	09/585,916	09/631,187	09/620,765	09/608,239	09/608,847	09/586,399	09/603,275	09/572,127	09/602,680	09/569,232	09/552,945	09/592,796	09/589,723	09/553,526	09/556,476	09/448,632	09/452,446	09/371,549	9 09/453,753	SeralNo 4
8/27/2002	6/28/2005	11/20/2001	12/30/2003	10/22/2002	2/19/2002	3/12/2002	8/13/2002	4/2/2002	9/18/2001	5/21/2002	1/14/2003	11/20/2001	12/25/2001	3/6/2001	9/24/2002	9/18/2001	2/26/2002	11/6/2001	3/26/2002	8/28/2001	9/18/2001	6/19/2001	4/3/2001	12/5/2000	6/11/2002	IssueDate
6,442,068	6,912,598	6,320,361	6,670,229	6,469,934	6,349,059	6,356,481	6,433,583	6,366,496	6,292,400	6,392,936	6,507,183	6,320,790	6,333,885	6,198,660	6,456,530	6,292,398	6,351,413	6,314,043	6,363,015	6,282,125	6,292,396	6,249,456	6,212,112	6,157,243	6,404,679	PatentNo
US	SN	υs	Sn	SS	SN	US	દ્ધ	æ	ક્ર	US	SS	St	US	ĸ	æ	ES	us	ĸ	S	us	us	SU	us	1	SS	Country

US	6,351,434	2/26/2002	09/767,762	1/23/2001	The state of the s			
ß	6,677,206	1/13/2004	09/740,407	12/19/2000	SYNCHRONOUS COUNTER FOR FLECTRONIC ASSAUCHCE	Issued	Utility - ORG	NMXS-0643.00/US
٤	460,524,0	201000			NON-VOLATILE HIGH-PERFORMANCE MEMORY DEVICE AND RELATIVE	tssued	Utility - ORG	NMXS-0642-00/US
; S	6,898,745	8/6/2002	09/778.330	2/6/2001	VOLTAGE BOOSTING DEVICE, IN PARTICULAR FOR SPEEDING POWER-UP OF MULTILEVEL NONVOLATILE MEMORIES	Issued	Utility - ORG	NMXS-0641.00/US
S	6,418,051	7007/61/	7,0°50,1°50	10002/rz/m	INTEGRATED DEVICE WITH OPERATIVITY TESTING	Abandoned	Utility - ORG	\$0.100.0400-CVIAINI
ક્ર	6,437,636	8/20/2002	09//4/,312	7/14/201	NON-VOLATILE MEMORY DEVICE WITH CONFIGURABLE ROW REDUNDANCY	Issued	Utility - ORG	SO/00/6590-SYMM
S	0,14,10	2002 focts	2000000	מממל בכל בל	LOW CONSUMPTION VOLTAGE BOOST DEVICE	Issued	Utility - ORG	NMXS-0638.00/US
ā 1	6 301 173	4/30/2002	09/686.362	10/10/2000	SERIAL-FLASH, EPROM, EEPROM AND FLASH EEPROM NONVOLATILE MEMORY IN AMG	Issued	Utility - ORG	NMXS-0637.00/US
<u> </u>	6.525.961	2/25/2003	09/952,957	9/12/2001	METHOD AND CIRCUIT FOR PROGRAMMING A MULTILEVEL NON-VOLATILE MEMORY	Issued	Utility - ORG	NMXS-0635.00/US
ß	6,128,219	10/3/2000	09/428,683	10/27/1999	TEST METHOD	Issued	Utility - ORG	NMXS-0633.00/US
S	6,373,780	4/16/2002	09/627,273	7/28/2000	SINGLE SUPPLY VOLTAGE NONVOLATILE MEMORY DEVICE WITH ROW DECODING	Issued	Utility - ORG	NMXS-0632.00/US
U.S.	6,420,223	7/16/2002	09/730,518	12/5/2000	MANUFACTURING PROCESS FOR NON-VOLATILE FLOATING GATE MEMORY CELLS INTEGRATED ON A SEMICONDUCTOR SUBSTRATE AND COMPRISED IN A CELL MATRIX WITH AN ASSOCIATED CONTROL CIRCUITRY	Issued	Utility - ORG	NMXS-0631.00/US
ᅜ	6,603,171	8/5/2003	10/225,315	8/20/2002	PROCESS FOR MANUFACTURING ELECTRONIC DEVICES COMPRISING NONVOLATILE MEMORY CELLS OF REDUCED DIMENSIONS	issued	Utility - DIV	NMXS-0630.01/US
US	6,509,222	1/21/2003	09/718,971	11/22/2000	MEMORY CELLS OF REDUCED DIMENSIONS	Issued	Utility - ORG	NMXS-0630.00/US
55	6,549,485	4/15/2003	09/972,753	10/5/2001	CONTROL AND TIMING STRUCTURE FOR A MEMORY	issued	Odilty - Osts	HIBS COZZOVI UZ
RJ.	6,385,107	5/7/2002	09/710,067	11/9/2000	ARCHITECTURE FOR HANDLING INTERNAL VOLTAGES IN A NON-VOLATILE MEMORY, PARTICULARLY IN A SINGLE-VOLTAGE SUPPLY TYPE OF DUAL-WORK FLASH MEMORY	lssued	Utility - ORG	NMXS-0628.00/US
æ	6,362,053	3/26/2002	09/630,933	8/2/2000	FLOW PROCESS FOR PRODUCING NON-VOLATILE MEMORIES WITH DIFFERENTIATED REMOVAL OF SACRIFICAL OXIDE	Issued	Utility - ORG	NMXS-0627.00/US
US S	6,507,534	1/14/2003	09/797,171 -	2/27/2001	COLUMN DECODER CIRCUIT FOR PAGE READING OF A SEMICONDUCTOR MEMORY	Issued	Utility - ORG	NMXS-0626.00/US
ž (S	6,400,607	10/29/2002	09/699,043	10/27/2000	READING METHOD AND CIRCUIT FOR A NON-VOLATILE MEMORY	Issued	Utility - ORG	NMXS-0625.00/US
S	6,528,885	3/4/2003	789,896/60	10/27/2001	READING CIRCUIT FOR A NON-VOLATILE MEMORY	issued	Utility - ORG	NMXS-0624.00/US
		2/4/2000	00,000 000	10/1/2001	ANTI-DECIPHERING CONTACTS	Lapsed	Utility - ORG	NMXS-0623.00/US
US	6,424,121	7/23/2002	09/714,837	11/15/2000	VOLTAGE GENERATOR SWITCHING BETWEEN ALTERNATING, FIRST AND SECOND VOLTAGE VALUES, IN PARTICULAR FOR PROGRAMMING MULTILEVEL CELLS	lssued	Utility - ORG	NMXS-0622.00/US
ß	6,854,040	2/8/2005	09/717,938	11/21/2000	READING METHOD	lssued	Utility - ORG	NMXS-0621.00/US
s	6,574,146	6/3/2003	09/738,889	12/15/2000	CIRCUIT AND METHOD FOR TIMING MULTI-LEVEL NON-VOLATILE MEMORIES	Issued	Utility - ORG	NNIX5-0620.00/05
S.	6,307,778	10/23/2001	09/658,236	9/8/2000	NON VOLATILE MEMORY WITH DETECTION OF SHORT CIRCUITS BETWEEN WORD LINES	Issued	Utility - ORG	Sn/00/619-05/NN
S.	6,638,833	10/28/2003	09/804,693	3/9/2001	PROCESS FOR THE FABRICATION OF INTEGRATED DEVICES WITH REDUCTION OF DAMAGE FROM PLASMA	Issued	Utility - ORG	NMXS-0618.00/US
<u> </u>	6.438.040	8/20/2002	09/629,229	7/31/2000	ENABLING CIRCUIT FOR OUTPUT DEVICES IN ELECTRONIC MEMORIES	Issued	Utility - ORG	NMXS-0617.00/US
7	6 377 184	17/4/7001	09/621.019	7/21/2000	READ CIRCUIT FOR A NONVOLATILE MEMORY	Issued	Utility - ORG	NMXS-0615.00/US
SS	6,501,147	12/31/2002	09/713,144	11/14/2000	MANUFACTURE OF AN HV-MOS TRANSISTOR WITH LOW MULTIPLICATION FACTOR IN A DUAL-GATE CMOS PROCESS	Issued	Utility - ORG	NMXS-0614.00/US
SU	6,381,177	4/30/2002	09/699,309	10/27/2000	IN PARTICULAR OF THE FLASH EEPROM AND EPROM TYPE	Issued	Utility - ORG	NMXS-0613.00/US
Country	issueDate Patentino	SsueDate	Elebate SetalNo 1	FileDate		MatterStabus	Matterlype	MILECHIO MARKETYPE MARKESTADIS

Page 24 of 40

	-
ı	•
	=
ı	_
	~
ı	•
	ŧ
ı	
	S
ı	v
ı	-
ı	S
ı	8
ı	m
	Ξ
ı	Ä
	-
	745
١	2
	æ
	-
	=
	u

us	6,842,191	1/11/2005	09/705,145	11/2/2000	ed COLOR IMAGE RESTORATION WITH ANTI-ALIAS	G Issued	Utility - ORG	NMXX-767-100/US
ន	6,587,913	7/1/2003	09/773,300	1/31/2001	ed MODE WITH THE TWO SEMI-ARRAYS INDEPENDENTLY READABLE IN RANDOM ACCESS ASYNCHRONOUS MODE		Utility - ORG	NMXS-0670.00/US
US	6,625,706	9/23/2003	09/773,760	1/31/2001		i i i i i i i i i i i i i i i i i i i	ounty - One	100000000000000000000000000000000000000
US	6,366,634	4/2/2002	09/774,878	1/31/2001		-	Utility - ORG	NMXS-0666 00/3/S
S	6,473,339	10/29/2002	09/773,272	1/31/2001			Utility - ORG	NWXS-0669-00/135
SS	6,452,864	9/17/2002	09/774,539	1/31/2001		G Issued	Utility - ORG	NMXS-0566.00/US
SS	6,470,431	10/22/2002	09/774,542	1/31/2001		6 Issued	Utility - ORG	NMXS-0665.00/US
ᅜ	6,442,072	8/27/2002	09/745,286	12/21/2000		G Issued	Utility - ORG	NMXS-0664.00/US
Ŋ	6,282,134	8/28/2001	09/670,471	9/26/2000	ed Memory test method and nonvolatile memory with low error masking probability	5 Issued	Utility - ORG	NMXS-0663.00/US
US	6,438,048	8/20/2002	09/670,248	9/26/2000	ed NONVOLATILE MEMORY AND HIGH SPEED MEMORY TEST METHOD	ssued	Utility - ORG	NMXS-Ubb2.UU/US
æ	6,420,926	7/16/2002	09/738,890	12/15/2000			Utility - ORG	NMXS-U661.00/US
ß	6,781,916	8/24/2004	10/442,844	5/20/2003			Utility - DIV	NMXS-0660.01/US
S	6,594,192	7/15/2003	09/653,495	8/31/2000			Utility - ORG	NMXS-0660.00/US
55	6,476,669	11/5/2002	09/902,206	7/10/2001			Utility - DIV	NMXS-0659.01/US
ន	6,281,734	8/28/2001	09/476,036	12/31/1999	REFERENCE VOLTAGE ADJUSTMENT	3 Issued	Utility - ORG	NMXS-0659.00/US
55	6,580,637	6/17/2003	09/972,769	10/5/2001		3 Issued	Utility - ORG	NMXS-0658.00/US
ß	6,750,505	6/15/2004	10/337,556	1/7/2003	NON-VOLATILE MEMORY CELL WITH A FLOATING GATE REGION AUTOALIGNED TO THE ISOLATION AND WITH A HIGH COUPLING COEFFICIENT	/ Issued	Utility - DIV	NMXS-0657.01/US
ន	6,537,879	3/25/2003	09/900,501	7/6/2001			Utility - ORG	NMXS-0657.00/US
2	6,559,709	5/6/2003	09/821,827	3/28/2001	L	Abandoned	Utility - ORG	NMXS-0656.00/US
ह्न	6,476,664	11/5/2002	09/823,262	3/29/2001			Utility - ORG	NMXS-0655,00/US
ĸ	6,549,473	4/15/2003	09/871,234	5/30/2001	CIRCUITAL STRUCTURE FOR READING DATA IN A NON-VOLATILE MEMORY DEVICE	issued	Utility - ORG	NMXS-0654.00/US
ĸs	6,507,517	1/14/2003	09/871,235	5/30/2001		issued	Utility - ORG	NMXS-0653,00/US
US	7,168,016	1/23/2007	09/823,926	3/30/2001		3 Issued	Utility - ORG	NMXS-0652.00/US
æ	6,686,241	2/3/2004	09/798,778	3/2/2001	METHOD OF FORMING LOW-RESISTIVITY CONNECTIONS IN NON-VOLATILE MEMORIES	issued	Utility - ORG	NMXS-0651.00/US
ષ્ટ	6,650,173	11/18/2003	09/714,852	11/15/2000	PROGRAMMABLE VOLTAGE GENERATOR	Issued	Utility - ORG	NMXS-0650.00/US
US.	6,466,479	10/15/2002	09/898,744	7/3/2001		issued	Utility - ORG	NMXS-0649.00/US
S	6,581,134	6/17/2003	09/817,804	3/26/2001		issued	Utility - ORG	NMXS-0648.00/US
ß	6,451,653	9/17/2002	09/858,335	5/15/2001	MANUFACTURING PROCESS FOR THE INTEGRATION IN A SEMICONDUCTOR CHIP OF AN INTEGRATED CIRCUIT INCLUDING A HIGH-DENSITY INTEGRATED CIRCUIT COMPONENTS PORTION AND A HIGH-PERFORMANCE LOGIC INTEGRATED CIRCUIT COMPONENTS PORTION	Issued	បឋារិស្ម - ORG	NMXS-0647.00/US
US	6,954,395	10/11/2005	10/742,181	12/19/2003			Utility - DIV	NMXS-0646,03/US
5 8	7,072,212	7/4/2006	10/742,429	12/19/2003		-	Utility - DIV	NMXS-0646.02/US
7 8	808 589.9	1/27/2004	10/179.553	6/24/2002		1	Utility - DIV	NMXS-0646.01/US
5 8	6.414.875	7/2/2002	09/817.363	3/20/2001		1	Utility - ORG	NMXS-0646.00/US
5 5	6,501,700	12/31/2002	09/974.737	10/9/2001		$\frac{1}{2}$	Utility - ORG	NMXS-0645.00/US
S. Amitonia	37. 708 y	10/12/2004	09/877 369		SYNCHRONIZATION CIRCUIT FOR READ PATHS OF AN ELETRONIC MEMORY	Talega Ballan	200	NMXS-0644.00/US
	To the second se		CONTINUES	Tillenare.	Exhibit A - US Issued Patents	Nattersiatis	MatterType	MII DCKING

	-
ı	7
1	_
1	=
1	•
	•
4	•
1	•
	•
	ç
1	u
•	
	12
	2.5
	S
•	c
1	7
	12
	О
•	
ı	۳
1	nī
1	-
	-
	ш
ł	**
•	=
2	17
5	٧ı

		MatterStatus			SerialNo	FlieDate SerialNo IssueDate PatentNo IssueDate	PatentNo II	Country
NMXS-0672.00/US	Utility - NSPCT	Issued	VOLTAGE PRODUCTION CIRCUIT	6/26/2000	10/019,771	9/16/2003	6,621,720	ક્ર
NMXS-0673.00/US	Utility - ORG	Issued	METHOD FOR PAGE MODE WRITING IN AN ELECTRICALLY ERASABLE/PROGRAMMABLE NON-VOLATILE MEMORY AND CORRESPONDING ARCHITECTURE	9/12/2000	09/660,303	1/7/2003	6,504,791	US
NMXS-0674,00/US	Utility - ORG	Issued	MEMORY INCORPORATING COLUMN REGISTER AND METHOD OF WRITING IN SAID MEMORY	9/29/2000	09/675,366	10/23/2001	6,307,792	Я
NMXS-0674.01/US	VIG - VIIIGN	issued	MEMORY INCORPORATING COLUMN REGISTER AND METHOD OF WRITING IN SAID MEMORY	9/13/2001	09/952,904	5/7/2002	6,385,096	SS
NMXS-0675.00/US	Utility - ORG	Issued	ARCHITECTURE OF A NON-VOLATILE ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY	9/7/2000	09/657,319	8/14/2001	6,275,413	SS
NMXS-0677.00/US	Utility - ORG	Issued	PAGE BY PAGE PROGRAMMABLE FLASH MEMORY	12/14/2000	09/737,170	1/4/2005	6,839,285	S
NMXS-0678.00/US	Utility - ORG	Issued	METHOD FOR THE CORRECTION OF A BIT IN A STRING OF BITS	12/15/2000	09/737,827	5/11/2004	6,735,733	S
NMX5-0679.00/US	Utility - ORG	Issued	HIGH-EFFICIENCY BIDIRECTIONAL VOLTAGE BOOSTING DEVICE	2/13/2001	09/788,623	9/10/2002	6,448,842	SS
NMXS-0680.00/US	Utility - ORG	Issued	CHARGE PUMP BOOSTER DEVICE WITH TRANSFER AND RECOVERY OF THE CHARGE	2/13/2001	09/785,042	6/11/2002	6,404,272	55
NMXS-0681.00/US	Utility - ORG	Issued	NONVOLATILE MEMORY CELL WITH HIGH PROGRAMMING EFFICIENCY	7/30/2001	09/919,341	5/11/2004	6,734,490	ક્ક
NMXS-0682.00/US	Utility - ORG	Issued	METHOD AND A CIRCUIT STRUCTURE FOR MODIFYING THE THRESHOLD VOLTAGES OF NON-VOLATILE MEMORY CELLS	7/18/2001	09/908,986	2/11/2003	6,519,183	SS
Sn/00'8890-5xww	Utility - ORG	Issued	CONTROL CIRCUIT FOR A VARIABLE-VOLTAGE REGULATOR OF A NONVOLATILE MEMORY WITH HIERARCHICAL ROW DECODING	9/21/2001	09/960,851	1/7/2003	6,504,758	υs
NMXS-0684.00/US	Utility - ORG	Issued	CIRCUIT ARRANGEMENT FOR THE LOWERING OF THE THRESHOLD VOLTAGE OF A DIODE CONFIGURED TRANSISTOR	6/13/2001	09/881,661	12/31/2002	6,501,673	ĸ
NMXS-0685.00/US	Utility - ORG	Issued	DIRECT-COMPARISON READING CIRCUIT FOR A NONVOLATILE MEMORY ARRAY	8/15/2001	09/930,875	10/8/2002	6,462,987	SS
NMXS-0686.00/US	Utility - ORG	penssi	NON-VOLATILE MEMORY WITH A CHARGE PUMP WITH REGULATED VOLTAGE	7/19/2001	09/909,467	11/12/2002	6,480,436	S
NMXS-0687.00/US	Utility - ORG	Issued	CHARGE PUMP WITH EFFICIENT SWITCHING TECHNIQUES	12/11/2000	09/735,277	3/19/2002	6,359,500	SU
SO /00'8890-521Min	Ubirty - ORG	Issued	High-voltage bidirectional switch made using high-voltage MOS transistors	6/16/2000	09/595,680	9/11/2001	6,288,603	ន
NMXS-0691.00/US	Utility - ORG	Issued	LATERAL DMOS TRANSISTOR WITH FIRST AND SECOND DRAIN ELECTRODES IN RESPECTIVE CONTACT WITH HIGH-AND LOW-CONCENTRATION PORTIONS OF A DRAIN	9/20/2001	09/960,254	9/23/2003	6,624,471	S 8
NMXS-0692.00/US	Utility - ORG	Issued	VOLTAGE BOOSTER WITH A LOW OUTPUT RESISTANCE	2/13/2001	09/785,083	6/11/2002	6.404.273	ន
NMX5-0693.00/US	Utility - ORG	Issued	MULTIPURPOSE METHOD FOR CONSTRUCTING AN ERROR-CONTROL CODE FOR MULTILEVEL MEMORY CELLS OPERATING WITH A VARIABLE NUMBER OF STORAGE LEVELS, AND MULTIPURPOSE ERROR-CONTROL METHOD USING SAID ERROR-CONTROL CODE	11/2/2001	10/015,949	5/16/2006	7,047,478	SS
NMXS-0694.00/US	Utility - ORG	Issued	FOLDING TOP FOR A MOTOR VEHICLE	10/31/2001	09/002,599	8/5/2003	6,603,681	S
NMXS-0595.00/US	Utility - ORG	Issued	NONVOLATILE SEMICONDUCTOR MEMORY CAPABLE OF SELECTIVELY ERASING A PLURALITY OF ELEMENTAL MEMORY UNITS	7/31/2001	09/919,789	3/11/2003	6,532,171	SU
Sn/00°9690°5XWN	Utility - ORG	Issued	ELECTRICALLY MODIFIABLE, NON-VOLATILE, SEMICONDUCTOR MEMORY WHICH CAN KEEP A DATUM STORED UNTIL AN OPERATION TO MODIFY THE DATUM IS COMPLETED.	12/28/2001	10/036,088	1/4/2005	6,839,818	SO
NMXS-0697.00/US	Utility - ORG	Issued	VOLTAGE REGULATOR FOR LOW-CONSUMPTION CIRCUITS	11/7/2001	09/008,540	5/6/2003	6,559,627	S
NMXS-0698.00/US	Utility - ORG	Issued	SMALL SIZE, LOW CONSUMPTION, MULTILEVEL NONVOLATILE MEMORY	10/4/2001	09/972,726	4/1/2003	6,542,404	SS
NMXS-0699.00/US	Utility - ORG	Issued	METHOD FOR STORING AND READING DATA IN A MULTILEVEL NONVOLATILE MEMORY	10/11/2001	09/976,473	11/11/2003	6,646,913	SS
NMXS-0700.00/US	Utility - ORG	Abandoned	NONVOLATILE MEMORY DEVICE, HAVING PARTS WITH DIFFERENT ACCESS TIME, RELIABLITY, AND CAPACITY	9/19/2001	09/957,628	12/10/2002	6,493,260	R
NMXS-0701.00/US	Utility - ORG	Issued	CONTROL CIRCUIT FOR AN OUTPUT DRIVING STAGE OF AN INTEGRATED CIRCUIT	11/21/2001	09/991,493	5/20/2003	6,567,318	SN

) JIGE
l	-
l	S
	SSUec
	d Pat
	ents

ISSUED ISSUED	US.	7,084,032	8/1/2006	10/356,351	1/30/2003		issued	Oully - ORG	20,000,000
Mediatichesis Mediatichesi	บร	7,017,099	3/21/2006	10/159,782	5/30/2002		Issued	Culty-Orig	NMXC0732 00/116
Material Residence Materia	S	6,724,658	4/20/2004	10/133,231	4/26/2002		150 GEC	The Carry City	NWXS-0231 OO/US
International Column	RS	6,639,833	10/28/2003	10/076,023	2/13/2002		issued	Hellion - Con	NI/OU UEZU-SXIMIN
Mariesti British Mariesti Br	55	6,/28,141	4/27/2004	4,0/c27 for	2007/07/4		Transit of the state of the sta		NMXS-0729.00/11s
WARRING CIRCUIT FOR PROCRAMING PIERWACHTC ROW DECODING IN NON-VOLATILE 5/14/2001 5/18/2003 5/1	5	6,700,319	3/2/2004	10/173 97/	4716/2002		issued	Utility - ORG	NMXS-0728.00/US
MARINESTRIAN MARING GIOCHT CON MULTI-LER MEMORY CELLS WITH PROGRAMA AND RESPONSITY 1/2/2001 10/25/201 10		700 000	o la Canada	10/176 00%	cuuc/uc/s		İssued	Utility - ORG	NMXS-0727.00/US
WARRISTHAM	8	6,668,303	12/23/2003	10/057,768	1/24/2002		Issued	Utility - ORG	NMXS-0726.00/US
SESUADE SUSTING CIRCLIT FOR MULTI-LEPEL MEMORY CELLS STANDOIL STANDOIL SUSTEDIANS SU	SS	6,871,258	3/22/2005	10/159,780	5/30/2002		Issued	Utility - ORG	NMXS-0725.00/US
Interview Inte	5	6,618,315	9/9/2003	10/057,769	1/24/2002		Issued	Dully - One	CO /07-4-00/ CO
Interviews Int	ឆ	6,605,985	8/12/2003	10/162,135	6/3/2002		Issued	Utility - ORG	NMXS-0723.00/US
State	æ	6,731,557	5/4/2004	10/176,387	6/20/2002		Abandoneo	Utility - ORG	NMXS-0722.00/US
SEASONG CIRCUIT FOR MULTI-LEVEL MEMORY CELLS	S	6,657,895	12/2/2003	10/118,660	4/8/2002		Issued	Other-Ord	MIND-0721-00/03
SESSUED SECURITY FOR MULTI-LEVEL MEMORY CELLS SCHAPLOOIS SUBJECT SECURITY SUBJECT	S	6,963,512	11/8/2005	10/328,721	12/23/2002		Issued	Utility - ORG	NMXS-0720.00/US
SESSURED SACE SAC	s	6,655,758	12/2/2003	10/035,909	12/19/2001		Issued	Other - ORG	SO (00'91/0-cylala)
ISSUED I	S	6,643,179	11/4/2003	10/047,918	1/14/2002		Issued	Utility - ORG	NMXS-0717.00/US
Internation Internation	us	6,667,903	12/23/2003	10/017,502	12/14/2001		issued	Outry - Ong	1000 or 40.00/ 03
	s	6,552,952	4/22/2003	10/158,553	5/30/2002		Issued	Utility - ORG	NMXS-0716 00/135
Interestables Interestable	ß	6,687,159	2/3/2004	10/036,337	12/19/2001		Issued	Utility - ORG	NMXS-0714.00/US
ISSUEDED ISSUED	g	6,687,167	2/3/2004	10/225,513	8/20/2002		Issued	Utility - ORG	NMXS-0713.00/US
SEVERIOR SEVERIOR	ß	6,829,177	12/7/2004	10/161,055	5/30/2002		issued	Utility - ORG	NMXS-0712.00/US
Serial No. Ser	SS	6,788,586	9/7/2004	10/161,053	5/30/2002		Issued	Utility - ORG	NMXS-0711.00/US
Serial No. Ser	ន	6,594,180	7/15/2003	10/158,554	5/30/2002		Issued	OBINY - ORG	CO (OD.OT / O.CVININI
Serial S	S	6,700,226	3/2/2004	10/035,006	12/27/2001		Issued	Utility - ORG	SU/00.80/0-2X/MN
Serial S	3	6.788.517	9/7/2004	09/917,613	7/26/2001		lssued	Utility - ORG	NMXS-0707.00/US
Serial Several Serial	S	6,788,579	9/7/2004	10/119,523	4/9/2002		Issued	Utility - ORG	NMXS-0706.00/US
Mattrestatus Seriamo	s	6,480,421	11/12/2002	09/003,474	10/25/2001		Issued	Utility - ORG	NMXS-0705.00/US
Matricistries Seria Mos	æ	6,674,385	1/6/2004	10/060,076	1/29/2002		Issued	Utility - CON	NMXS-0704.01/US
MattreStatus SerialNo	S	6,493,268	12/10/2002	09/905,163	7/12/2001		Issued	Utility - ORG	NMXS-0703.00/US
Matrixians Figure 1 Section 1 Section 1 Section 1 Section 1 Section 1 Section 1	SCI	6,535,428		09/882,535		BIASING CIRCUIT FOR MULTI-LEVEL MEMORY CELLS	Issued	Utility - ORG	NMXS-0702.00/US
			Heri	Salara Salara Salara Salara Salara Salara Salara Salara Salara Salara Salara Salara Salara Salara Salara Salar	737	Sign to the second seco	MatterStatu	MatterType	Malebokowo

Page 27 of 40

Mill-Dording Matter type NationStatus	MatterType	MatterStatus	Hite	FileDate	SerialNo	Distriction PatentNo	PatentNo	Country
NMXS-0733.00/US	Utility - ORG	Issued	MANUFACTURING PROCESS OF A SEMICONDUCTOR NON-VOLATILE MEMORY CELL		10/323,615	8/28/2007	7,262,098	ន
NMXS-0734.00/US	Utility - ORG	Issued	PROCESS FOR REMOVING POLYMERS DURING THE FABRICATION OF SEMICONDUCTOR DEVICES	7/2/2002	10/189,152	4/13/2004	6,720,271	SS
NMXS-0735.00/US	Utility - ORG	Issued	LOW POWER CHARGE PUMP CIRCUIT	11/7/2002	10/290,030	11/9/2004	6,816,001	US
NMXS-0736.00/US	Utility - ORG	issued	CONTENT ADDRESSABLE MEMORY (CAM) WITH BATTERY BACK-UP	6/29/2001	09/895,491	12/17/2002	6,496,439	SU
NMXS-0737.00/US	Utility - ORG	Issued	Data output buffer with precharge	8/11/2000	09/636,363	9/18/2001	6,292,405	SS
NMXS-0738.00/US	Utility - ORG	Issued	INTERLACED MEMORY DEVICE WITH RANDOM OR SEQUENTIAL ACCESS	10/15/2001	09/977,561	3/2/2004	6,701,419	US
NMXS-0739.00/US	Utility - ORG	Issued	OUTPUT BUFFER AND METHOD OF DRIVING	8/8/2001	09/925,842	12/3/2002	6,489,807	SS
NMXS-0740.00/US	Utility - ORG	Issued	GENERATOR CIRCUIT FOR VOLTAGE RAMPS AND CORRESPONDING VOLTAGE GENERATION METHOD	12/28/2001	10/033,711	11/18/2003	6,650,153	US
NMXS-0741.00/US	Utility - ORG	Issued	SOOST DEVICE FOR NONVOLATILE MEMORIES WITH AN INTEGRATED STAND-BY CHARGE PUMP	2/13/2002	10/076,134	11/18/2003	6,650,569	æ
NMXS-0742.00/US	Utility - ORG	Abandoned	CHARGE PUMP FOR A NONVOLATILE MEMORY WITH READ VOLTAGE REGULATION IN THE PRESENCE OF ADDRESS SKEW, AND NONVOLATILE MEMORY COMPRISING SUCH A CHARGE PUMP	2/5/2002	10/068,560	5/6/2003	6,560,145	55
NMXS-0743.00/US	Utility - ORG	lssued	DEVICE AND METHOD FOR TIMING THE READING OF A NONVOLATILE MEMORY WITH REDUCED SWITCHING NOISE	2/15/2002	10/077,687	1/6/2004	6,674,666	ક્ર
NMXS-0744.00/US	Utility - ORG	Issued	DEVICE AND METHOD FOR AUTOMATICALLY GENERATING AN APPROPRIATE NUMBER OF WAIT CYCLES WHILE READING A NONVOLATILE MEMORY	4/3/2002	10/115,888	7/12/2005	6,917,994	SS
NMXS-0745.00/US	Utility - ORG	Issued	CIRCUIT FOR GENERATING A PULSE SIGNAL INDEPENDENT OF VOLTAGE AND TEMPERATURE VARIATIONS	10/31/2001	09/998,903	4/15/2003	6,549,486	US
NMXS-0746.00/US	Utility - ORG	Issued	NEGATIVE CHARGE PUMP ARCHITECTURE WITH SELF-GENERATED BOOSTED PHASES	10/31/2001	09/998,902	4/13/2004	6,720,822	S.
NMXS-0748.00/US	Utility - ORG	issued	THRESHOLD AMPUFIER	8/9/2001	09/925,979	4/15/2003	6,549,048	SS
NMXS-0749.00/US	Utility - NSPCT	Issued	PAGE-ERASABLE FLASH MEMORY	11/14/2001	10/438,733	10/19/2004	6,807,103	US.
NMXS-0750.00/US	Utility - UKG	Issued	METHOD AND DEVICE FOR SEQUENTIAL READOUT OF A MEMORY WITH ADDRESS	1/29/2002	10/060,105	8/10/2004	6,774,663	US
			STACH MEMORY INCLUDING MEANS OF CHECKING MEMORY CELL TUBERTION	21 221 2002	10,000,000	00021510	0,526,50	8
NMXS-0752.00/US	Utility - ORG	Issued	FLASH MEMORY INCLUDING MEANS OF CHECKING MEMORY CELL THRESHOLD VOLTAGES	11/15/2001	09/997,214	5/27/2003	6,568,510	S
NMXS-0752.01/US	Utility - DIV	Issued	FLASH MEMORY INCLUDING MEANS OF CHECKING MEMORY CELL THRESHOLD VOLTAGES	1/28/2003	10/352,581	3/30/2004	6,714,453	Su
NMXS-0753.00/US	Utility - NSPCT	Issued	CONTACT LESS IC CARD WITH OPERATING SYSTEM USED IN CONTACT TYPE CARDS AND READER FOR SUCH CONTACTLESS CARDS	2/14/2002	10/471,883	1/16/2007	7,163,154	US.
NMXS-0754.00/US	Utility - ORG	Issued	FLASH EEPROM AND EPROM ARRAYS WITH SELECT TRANSISTORS WITHIN THE BIT LINE PITCH	3/11/1994	08/212,176	9/17/1996	5,557,124	ᅜ
NMXS-0755.00/US	Utility - ORG	Issued	METHOD OF RE-PROGRAMMING AN ARRAY OF NON-VOLATILE MEMORY CELLS, IN PARTICULAR OF THE NOR ARCHITECTURE FLASH TYPE, AFTER AN ERASE OPERATION, AND A CORRESPONDING MEMORY DEVICE	6/12/2002	10/171,078	11/25/2003	6,654,287	S
NMXS-0756.00/US	Utility - ORG	Issued	MEMORY DEVICE	10/24/2001	10/041,684	5/20/2003	6,567,296	SS
NMXS-0757.00/US	Utility - ORG	Issued	WORD LINE SELECTOR FOR A SEMICONDUCTOR MEMORY	2/20/2003	10/372,626	3/8/2005	6,865,114	US
NMX5-0/58.00/US	Utility - ORG	Issued	DESIGN FAILURE MODE EFFECT ANALYSIS (DFMEA)	12/26/2002	10/330,485	4/25/2006	7,035,769	SU
NMXS-0759.00/US	Utility - ORG	Issued	POWER SUPPLY CIRCUIT STRUCTURE FOR A ROW DECODER OF A MULTILEVEL NON- VOLATILE MEMORY DEVICE	12/30/2002	10/334,126	12/7/2004	6,829,168	US
NMXS-0760.00/US	Utility - ORG	issued	BINARY ENCODING CIRCUIT	12/20/2002	10/325,707	2/24/2004	6,696,990	SS
NMXS-0761.00/US	Utility - ORG	Issued	REGULATION METHOD FOR THE DRAIN, BODY AND SOURCE TERMINALS VOLTAGES IN A NON-VOLATILE MEMORY CELL DURING A PROGRAM PHASE AND CORRESPONDING PROGRAM CIRCUIT	12/27/2002	10/331,116	10/26/2004	6,809,961	LS.

77
7
- 27
-
٠.
_
S
-
155
-
22
_
ಌ
a
**
æ
3
7
W

, ,	13 US	6,930,913	8/16/2005	10/372,639	2/20/2003	CONTACT STRUCTURE, PHASE CHANGE MEMORY CELL, AND MANUFACTURING METHOD THEREOF WITH ELIMINATION OF DOUBLE CONTACTS	Issued	Utility - CIP	NMXS-0783.00/US
<i>"</i>	Sn 99	7,372,166	5/13/2008	11/258,340	10/24/2005	OPTIMIZED HEATER SHAPE, AND MANUFACTURING METHOD THEREOF	Issued	Utility - DIV	NMXS-0782.01/US
	55	6,972,430	12/6/2005	10/371,154	2/20/2003	SUBITHOGRAPHIC CONTACT STRUCTURE, PHASE CHANGE MEMORY CELL WITH OPTIMIZED HEATER SHAPE, AND MANUFACTURING METHOD THEREOF	Issued	Utility - CIP	NMXS-0782.00/US
	57 US	7,993,957	8/9/2011	11/045,170	1/27/2005	PHASE CHANGE MEMORY CELL AND MANUFACTURING METHOD THEREOF USING MINITRENCHES	Issued	Utility - DIV	NMX5-0780.01/US
		6,891,747	5/10/2005	10/372,761	2/20/2003	PHASE CHANGE MEMORY CELL AND MANUFACTURING METHOD THEREOF USING MINITRENCHES	Issued	Utility - CIP	NMXS-0780.00/US
	Su 4	7,149,844	12/12/2006	10/390,556	3/14/2003	NON-VOLATILE MEMORY DEVICE	Issued	Utility - ORG	NMXS-0779.00/US
	us 85	6,920,066	7/19/2005	10/438,175	5/13/2003	PROGRAMMING METHOD OF THE MEMORY CELLS IN A MULTILEVEL NON-VOLATILE MEMORY DEVICE	Issued	Utility - ORG	NMXS-0778.00/US
	71 US	7,227,171	6/5/2007	10/313,991	12/5/2002	SMALL AREA CONTACT REGION, HIGH EFFICIENCY PHASE CHANGE MEMORY CELL AND FABRICATION METHOD THEREOF	Issued	Utility - ORG	NMXS-0777.00/US
	SO EI	6,586,313	7/1/2003	09/997,227	11/29/2001	METHOD FOR AVOIDING THE EFFECTS OF LACK OF UNIFORMITY IN TRENCH ISOLATED INTEGRATED CIRCUITS	Issued	Utility - ORG	NMXS-0776.00/US
	73 US	6,946,673	9/20/2005	10/345,129	1/14/2003	INTEGRATED RESISTOR, PHASE-CHANGE MEMORY ELEMENT INCLUDING THIS RESISTOR, AND PROCESS FOR THE FABRICATION THEREOF	Issued	Utility - ORG	NMXS-0775.00/US
<u>.</u>			9/13/2005	10/440,043	5/15/2003	SELF-REPAIR METHOD FOR NONVOLATILE MEMORY DEVICES WITH ERASING/PROGRAMMING FAILURE, AND RELATIVE NONVOLATILE MEMORY DEVICE	issued	Utility - ORG	NMXS-0774.00/US
	US US	7,221,602	5/22/2007	10/735,250	12/12/2003	MEMORY SYSTEM COMPRISING A SEMICONDUCTOR MEMORY	Issued	Othry - ORG	MIND-07/3,00/05
-	ŀ		11/9/2004	10/319,439	12/12/2002	ARCHITECTURE OF A PHASE-CHANGE NONVOLATILE MEMORY ARRAY	Issued	Otility - ORG	NINE 0772 00/05
<u>. </u>	US	6,981,107	12/27/2005	10/281,078	10/24/2002	FAST PROGRAMMING METHOD FOR NONVOLATILE MEMORIES, IN PARTICULAR FLASH MEMORIES, AND RELATIVE MEMORY ARCHITECTURE	Issued	Utility - ORG	NMXS-0771.00/US
	SS US	6,891,755	5/10/2005	10/340,207	1/10/2003	ARCHITECTURE FOR A FLASH-EEPROM SIMULTANEOUSLY READABLE IN OTHER SECTORS WHILE ERASING AND/OR PROGRAMMING ONE OR MORE SECTORS	ksued	Utility - ORG	NMXS-0770.00/US
	72 us	7,115,472	10/3/2006	10/964,049	10/12/2004	PROCESS FOR MANUFACTURING A DUAL CHARGE STORAGE LOCATION MEMORY CELL	Issued	Utility - DIV	NMXS-0769.01/US
	23 US	6,825,523	11/30/2004	10/267,033	10/7/2002	PROCESS FOR MANUFACTURING A DUAL CHARGE STORAGE LOCATION MEMORY CELL	Issued	Utility - ORG	NMXS-0769.00/US
*')77 US	6,754,107	6/22/2004	10/331,185	12/27/2002	SINGLE SUPPLY VOLTAGE, NONVOLATILE PHASE CHANGE MEMORY DEVICE WITH CASCODED COLUMN SELECTION AND SIMULTANEOUS WORD READ/WRITE OPERATIONS	issued	Utility - ORG	NMXS-0768.00/US
	N Z	7,284,144	10/16/2007	10/309,759	12/4/2002	FINITE STATE MACHINE INTERFACE HAS ARBITRATION STRUCTURE TO STORE COMMAND GENERATED BY INTERNAL CIRCUITS DURING EVALUATION PHASE OF STATE MACHINE FOR FLASH EEPROM DEVICE	issued	Utility - ORG	NMXS-0767.00/US
)))	Sn Or	6,958,510	10/25/2005	10/294,999	11/14/2002	PROCESS FOR FABRICATING A DUAL CHARGE STORAGE LOCATION MEMORY CELL	tssued	Utility - ORG	NMXS-0766.00/US
		6,822,906	11/23/2004	10/331,158	12/26/2002	SENSE AMPLIFIER STRUCTURE FOR MULTILEVEL NON-VOLATILE MEMORY DEVICES AND CORRESPONDING READING METHOD	Issued	Utility - ORG	NMXS-0765.00/US
	SU	6,958,949	10/25/2005	10/331,177	12/27/2002	DECODING STRUCTURE FOR A MEMORY DEVICE WITH A CONTROL CODE	Issued	Utility - ORG	NMXS-0764.00/US
		5 882 001	4/19/2005	10/372.044	2/20/2003	ELECTRICALLY-PROGRAMMABLE NON-VOLATILE MEMORY CELL	Issued	Utility - ORG	NMXS-0763.00/US
	us I	6,965,523	11/15/2005	10/964,160	10/12/2004	MULTILEVEL MEMORY DEVICE WITH MEMORY CELLS STORING NON-POWER OF TWO VOLTAGE LEVELS	issued	Utility - DIV	NMXS-0762.01/US
)7 us	6,816,407	11/9/2004	10/259,252	9/26/2002	METHOD FOR STORING AND READING DATA IN A MULTILEVEL NONVOLATILE MEMORY, AND ARCHITECTURE THEREFOR	Issued	Utility - ORG	NMXS-0762.00/US
2	60	Patentio	definition	Senaino	Seriaino Pagento Pagento Continuo	Exhibit A - US Issued Patents	Matterstatus	Matterlype	MIT DEGINO MARKETINDE

۱		
١	E.	
Ī	×	
ı	≕.	
1	•	
ı	≂	
ı	-	
ł	7	
ł	·	
ı	9	
ŧ	S	
	5	
ì	ŝ	
ı	⊊	
ı	뽔	
ı	***	
ı	7	
ı	<u>m</u>	
ı	æ	
ı	Ë	
ı	r#	
ı	٧,	

SN	7,390,755	6/24/2008	10/137,096	5/1/2002	AMERICAN LOST EICH CEEMAN			
S	6,826,083	11/30/2004	10/426,924	4/29/2003		les les	Utility - CIP	NMXS-0812.00/US
SC	7,031,189	4/18/2006	10/434,395	5/7/2003	METHOD FOR REDUCING SPURIOUS ERASING DURING PROGRAMMING OF A	keiled	Utility - ORG	SN/00T180-SXWN
S	7,184,319	2/27/2007	10/675,221	9/30/2003	MENGORY DEVICE NON-YOLATILE LATCH CIRCUIT	Issued	Utility - ORG	NMXS-0810.00/US
US	6,760,265	7/6/2004	10/299,965	11/19/2002	METHOD FOR ERASING NON-YOLATHE MEMORY CELLS AND CORRESPONDED TO	issued	Utility - ORG	NWXS-D8D8 D0/US
S	6,934,192	8/23/2005	10/178,796	6/24/2002	READ AASISTOR WITH A LOW CURRENT COMMITTEE FROM A BREAKDOWN OF AN	issued	Utility - ORG	NMXS-0807.00/US
S	6,738,286	5/18/2004	10/277,183	10/21/2002	BITS OF A FIRST AND SECOND TYPE	Issued	Utility - ORG	Sn/00'9080-SXWN
S	6,621,737	9/16/2003	10/096,531	3/11/2002	CIRCUIT AND ASSOCIATED METHOD FOR THE ERASURE OR PROGRAMMING OF A MEMORY CELL	issued	Utility - ORG	SN/00′5080-5XWN
ᅜ	6,594,177	7/15/2003	09/922,176	8/2/2001	REDUREANCY CIRCUIT AND METHOD FOR REPLACING DEFECTIVE MEMORY CELLS IN A FLASH MEMORY DEVICE	Issued	Utility - ORG	NMXS-0804.00/US
ន	6,563,732	5/13/2003	09/922,068	8/2/2001	REDUNDANCY CIRCUIT AND METHOD FOR FLASH MEMORY DEVICES	issued	ounty - Once	
5 5	6,552,935	4/22/2003	-09/922,044	8/2/2001	DUAL BANK FLASH MEMORY DEVICE AND METHOD	Issued	Utility - ORG	NMX5-0803-07/13 20/00-2080-20/03
ā 5	6 Agn 107	12/3/2005	09/922 043	8/2/2001	SECTOR PROTECTION CIRCUIT AND METHOD FOR FLASH MEMORY DEVICES	issued	Utility - ORG	NMXS-0801.00/US
5	7000,000	2005 (c.t.) 3	10/702 443	7/77/7004	BUILT-IN TESTING METHODOLOGY IN FLASH MEMORY	Issued	Utility - ORG	NMXS-0800.00/US
ā	7 355 908	4/8/2008	10/639.240	8/11/2003	NONVOLATILE STORAGE DEVICE AND SELF-REDUNDANCY METHOD FOR THE SAME	issued	Utility - ORG	NMXS-0799.00/US
ક્ક	6,996,697	2/7/2006	10/371,221	2/21/2003	METHOD OF WRITING A GROUP OF DATA BYTES IN A MEMORY AND MEMORY DEVICE	Issued	Utility - ORG	NMXS-0798-00/US
æ	7,050,322	5/23/2006	10/360,840	2/7/2003	DEVICE INTEGRATING A NONVOLATILE MEMORY ARRAY AND A VOLATILE MEMORY ARRAY	Issued	Utility - ORG	NMXS-0797.00/US
S	6,990,596	1/24/2006	10/325,486	12/19/2002	MEMORY DEVICE OUTPUTTING READ DATA IN A TIME STARTING FROM A RISING EDGE OF AN EXTERNAL CLOCK THAT IS SHORTER THAN THAT OF KNOWN DEVICES	lssued	Utility - ORG	NMXS-0796.00/US
S	7,216,212	5/8/2007	10/387,141	3/11/2003	SEMICONDUCTOR MEMORY WITH SELF-REFRESH CAPABILITY	issued	Othry - ORG	14(A)V7-0124(A)A)
S	6,892,269	5/10/2005	10/271,352	10/15/2002	NONVOLATILE MEMORY DEVICE WITH DOUBLE SERIAL/PARALLEL COMMUNICATION INTERFACE	Issued	Utility - ORG	NMXS-0793.00/US
US.	6,801,466	10/5/2004	10/331,147	12/27/2002	CIRCUIT FOR CONTROLLING A REFERENCE NODE IN A SENSE AMPLIFIER	issued	Utility - ORG	NMXS-0792.00/US
ន	6,731,550	5/4/2004	10/161,501	5/31/2002	REDUNDANCY CIRCUIT AND METHOD FOR SEMICONDUCTOR MEMORY DEVICES	Issued	Utility - ORG	NMXS-0791.00/US
ន	6,822,919	11/23/2004	10/190,917	7/8/2002	SINGLE ENDED OUTPUT SENSE AMPLIFIER CIRCUIT WITH REDUCED POWER CONSUMPTION AND NOISE	issued	Utility - ORG	NMXS-0790.00/US
US	6,998,348	2/14/2006	10/428,338	5/1/2003	METHOD FOR MANUFACTURING ELECTRONIC CIRCUITS INTEGRATED ON A SEMICONDUCTOR SUBSTRATE	Abandoned	Utility - ORG	NMXS-0789.00/US
S	6,903,995	6/7/2005	10/449,761	5/30/2003	TEST STRUCTURE FOR THE MEASUREMENT OF CONTACT TO GATE DISTANCE IN NON-VOLATILE MEMORY DEVICES AND CORRESPONDING TEST METHOD	Issued	Utility - ORG	NMXS-0788.00/US
US.	6,882,231	4/19/2005	10/406,628	4/2/2003	ADJUSTABLE FREQUENCY OSCILLATOR WITH PROGRAMMABLE CALIBRATING CIRCUIT AND RELATED SYSTEM AND METHOD	Issued	Utility - ORG	NMXS-0787.00/US
S	7,088,614	8/8/2006	10/331,161	12/26/2002	PROGRAMMING METHOD FOR A MULTILEVEL MEMORY CELL	Issued	Utility - ORG	NMXS-0786.00/US
US.	6,876,033	4/5/2005	10/606,164	6/25/2003	ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY CELL	lssued	Utility - ORG	NMXS-0785.00/US
S	7,002,399	2/21/2006	10/402,852	3/28/2003	BASIC STAGE FOR A CHARGE PUMP CIRCUIT	Issued	Utility - ORG	NMXS-0784.00/US
US	7,402,455	7/22/2008	11/156,989	6/20/2005	MANUFACTURING METHOD OF A CONTACT STRUCTURE AND PHASE CHANGE MEMORY CELL WITH ELIMINATION OF DOUBLE CONTACTS	issued	Utility - DIV	NMXS-0783.01/US
Country	SueDate ParentNo Country)ssueDate	FREDATE TO SCHOOL OF	Filebate	鑑	MatterStatus	MatterType MatterStatus	MH-DcktNo

ង	7,478,292	1/13/2009	10/741,815	12/18/2003	DEVICE WITH IMPROVED PROGRAMMING GRANULARITY	Issued	Utility - ORG	NMXS-0834.00/US
SU	7,110,300	9/19/2006	10/782,725	2/19/2004		Issued	Utility - ORG	NMXS-0833.00/US
US	6,836,442	12/28/2004	10/614,693	7/7/2003		Issued	Utility - ORG	NMXS-0832.00/US
US.	7,772,084	8/10/2010	12/006,706	1/4/2008	PROCESS FOR SELF-ALIGNED MANUFACTURE OF INTEGRATED ELECTRONIC DEVICES	Issued	Utility - DIV	NMXS-0831.01/US
US	7,468,535	12/23/2008	10/713,538	11/14/2003		Issued	Utility - ORG	NMXS-0831.00/US
SS	7,566,610	7/28/2009	11/343,593	1/30/2006	PROCESS FOR MANUFACTURING INTEGRATED RESISTIVE ELEMENTS WITH SILICIDATION PROTECTION	ssued	Utility - DIV	Sn/t0'0680-5XWN
S	7,176,553	2/13/2007	10/672,293	9/26/2003	INTEGRATED RESISTIVE ELEMENTS WITH SILICIDATION PROTECTION	lssued	Utility - ORG	NMXS-0830.00/US
ા	6,856,547	2/15/2005	10/664,606	9/16/2003	CIRCUIT FOR BIASING AN INPUT NODE OF A SENSE AMPUFIER WITH A PRE-CHARGE STAGE	lssued	Utility - ORG	NMXS-0829.00/US
US.	6,944,061	9/13/2005	10/724,022	11/26/2003	SINGLE CELL ERASING METHOD FOR RECOVERING MEMORY CELLS UNDER PROGRAMMING DISTURBS IN NON VOLATILE SEMICONDUCTOR MEMORY DEVICES	Issued	Utility - ORG	NMXS-0828.00/US
us	6,956,773	10/18/2005	10/706,306	11/12/2003	CIRCUIT FOR PROGRAMMING A NON-VOLATILE MEMORY DEVICE WITH ADAPTIVE PROGRAM LOAD CONTROL	Issued	Utility - ORG	NMXS-0827.00/US
S	7,031,193	4/18/2006	10/729,875	12/5/2003	METHOD AND DEVICE FOR PROGRAMMING AN ELECTRICALLY PROGRAMMABLE NON- VOLATILE SEMICONDUCTOR MEMORY	kssued	Utility - ORG	NMXS-0826.00/US
IJS	7,060,995	6/13/2006	10/657,801	9/8/2003	ION-IMPLANTATION MACHINE, CONTROL METHOD THEREOF, AND PROCESS FOR MANUFACTURING INTEGRATED DEVICES	Issued	Utility - ORG	NMXS-0824.00/US
ક્ર	7,456,467	11/25/2008	11/258,675	10/25/2005	PROCESS FOR MANUFACTURING A BYTE SELECTION TRANSISTOR FOR A MATRIX OF NON VOLATILE MEMORY CELLS AND CORRESPONDING STRUCTURE	Issued	Utility - DIV	NMXS-0823.01/US
SS	6,972,454	12/6/2005	10/715,887	11/18/2003	PROCESS FOR MANUFACTURING A BYTE SELECTION TRANSISTOR FOR A MATRIX OF NON VOLATILE MEMORY CELLS AND CORRESPONDING STRUCTURE	lssued	Utility - ORG	NMXS-0823.00/US
돐	6,949,803	9/27/2005	10/675,245	9/29/2003	MANUFACTURING PROCESS FOR A HIGH VOLTAGE TRANSISTOR INTEGRATED ON A SEMICONDUCTOR SUBSTRATE WITH NON-VOLATILE MEMORY CELLS AND CORRESPONDING TRANSISTOR	Issued	Utility - ORG	NMXS-0822.00/US
SS	6,930,927	8/16/2005	10/616,414	7/8/2003	LINE SELECTOR FOR A MATRIX OF MEMORY ELEMENTS	Issued	Utility - ORG	NMXS-0821.00/US
US	6,922,366	7/26/2005	10/423,845	4/24/2003	SELF-REPAIR METHOD FOR NONVOLATILE MEMORY DEVICES USING A SUPERSECURE ARCHITECTURE, AND NONVOLATILE MEMORY DEVICE	Issued	Utility - ORG	NMXS-0820.00/US
ន	6,901,011	5/31/2005	10/417,416	4/15/2003	SELF-REPAIR METHOD VIA ECC FOR NOWVOLATILE MEMORY DEVICES, AND RELATIVE NONVOLATILE MEMORY DEVICE	lssued	Utility - ORG	SO/00'6180-5XWN
US	7,563,684	7/21/2009	11/264,084	11/1/2005	PROCESS FOR MANUFACTURING AN ARRAY OF CELLS INCLUDING SELECTION BIPOLAR JUNCTION TRANSISTORS	Issued	Utility - DIV	NMXS-0818.01/US
us	6,989,580	1/24/2006	10/680,721	10/7/2003	PROCESS FOR MANUFACTURING AN ARRAY OF CELLS INCLUDING SELECTION BIPOLAR JUNCTION TRANSISTORS	Issued	Utility - ORG	Sn/00'8T80-5XWIN
US	7,446,011	11/4/2008	11/551,170	10/19/2006	ARRAY OF CELLS INCLUDING A SELECTION BIPOLAR TRANSISTOR AND FABRICATION METHOD THEREOF	Issued	VIG - VIIIO	NMXS-0817.01/US
æ	7,135,756	11/14/2006	10/680,727	10/7/2003	ARRAY OF CELLS INCLUDING A SELECTION BIPOLAR TRANSISTOR AND FABRICATION METHOD THEREOF	Issued	Utility - ORG	NMXS-0817.00/US
S	6,909,264	6/21/2005	10/608,998	6/26/2003	VOLTAGE REGULATOR WITH VERY QUICK RESPONSE	Issued	Utility - ORG	NMXS-0816.00/US
ß	7,163,898	1/16/2007	10/631,463	7/30/2003	METHOD FOR MANUFACTURING SEMICONDUCTOR INTEGRATED CIRCUIT STRUCTURES	Issued	Utility - ORG	NMXS-0815.00/US
SS	6,822,905	11/23/2004	10/331,106		IL VOLTAGE IN A NON-VOLATILE ORRESPONDING PROGRAM CIRCUIT	Issued	Utility - ORG	NMXS-0813.00/US
Country	FileDate SerialNo SerialNo PatentNo Country	IssueDate	SeralNo	FileDate	MILDORING Natiety me Naties aris Salar MatterStatus	Matter ype	MTI Dektino	

ŀ	8
ı	7
ŧ	
ı	Р
ŀ	•
	_
	S
	-
ı	ĸ
١	Ġ
	o
	Q,
	**
	ขั
	ヹ
	122
	크
	u

	સ	7,023,047	4/4/2006	10/745,295	12/23/2003	MOS DEVICE AND PROCESS FOR MANUFACTURING MOS DEVICES USING DUAL- POLYSILICON LAYER TECHNOLOGY	Issued	Utility - ORG	Sn/00'6980-5ximin
	ષ્ટ	7,214,596	5/8/2007	10/909,749	8/2/2004	METHOD FOR THE FABRICATION OF ISOLATION STRUCTURES	Issued	Utility - ORG	NMXS-0866.00/US
1	S	7,075,844	7/11/2006	10/762,195	1/20/2004	PARALLEL SENSE AMPLIFIER WITH MIRRORING OF THE CURRENT TO BE MEASURED INTO EACH REFERENCE BRANCH	issued	Utility - ORG	NMXS-0865.00/US
	SS	7,288,008	10/30/2007	11/089,942	3/25/2005	NONLITHOGRAPHIC METHOD OF DEFINING GEOMETRIES FOR PLASMA AND/OR ION IMPLANTATION TREATMENTS ON A SEMICONDUCTOR WAFER	Issued	Utility - ORG	NMXS-0864.00/US
1	S	6,897,710	5/24/2005	10/748,697	12/30/2003	VOLTAGE SUPPLY DISTRIBUTION ARCHITECTURE FOR A PLURALITY OF MEMORY MODULES	Issued	Utility - ORG	NMXS-0863.00/US
	US	7,885,116	2/8/2011	12/368,271	2/9/2009	SENSE AMPLIFIER FOR LOW-SUPPLY-VOLTAGE NONVOLATILE MEMORY CELLS	Issued	Utility - CON	NMXS-0862.01/US
	S	7,508,716	3/24/2009	10/777,457	2/12/2004	SENSE AMPLIFIER FOR LOW-SUPPLY-VOLTAGE NONVOLATILE MEMORY CELLS	Issued	Utility - ORG	NMXS-0862.00/US
	æ	6,953,609	10/11/2005	10/686,556	10/14/2003	HIGH-DENSITY PLASMA PROCESS FOR DEPOSITING A LAYER OF SILICON NITRIDE	Issued	Utility - ORG	NMXS-0861.00/US
	æ	7,068,540	6/27/2006	10/729,829	12/5/2003	METHOD AND DEVICE FOR PROGRAMMING AN ELECTRICALLY PROGRAMMABLE NON- VOLATILE SEMICONDUCTOR MEMORY	Issued	Utility - ORG	NMXS-0860.00/US
1	æ	7,006,025	2/28/2006	10/861,340	6/4/2004	METHOD FOR GENERATING A REFERENCE CURRENT FOR SENSE AMPLIFIERS AND CORRESPONDING GENERATOR	Issued	Utility - ORG	NMXS-0859.00/US
	SO	7,023,738	4/4/2006	10/835,538	4/29/2004	FULL-SWING WORDLINE DRIVING CIRCUIT	Issued	Utility - ORG	NMXS-0858.00/US
1	ᅜ	7,154,803	12/26/2006	10/893,760	7/16/2004	REDUNDANCY SCHEME FOR A MEMORY INTEGRATED CIRCUIT	Issued	Utility - ORG	NMXS-0857.00/US
	SS.	7,027,317	4/11/2006	10/720,013	11/20/2003	SEMICONDUCTOR MEMORY WITH EMBEDDED DRAM	issued	Utility - ORG	NMXS-0855.00/US
I	SO	6,894,934	5/17/2005	10/728,372	12/4/2003	NON-VOLATILE MEMORY CELL SENSING CIRCUIT, PARTICULARLY FOR LOW POWER SUPPLY VOLTAGES AND HIGH CAPACITIVE LOAD VALUES	Issued	Utility - ORG	NMXS-0854.00/US
1	S	6,947,329	9/20/2005	10/675,805	9/30/2003	METHOD FOR DETECTING A RESISTIVE PATH OR A PREDETERMINED POTENTIAL IN NON-VOLATILE MEMORY ELECTRONIC DEVICES	Issued	Utility - ORG	NMXS-0853.00/US
	Sn	7,125,807	10/24/2006	10/746,878	12/23/2003	METHOD FOR MANUFACTURING NON-VOLATILE MEMORY CELLS ON A SEMICONDUCTOR SUBSTRATE	Issued	Utility - ORG	NMXS-0851.00/US
	LS	7,125,808	10/24/2006	10/749,020	12/29/2003	METHOD FOR MANUFACTURING NON-VOLATILE MEMORY CELLS ON A SEMICONDUCTIVE SUBSTRATE	Issued	Utility - ORG	NMX\$-0850.00/US
	ĸ	7,304,485	12/4/2007	10/850,834	5/21/2004	ANALYSIS OF THE QUALITY OF CONTACTS AND VIAS IN MULTI-METAL FABRICATION PROCESSES OF SEMICONDUCTOR DEVICES, METHOD AND TEST CHIP ARCHITECTURE	Issued	Utility - ORG	NMXS-0849.00/US
	SJ	7,249,231	7/24/2007	10/781,974	2/18/2004	SEMICONDUCTOR MEMORY WITH ACCESS PROTECTION SCHEME	Issued	Utility - ORG	NMXS-0845.00/US
	LS	7,031,191	4/18/2006	10/748,701	12/30/2003	STABILIZATION METHOD FOR DRAIN VOLTAGE IN NON-VOLATILE MULTI-LEVEL MEMORY CELLS AND RELATED MEMORY DEVICE	Issued	Utility - ORG	NMXS-0844.00/US
I	SS	6,934,185	8/23/2005	10/724,023	11/26/2003	PROGRAMMING METHOD FOR NON VOLATILE MULTILEVEL MEMORY CELLS AND CORRESPONDING PROGRAMMING CIRCUIT	Issued	Utility - ORG	NMXS-0843.00/US
1	SS	7,035,142	4/25/2006	10/748,696	12/30/2003	NON VOLATILE MEMORY DEVICE INCLUDING A PREDETERMINED NUMBER OF SECTORS	Issued	Utility - ORG	NMXS-0842.00/US
	ષ્ટ	6,950,337	9/27/2005	10/719,650	11/21/2003	NONVOLATILE MEMORY DEVICE WITH SIMULTANEOUS READ/WRITE	Issued	Utility - ORG	NMXS-0840.00/US
D /	Б	6,950,324	9/27/2005	10/727,150	12/3/2003	MEMORY DEVICE COMPOSED OF A PLURALITY OF MEMORY CHIPS IN A SINGLE PACKAGE	Issued	Utility - ORG	NMXS-0839.00/US
\ TE	SS	6,940,756	9/6/2005	10/739,928	12/18/2003	NON-VOLATILE MEMORY DEVICE WITH IMPROVED SEQUENTIAL PROGRAMMING SPEED	issued	Utility - ORG	NMXS-0838.00/US
╌┤ ═┡	S	6,956,787	10/18/2005	10/700,322	11/3/2003	METHOD AND DEVICE FOR TIMING RANDOM READING OF A MEMORY DEVICE	Issued	Utility - ORG	NMXS-0837.00/US
	US	7,023,728	4/4/2006	10/746,555	12/24/2003	SEMICONDUCTOR MEMORY SYSTEM INCLUDING SELECTION TRANSISTORS	lssued	Utility - ORG	Sn/00'9880-5XWN
•	ß	6,967,876	11/22/2005	10/651,019	8/28/2003	METHOD FOR CONTROLLING PROGRAMMING VOLTAGE LEVELS OF NON-VOLATILE MEMORY CELLS, THE METHOD TRACKING THE CELL FEATURES, AND CORRESPONDING VOLTAGE REGULATOR	issued	Utility - ORG	NMXS-0835.00/US
	SS	7,730,383	6/1/2010		10/14/2008	STRUCTURE AND METHOD FOR DETECTING ERRORS IN A MULTILEVEL MEMORY DEVICE WITH IMPROVED PROGRAMIMING GRANULARITY	Issued	Utility - DIV	NMXS-0834.01/US
0.6051	Country	JisueDate Patentilo Comity	Jissuelpate	Senalvo	filebate	Exhibit A - US issued Patents	MalterStatus	MainerType	MILDOMNO

PATENT

0
ੜ
ъ
ï
Ñ
ssued
Patents

			Exhibit A - US Issued Patents	Enduate	Serring	NoneDate (1)	PatentNo	Country
Sn/00'5680-5XWN	Utility - ORG	lssued	METHOD FOR REDUCING NON-UNIFORMITY OR TOPOGRAPHY VARIATION BETWEEN AN ARRAY AND CIRCUITRY IN A PROCESS FOR MANUFACTURING SEMICONDUCTOR INTEGRATED NON-VOLATILE MEMORY DEVICES	2/16/2005	11/059,294	3/20/2007	7,192,820	US.
SN/00'9680-5XIVIN	Utility - ORG	Issued	EXPLOITING A STATISTICAL DISTRIBUTION OF THE VALUES OF AN ELECTRICAL CHARACTERISTIC IN A POPULATION OF AUXILIARY MEMORY CELLS FOR OBTAINING REFERENCE CELLS	12/23/2005	11/318,053	12/8/2009	7,630,263	<u> </u>
NMXS-0897.00/US	Utility - ORG	fssued	SENSE AMPUFIER WITH EQUALIZER AMETALON FOR BETHEVING DEFECTS AFTER A METAL FICHING IN SEMICONDIVITOR	8/6/2004	10/913,788	11/14/2006	7,136,305	
NMXS-0898.00/US	Utility - ORG	Issued	METHOD FOR REDUCING DEFECTS AFTER A METAL ETCHING IN SEMICONDUCTOR DEVICES	12/10/2004	11/009,687	10/30/2007	7,288,427	S V T
Sn/00'6680-5XWN	Utility - ORG	Issued	METHOD FOR PERFORMING ERROR CORRECTIONS OF DIGITAL INFORMATION CODIFIED AS A SYMBOL SEQUENCE	3/19/2004	10/805,168	2/5/2008	7,328,397	US
NMXS-0900.00/US	Utility - ORG	issued	INTEGRATED MEMORY SYSTEM	3/19/2004	10/805,182	6/1/2010	7,730,357	US
NMXS-0901.00/US	Utility - ORG	Issued	PHASE CHANGE MEMORY DEVICE WITH BIASING OF DESELECTED BIT LINES	8/25/2004	10/926,784	8/15/2006	7,092,277	US.
NMX5-0902.00/US	Utility - ORG	issued	MANUFACTURING METHOD FOR NON-ACTIVE ELECTRICALLY STRUCTURES IN ORDER TO OPTIMIZE THE DEFINITION OF ACTIVE ELECTRICALLY STRUCTURES IN AN ELECTRONIC CIRCUIT INTEGRATED ON A SEMICONDUCTOR SUBSTRATE AND	8/3/2004	10/911,220	2/21/2006	7,001,800	ß
NMXS-0902.01/US	Utility - DIV	ssued	MANUFACTURING METHOD FOR NON-ACTIVE ELECTRICALLY STRUCTURES IN ORDER TO OPTIMIZE THE DEFINITION OF ACTIVE ELECTRICALLY STRUCTURES IN AN ELECTRONIC CIRCUIT INTEGRATED ON A SEMICONDUCTOR SUBSTRATE AND CORRESPONDING CIRCUIT	1/19/2006	11/334,988	1/22/2008	7,320,904	US
NMXS-0903.00/US	Utility - ORG	Issued	SEALING METHOD FOR ELECTRONIC DEVICES FORMED ON A COMMON SEMICONDUCTOR SUBSTRATE AND CORRESPONDING CIRCUIT STRUCTURE	10/22/2004	10/971,774	7/18/2006	7,078,294	ß
NMXS-0904.00/US	Utility - ORG	Issued	SENSING CIRCUIT FOR A SEMICONDUCTOR MEMORY	8/6/2004	10/913,128	9/18/2007	7,272,059	ક્ર
Sn/00'5060-5XWN	Utility - ORG	Issued	BIT LINE DISCHARGE CONTROL METHOD AND CIRCUIT FOR A SEMICONDUCTOR MEMORY	10/22/2004	10/971,776	8/14/2007	7,257,039	S.
NMXS-0906.00/US	Utility - ORG	Issued	SENSING CIRCUIT FOR A SEMICONDUCTOR MEMORY	8/1/2005	11/194,739	2/27/2007	7,184,348	SU
NMXS-0908.00/US	Utility - ORG	Issued	METHOD FOR MANUFACTURING NON-VOLATILE MEMORY DEVICES INTEGRATED IN A SEMICONDUCTOR SUBSTRATE	12/27/2005	11/319,798	9/2/2008	7,419,876	SO
NMXS-0910.00/US	Utility - ORG	panssi	DISTRIBUTION OF AN ELECTRIC QUANTITY THROUGH A CIRCUIT	7/20/2005	11/185,905	4/21/2009	7,521,989	US
NMXS-0912.00/US	Utility ~ ORG	issued	PAGE BUFFER CIRCUIT AND METHOD FOR A PROGRAMMABLE MEMORY DEVICE	6/24/2005	11/166,354	7/28/2009	7,567,456	SU
NMXS-0913.00/US	Utility - ORG	lssued	SEMICONDUCTOR MEMORY DEVICE WITH INFORMATION LOSS SELF-DETECT CAPABILITY	5/1/2006	11/415,879	8/19/2008	7,414,902	ક્ર
NN8XS-0914.00/US	Utility - ORG	Issued	NONVOLATILE PHASE CHANGE MEMORY DEVICE AND BIASING METHOD THEREFOR	8/2/2005	11/195,359	9/11/2007	7,269,080	S
NMXS-0916.00/US	Utility - ORG	Issued	PHASE CHANGE MEMORY CELL WITH JUNCTION SELECTOR AND MANUFACTURING METHOD THEREOF	12/19/2005	11/312,253	10/14/2008	7,436,692	US.
NMXS-0917.00/US	Utility - ORG	Issued	READ/VERIFY CIRCUIT FOR MULTILEVEL MEMORY CELLS WITH RAMP READ VOLTAGE, AND READ/VERIFY METHOD THEREOF	7/8/2005	11/178,240	7/8/2008	7,397,702	US.
NMXS-0919.00/US	Utility - ORG	lssued	METHOD OF MAKING A FLOATING GATE NON-VOLATILE MOS SEMICONDUCTOR MEMORY DEVICE WITH IMPROVED CAPACITIVE COUPLING AND DEVICE THUS OBTAINED	12/22/2005	11/317,641	8/30/2011	8,008,701	υş
NMXS-0920.00/US	Utility - ORG	Issued	PROGRAMMABLE NAND MEMORY	7/14/2005	11/183,229	6/8/2010	7,733,697	ଧ
NMXS-0921.00/US	Utility - ORG	Issued	DATA CONTROL UNIT CAPABLE OF CORRECTING BOOT ERRORS, AND CORRESPONDING SELF-CORRECTION METHOD	6/9/2005	11/149,948	10/28/2008	7,444,543	us
NMXS-0923.00/US	Utility - ORG	Issued	TRIMMING FUNCTIONAL PARAMETERS IN INTEGRATED CIRCUITS	4/25/2005	11/113,818	5/22/2007	7,221,212	SU
NMXS-0924.00/US	Utility - ORG	Issued	METHOD FOR MANUFACTURING ELECTRONIC NON-VOLATILE MEMORY DEVICES INTEGRATED IN A SEMICONDUCTOR SUBSTRATE	12/27/2005	11/319,750	2/5/2008	7,326,615	SU

PATENT

Exhibit A - US Issued Patents

rs	7,324,379	1/29/2008	11/241,729	9/30/2005	THE NOBE ON THE HIGH-VOLTAGE SUPPLY LINE			
US	7,352,645	4/1/2008	11/250,176	10/13/2005	MEMORY DEVICE AND METHOD FOR OPERATING THE SAME WITH HIGH REJECTION OF	Issued	Utility - ORG	NMXS-0965.00/US
rs	7,317,637	1/8/2008	11/261,903	10/27/2005	MEMORY DEVICE	issued	Utility - ORG	NMXS-0964.00/US
ᅜ	7,274,594	9/25/2007	11/279,378	4/11/2006	MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR	leaned of	Utility - ORG	NWXX-0963.00/US
ß	7,295,472	11/13/2007	11/279,384	4/11/2006	NON-VOLATILE MEMORY ELECTRONIC DEVICE WITH MAND TRANSPORTED TO THE SECOND		litility - ORG	NMXS-0961.00/US
S	7,532,060	5/12/2009	11/270,308	11/9/2005	INTEGRATED ELECTRONIC NON-VOLATILE MEMORY DEVICE HAVING NAND	Issued	Utility - ORG	NMXS-0959.00/US
S	7,196,943	3/27/2007	11/249,763	10/13/2005	CHARGE-PUMP DEVICE WITH INCREASED CURRENT OUTPLIF	Issued	Utility - ORG	NMXS-0958.00/US
ß	7,675,788	3/9/2010	11/401,521	4/11/2006	MEMORY DEVICE	Issued	Utility - ORG	NMXS-0957.00/US
S	7,483,296	1/27/2009	11/233,464	9/22/2005	ELECTRONIC NON-VOLATILE MEMORY DEVICE HAVING A CNAND STRUCTURE AND	Issued	Utility - ORG	NMXS-0954.00/US
દ્ધ	7,793,033	9/7/2010	11/852,937	9/10/2007	MEMORY DEVICE WITH UNIPOLAR AND RIPOLAR RELECTIONS	Issued	Utility - ORG	NMXS-0953.00/US
ક્ર	7,290,078	10/30/2007	\$85'800/TT	+007/E/7T	SERIAL MEMORY COMPRISING MEANS FOR PROTECTING AN EXTENDED MEMORY	ssued	VIG - VIIIAN	NMXS-0952.01/US
S	7,330,381	21 12 12000	11 5000 500	12/0/2004	SERIAL MEMORY COMPRISING MEANS FOR PROTECTING AN EXTENDED MEMORY ARRAY DITRING A WRITE OPERATION	ksued	Utility - ORG	NMXS-0952.00/US
	70000	2/17/2000	11/008 586	12/9/2004	METHOD AND APPARATUS FOR A CONTINUOUS READ COMMAND IN AN EXTENDED MEMORY ARRAY	Issued	Utility - ORG	NMXS-0950.00/US
ā	7.068.538	6/27/2006	10/921,365	8/18/2004	METHOD	Issued	Utility - ORG	NMX5-0949.00/US
ន	7,050,335	5/23/2006	10/867,378	6/14/2004	CELLS IN THE ERASED STATE	issued	Cently - Onto	
5 8	7,366,012	4/29/2008	11/138,884	5/25/2005	FLASH MEMORY COMPRISING MEANS FOR CHECKING AND CHECKING MEMORY DEVICE WITH REDUCED POWER CONSUMPTION		Filth One	NWXS-D989NN
5	7.457.908	11/25/2008	10/984,372	11/8/2004	SYNCHRONOIS MEMORY DEVICE WITH MULTI-SECTOR SELECTION COMMANDS	issued	Utility - ORG	NMXS-0947.00/US
Б	7,519,751	4/14/2009	10/886,003	7/7/2004	INTEGRATED MEMORY DEVICE	Issued	Utility - ORG	NMXS-0946.00/US
SU	7,180,786	2/20/2007	11/202,632	8/11/2005	METHOD OF GENERATING AN ENABLE SIGNAL OF A STANDARD MEMORY CORE AND	issued	Utility - ORG	NMXS-0945.00/US
					ROW DECODER FOR NAND MEMORIES	Issued	Utility - ORG	NMXS-0944,00/US
S	7,603,593	10/13/2009	12/033,855	2/19/2008	METHOD FOR MANAGING BAD MEMORY BLOCKS IN A NONVOLATILE-MEMORY DEVICE, AND NONVOLATILE-MEMORY DEVICE IMPLEMENTING THE MANAGEMENT METHOD	issued	Utility - CON	NMXS-0943.01/US
ន	7,254,062	8/7/2007	11/120,766	5/3/2005	CIRCUIT FOR SELECTING/DESELECTING A BITLINE OF A NON-VOLATILE MEMORY	Issued	Utility - ORG	NMXS-0941.00/US
53	7,177,217	2/13/2007	11/121,615	5/4/2005	REFERENCE CELLS OF A MEMORY	ssued	Odiny - OKG	
5 8	7,167,394	1/23/2007	11/121,616	5/4/2005		Abdilonilen	One Carry	NINAYS-DOAD OD/I IS
5	7,368,947	10/2/2007	11/012 712	12/15/2004	L	Issued	Dalley - ORG	NMXS-0939.00/11S
SS	7,333,310	2/19/2008	11/013,123	17/15/2004	VOLTAGE TRANSLATING CONTROL STRUCTURE	Issued	Utility - ORG	SO/001/560-5XIMIN
SN	7,411,433	8/12/2008	11/012,693	12/15/2004	ESD BONDING PAD	lssued	Utility - ORG	NMXS-0936.00/US
US	7,224,600	5/29/2007	10/783,935	2/20/2004	RESET RAMP CONTROL	Issued	Utility - ORG	NMXS-0935.00/US
S	7,208,987	4/24/2007	10/999,751	11/30/2004	TAMPER MEMORY CELL	Issued	Utility - ORG	NMXS-0934.00/US
S	7,173,845	2/6/2007	10/788,581	2/27/2004	RESET INITIALIZATION	Issued	Utility - ORG	NMXS-0933.00/US
S	7,012,417	3/14/2006	10/690,332	10/21/2003	USER RAM FLASH CLEAR	Issued	Utility - ORG	NMXS-0932,00/US
7 8	7,004,354	6/12/2007	10/690,368	10/21/2003	WAGNITUDE CONTENT ADDRESSABLE MEMORY	Issued	ONO-ONG	NMXS-0931.00/US
1 K	7,616,515	6/20/2005	10/695,294	10/27/2003	REGULATOR CIRCUITRY AND METHOD	Issued	Utility - ORG	S0/00/05/62-5XMIN
; {	7 540 045	11/10/2000	11/401.523	4/11/2006	INTEGRATED ELECTRONIC DEVICE HAVING A LOW VOLTAGE ELECTRIC SUPPLY	issued	Utility - ORG	NWXS-0929 00/15
SO	7,394,694 US	7/1/2008	11/445,491	5/31/2006	PLASH MEMORY DEVICE WITH NAND ARCHITECTURE WITH REDUCED CAPACITIVE COUPLING EFFECT	Issued	Utility - ORG	NMXS-0926.00/US
	The state of the s	IssueDate	SeralNo	FileDate		WILLECTION Matterlype MarterStatus	Wattertype:	CNITYTHEALTH
					LA INDICATOR DE LA COMPANION D	Consoling Board Confeed Consol	Section - American Section 50	MILTO CAN

Page 35 of 40

Exhibit A - US Issued Patents

S	7,571,362	8/4/2009	11/557,786	11/8/2006	MEMORY DEVICE	court - Owo	
US	7,554,861	6/30/2009	11/368,363	3/3/2006	NUMBER OF REFERENCE CELLS METHOD OF MANAGING FAILS IN A NON-YOLATHE MEMORY DEVICE AND BELATIVE METHOD OF MANAGING FAILS IN A NON-YOLATHE MEMORY DEVICE AND BELATIVE METHOD OF MANAGING FAILS IN A NON-YOLATHE MEMORY DEVICE AND BELATIVE METHOD OF MANAGING FAILS IN A NON-YOLATHE MEMORY DEVICE AND BELATIVE METHOD OF MANAGING FAILS IN A NON-YOLATHE MEMORY DEVICE AND BELATIVE METHOD OF MANAGING FAILS IN A NON-YOLATHE MEMORY DEVICE AND BELATIVE METHOD OF MANAGING FAILS IN A NON-YOLATHE MEMORY DEVICE AND BELATIVE METHOD OF MANAGING FAILS IN A NON-YOLATHE MEMORY DEVICE AND BELATIVE METHOD OF MANAGING FAILS IN A NON-YOLATHE MEMORY DEVICE AND BELATIVE METHOD OF MANAGING FAILS IN A NON-YOLATHE MEMORY DEVICE AND BELATIVE METHOD OF MANAGING FAILS IN A NON-YOLATHE MEMORY DEVICE AND BELATIVE METHOD OF MANAGING FAILS IN A NON-YOLATHE MEMORY DEVICE AND BELATIVE METHOD OF MANAGING FAILS IN A NON-YOLATHE MEMORY DEVICE AND BELATIVE METHOD OF MANAGING FAILS IN A NON-YOLATHE MEMORY DEVICE AND BELATIVE METHOD OF MANAGING FAILS IN A NON-YOLATHE MEMORY DEVICE AND BELATIVE METHOD OF MANAGING FAILS IN A NON-YOLATHE MEMORY DEVICE AND BELATIVE METHOD OF MANAGING FAILS IN A NON-YOLATHE MEMORY DEVICE AND BELATIVE METHOD OF MEMORY DEVICE AND BEL	Outry - Orio	NWXS-0996.00/03
S	7,653,863	1/26/2010	11/411,010	4/25/2006		Othry - ORG	NIMAS-DOOD TO IT IS
S	7,889,586	2/1/2011	12/248,843	10/9/2008		Utility - DIV	SO/TO'ZEGO-CVIAIN
æ	7,474,577	1/6/2009	11/444,892	5/31/2006		Utility - ORG	NIMAXS-0555 CA IVIS
SS	7,359,246	4/15/2008	11/340,414	1/26/2006	ISSUED INTERVIEW TO BE DESCRIPTION OF THE BASED ON A CURRENT GENERATOR TO BE DESCRIPTION OF THE BASED ON A CIRCUIT AND METHOD FOR DESCRIPT	Utility - ORG	NMXS-0991.00/US
S	7,289,368	10/30/2007	11/334,205	1/18/2006	Issued CONTROL OF VOLTAGES DURING ERASE AND RE-PROGRAM OPERATIONS OF MEMORY CELLS	Utility - ORG	NMXS-0990.00/US
SS	7,499,345	3/3/2009	11/605,209	11/27/2006	ISSUED INON-VOLATILE MEMORY IMPLEMENTED WITH LOW-VOLTAGES TRANSISTORS AND RELATED SYSTEM AND METHOD	Utility - ORG	NMXS-0989.00/US
SS	7,847,329	12/7/2010	11/411,982	4/26/2006	Issued VERTICAL MOSFET TRANSISTOR, IN PARTICULAR OPERATING AS A SELECTOR IN NONVOLATILE MEMORY DEVICES	Utility - ORG	NMXS-0988.00/US
SS	7,649,778	1/19/2010	12/409,740	3/24/2009	METHOD FOR ACCESSING IN READING, WRITING AND PROGRAMMING TO A NAND ISSUED NON-VOLATILE MEMORY ELECTRONIC DEVICE MONOLITHICALLY INTEGRATED ON SEMICONCTOR	Utility - DIV	NMXS-0987.01/US
SS	7,529,881	5/5/2009	11/561,799	11/20/2006	METHOD FOR ACCESSING IN READING, WRITING AND PROGRAMMING TO A NAND ISSUED NON-YOLATILE MEMORY ELECTRONIC DEVICE MONOLITHICALLY INTEGRATED ON SEMICONCTOR	Utility - ORG	NMXS-0987.00/US
SS	7,593,247	9/22/2009	11/300,145	12/14/2005	ISSUED STATES AND A REDUCED CAPACITIVE COUPLING	Utility - ORG	NWXS-0986.00/US
SU	7,439,536	10/21/2008	11/398,858	4/6/2006	Issued PHASE CHANGE MEMORY CELL WITH TUBULAR HEATER AND MANUFACTURING METHOD THEREOF	Utility - ORG	NIWXS-0985.00/US
rs	7,532,061	5/12/2009	11/437,268	5/19/2006	Issued CHARGE-PUMP TYPE, VOLTAGE-800STING DEVICE WITH REDUCED RIPPLE, IN PARTICULAR FOR NON-VOLATILE FLASH MEMORIES	Utility - ORG	NMXS-0984.00/US
S	7,521,983	4/21/2009	11/437,405	5/19/2006	Issued HIGH-VOLTAGE SWITCH WITH LOW OUTPUT RIPPLE FOR NON-VOLATILE FLOATING- GATE MEMORIES	Utility - ORG	NMXS-0983.00/US
us	7,880,123	2/1/2011	11/312,231	12/19/2005	Issued DUAL RESISTANCE HEATER FOR PHASE CHANGE DEVICES AND MANUFACTURING METHOD THEREOF	Utility - ORG	NMXS-0979.00/US
US	7,471,571	12/30/2008	11/348,513	2/6/2006	Issued IMETHOD FOR PROGRAMMING A MEMORY DEVICE SUITABLE TO MINIMIZE THE LATERAL COUPLING EFFECTS BETWEEN MEMORY CELLS	Utility - ORG	NMXS-0978.00/US
SS	7,012,832	3/14/2006	10/698,747	10/31/2003	ISSUED MAGNETIC MEMORY CELL WITH PLURAL READ TRANSISTORS	Utility - ORG	NMXS-0977.00/US
55	7,110,289	9/19/2006	10/816,271	3/31/2004	Issued METHOD AND SYSTEM FOR CONTROLLING MRAM WRITE CURRENT TO REDUCE POWER CONSUMPTION	Utility - ORG	NMXS-0976.00/US
SS	7,544,620	6/9/2009	11/648,838	12/28/2006	Issued PROCESS FOR DIGGING A DEEP TRENCH IN A SEMICONDUCTOR BODY AND SEMICONDUCTOR BODY SO OBTAINED	Utility - ORG	NMXS-0975.00/US
5 8	7,706,193	4/27/2010	11/964,250	12/26/2007	Issued VOLTAGE REGULATOR FOR THE PROGRAMMING CIRCUIT OF A MEMORY CELL	Utility - DIV	NMXS-0974.01/US
5 6	7,382,793	6/17/2008	11/280,803	11/16/2005		Utility - ORG	NMXS-0974.00/US
i S	7,535,770	6007/61/5	11/244 519	1/31/2007		Utility - ORG	NMXS-0972.00/US
Sn	7,397,700	7/8/2008	11/279,381	4/11/2006	Issued MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR ISSUED FLASH MEMORY DEVICE WITH REDUCED DEANN STREETS ISSUED FLASH MEMORY DEVICE WITH REDUCED DEVICE	Utility - ORG	NMXS-0969.00/US
æ	7,525,851	4/28/2009	11/434,564	5/15/2006	Issued ROW DECODER CIRCUIT AND RELATED SYSTEM AND METHOD	Utility - ORG	NMXS-0968.00/US
SU	7,319,604	1/15/2008	11/300,053	12/14/2005	ISSUED STATES IN THE PROPERTY OF THE PROPERTY	Utility - ORG	NMXS-0966.00/US
Country	PatentNo	FileDateCountry	SeralNo	FileDate		Militootiko Matterikpe Matterstatis	WIII-DektNo

Page 36 of 40

7
≅.
*
`
_
ŧ
C
77
ų,
7
ሯ
×
-
æ
ჲ
\equiv
⊽
Ωij
**
n
=
7
и

9/6/2011					11.12	NMXS-1053.00/11S
9/6/2011	12/104.118	4/16/2008		JRG Issued	Utility - ORG	NMXS-1052.00/US
16007///#	11/787 101	4/13/2007)RG Issued	Utility - ORG	NMXS-1050.00/US
1) 20/2005		3/14/2007)RG Issued	Utility - ORG	NMXS-1048.00/US
Trockett.		3/16/2007)RG Issued	Utility - ORG	NMXS-1047.00/US
8/5/2008	11/459.831	7/25/2006)RG Issued	Utility - ORG	NWXS-1046.00/US
10/18/2011		1/30/2007	ed ELECTRONIC DEVICE CONTAINING SEMICONDUCTOR POLYMERS AND CORRESPONDING MANUFACTURING PROCESS	JRG Issued	Utility - ORG	NMXS-1044.00/US
4/7/2009		4/24/2007		JRG Jssued	Utility - ORG	MWX3-1045.00/05
3/24/2009	11/740.941	4/27/2007		IRG Issued	Utility - ORG	NMXS-1040.00/US
8/17/2010		8/24/2007)RG issued	Utility - ORG	NMXS-1038.00/US
9/7/2010		9/8/2006	L	IRG Issued	Othety - ORG	10100500105
7/28/2009	11/469,754	9/1/2006		-	Unity - ORG	CO /OO-GZOT-CVIAINS
11/25/2008		1/14/2005		+	Utility - ORG	NIMAS TOSE OUTUS
4/22/2008		1/13/2005			Utility - UKG	SO /OC / TOT-CVIAIN
2/27/2007	11/093,012	3/29/2005			Utility - ORG	NWXS-1015.00/US
12/4/2007	11/279,663	4/13/2006	METHOD AND CIRCUIT FOR SIMULTANEOUSLY PROGRAMMING MEMORY CELLS)RG Issued	Utility - ORG	NMXS-1014.00/US
5/19/2009		1/20/2006	ed CIRCUIT FUR GENERATING AN INTERNAL ENABLING SIGNAL FOR AN OUTPUT BUFFER OF A MEMORY)RG Issued	utility - ORG	NMXS-1011.00/US
9/8/2009		7/7/2006		issued issued	onliny - ORG	CO /OO:OTOT-CVIAIRE
11/11/2008		6/8/2007		+	Utility - CON	SOUTO-520M
7/10/2007		9/28/2005			Utility - ORG	NMXS-1009.00/US
12/13/2005	11/076.785	3/10/2005	ed BUILT-IN SELF TEST FOR A COUNTER SYSTEM	RG Issued	Utility - ORG	NMXS-1008.00/US
6/1/2011	11/672,857	2/8/2007	ROW SELECTOR WITH REDUCED AREA OCCUPATION FOR SEMICONDUCTOR MEMORY DEVICES)RG Issued	Utility - ORG	NMXS-1007.00/US
1/22/2008	11/381,426	5/3/2006	RAMP GENERATOR AND RELATIVE ROW DECODER FOR FLASH MEMORY DEVICE	RG Issued	Utility - ORG	NMXS-1006.00/US
1/12/2010	11/460,531	7/27/2006	ed NON-VOLATILE MEMORY DEVICE WITH MULTIPLE REFERENCES AND CORRESPONDING CONTROL METHOD	RG Issued	Utility - ORG	NMXS-1004,00/US
1/19/2010	11/713,081	2/28/2007	NON VOLATILE MEMORY DEVICE ARCHITECTURE AND CORRESPONDING PROGRAMMING METHOD	RG Issued	Utility - ORG	NMXS-1003.00/US
3/30/2010	11/732,486	4/2/2007	METHOD FOR PROGRAMMING A MEMORY DEVICE SUITABLE TO MINIMIZE FLOATING GATE COUPLING AND MEMORY DEVICE	RG Issued	Utility - ORG	SD/0072001-SXWN
3/18/2008	11/367,707	3/2/2006	MEMORY DEVICE WITH TIME-SHIFTING BASED EMULATION OF REFERENCE CELLS	RG Issued	Utility - ORG	NMXS-1001.00/US
7/14/2009	11/605,190	11/27/2006	TRANSISTOR STRUCTURE WITH HIGH INPUT IMPEDANCE AND HIGH CURRENT CAPABILITY	RG Issued	Utility - ORG	NMXS-1000.00/US
4/22/2008	11/495,886	7/28/2006	NAND FLASH MEMORY WITH ERASE VERIFY BASED ON SHORTER EVALUATION TIME	RG Issued	Utility - ORG	SN/00'6660-SXWN
7/20/2010	11/432,301	5/10/2006	EDASH MEMORY DEVICE WITH IMPROVED MANAGEMENT OF PROTECTION INFORMATION	RG Issued	utility - ORG	SU/00.8660-5XMN
12/29/2009	11/949,598 12/29/2009 7,639,	6/1/2006	METHOD FOR MULTILEVEL PROGRAMMING OF PHASE CHANGE MEMORY CELLS USING A PERCOLATION ALGORITHM	PCT Issued	Utility - NSPCT	NMXS-0997.00/US

PATENT

₩,
0
~
➣
•
C
7=
U)
Z
ë
×
Œ.
2
ъ
Ţ
p.
0
Ø.
-
7
tri.

WII Down -	Manerlype	Matterstatus	Exhibit A - US Issued Patents	Filevare	DNIKERS			
NMXS-1054.00/US		Issued	EMBEDDED ERROR-CORRECTING ERROR-CORRECTING CODE	41	11/713,376	3/15/2011		SO
NMXS-1055.00/US	Utility - ORG	Issued	FAST PROGRAMMING MEMORY DEVICE	5/19/2008	12/123,359	9/13/2011	8,018,771	S
NMXS-1056.00/US	Utility - ORG	\$55Ued	OUTPUT BUFFER	12/13/2006	11/638,321	12/9/2008	7,463,051	55
NMXS-1056.01/US	Utility - DIV	Issued	OUTPUT BUFFER	10/30/2008	12/251,101	9/28/2010	7,804,322	S
NMXS-1062.00/US	Utility - ORG	Issued	REFERENCE CELL LAYOUT WITH ENHANCED RTN IMMUNITY	4/27/2007	11/741,462	6/23/2009	7,551,465	SS
NMXS-1066.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY DEVICE	10/12/2006	11/549,067	1/27/2009	7,483,300	S
NMXS-1067.00/US	Utility - ORG	Issued	METHOD FOR PROGRAMMING OF MEMORY CELLS, IN PARTICULAR OF THE FLASH TYPE, AND CORRESPONDING PROGRAMMING ARCHITECTURE	12/8/2006	11/636,382	10/20/2009	7,506,078	LS
NIVXS-1067.01/US	Utility - DIV	Issued	METHOD FOR PROGRAMMING OF MEMORY CELLS, IN PARTICULAR OF THE FLASH TYPE, AND CORRESPONDING PROGRAMMING ARCHITECTURE	9/20/2009	12/556,970	5/17/2011	7,944,751	ß
NMXS-1068.00/US	Utility - ORG	Issued	AUTOMATIC REGULATION METHOD FOR THE REFERENCE SOURCES IN A NON- VOLATILE MEMORY DEVICE AND CORRESPONDING MEMORY DEVICE	6/29/2007	11/771,677	7/28/2009	7,567,470	દ્ધ
NMXS-1070.00/US	Utility - ORG	Issued	METHOD FOR ACCESSING A MULTILEVEL NONVOLATILE MEMORY DEVICE OF THE FLASH NAND TYPE	7/20/2006	11/458,904	6/3/2008	7,382,660	æ
NMXS-1071.00/US	Utility - ORG	Issued	CONFIGURATION OF A MULTILEVEL FLASH MEMORY DEVICE	7/28/2006	11/460,777	5/3/2011	7,937,576	ន
NMXS-1075.00/US	Utility - ORG	Issued	ELECTRONIC DEVICE COMPRISING NON VOLATILE MEMORY CELLS WITH OPTIMIZED PROGRAMMING AND CORRESPONDING PROGRAMMING METHOD	2/28/2007	11/713,074	3/31/2009	7,512,032	r2
NMXS-1079.00/US	Utility - CIP	Issued	SEALING METHOD FOR ELECTRONIC DEVICES FORMED ON A COMMON SEMICONDUCTOR SUBSTRATE AND CORRESPONDING CIRCUIT STRUCTURE	7/17/2006	11/457,966	8/12/2008	7,410,872	ß
NMX5-1084.00/US	Utility - ORG	Issued	METHOD FOR COMPACTING THE ERASED THRESHOLD VOLTAGE DISTRIBUTION OF FLASH MEMORY DEVICES DURING WRITING OPERATIONS	8/24/2007	11/844,480	5/5/2009	7,529,136	ß
NMXS-1085.00/US	Utility - ORG	Issued	CIRCUIT AND METHOD FOR ELECTRICALLY PROGRAMMING A NON-VOLATILE	6/21/2007	11/766,493	3/3/2009	7,499,332	S
Sn/00-6801-5XWN	Utility - ORG	Issued	METHOD OF MANAGING A MULTILEVEL MEMORY DEVICE AND RELATED DEVICE	4/25/2008	12/109,525	5/4/2010	7,710,772	ß
NMXS-1090.00/US	Utility - ORG	Issued	METHOD OF MANAGING A MEMORY DEVICE EMPLOYING THREE-LEVEL CELLS	2/28/2008	12/039,268	8/24/2010	7,782,665	S
NMXS-1091.00/US	Utility - ORG	Issued	MEMORY DEVICE EMPEOYING THREE-LEVEL CELLS AND RELATED METHODS OF MANAGING	11/2/2007	11/934,144	9/29/2009	7,596,023	ន
NMXS-1093.00/US	Utility - ORG	Issued	MEMORY DEVICE WITH FAIL SEARCH AND REDUNDANCY	7/20/2007	11/780,581	1/12/2010	7,646,655	S
NMXS-1094.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY DEVICE AND METHOD OF HANDLING A DATUM READ FROM A MEMORY CELL	8/3/2007	11/833,400	5/12/2009	7,532,512	ଜ
NMXS-1095.00/US	Utility - ORG	issued	ADDRESS COUNTER FOR NONVOLATILE MEMORY DEVICE	7/27/2007	11/829,527	7/7/2009	7,558,152	US
NMXS-1104.01/US	Utility - CON	Expired	REDUCED-BEAK PLANOX PROCESS FOR THE FORMATION OF INTEGRATED ELECTRONIC COMPONENTS	11/23/1987	07/124,440	1/30/1990	4,897,365	SU
NMXS-1105.01/US	Utility - DIV	Expired	A METHOD FOR MANUSACTURING MOS/CMOS MONALITHIC INTEGRATED CIRCUITS INCLUDING SILICIDE AND POLYSILICON PATTERNING	12/15/1988	07/289,391	11/6/1990	4,968,645	S
NMXS-1106.00/US	Utility - ORG	Expired	ELECTRICALLY ALTERABLE, NONVOLATILE FLOATING GATE MEMORY DEVICE	5/27/1987	07/054,712	4/18/1989	4.823.175	3
CO /OO. JOET. CVININ	Othry - OKG	Expired	NONVOLATILE, SEMICONDUCTOR MEMORY DEVICE	6/22/1987	07/064,480	3/28/1989	4,816,883	S
NMXS-1108.00/US	Utility - ORG	Expired	GENERAL OR OF RESET PULSES UPON THE RISE OF THE POWER SUPPLY FOR CMOSTYPE INTEGRATED CIRCUITS	4/28/1988	07/187,581	12/19/1989	4,888,497	US
NMXS-1109.00/US	Utility - ORG	Expired	PROCESS FOR MANUFACTURING CMOS INTEGRATED DEVICES WITH REDUCED GATE LENGTHS	12/14/1988	07/284,272	11/6/1990	4,968,639	LS.
NMXS-1110.00/US	Utility - ORG	Expired	CIRCUIT FOR SENSING THE STATE OF MATRIX CELLS IN MOS EPROM MEMORIES INCLUDING AN OFFSET CURRENT GENERATOR	1/18/1989	07/298,487	8/14/1990	4 949 307	7
NMXS-1111.00/US	Utility - ORG	Expired	CMOS VOLTAGE MULTIPLIER	6/28/1989	07/372.493	177000	בחג ככם ג	5
NMXS-1113.00/US	Utility - ORG	Expired	CMOS LOGIC CIRCUIT FOR HIGH VOLTAGE OPERATION	6/30/1989	07/373,203	9/11/1990	4,956,569	5 2
NMXS-1114.00/US	Iltility - DBG	Expired	FABRICATION OF CMOS INTEGRATED DEVICES WITH REDUCED GATE FNGTH AND	7/18/1989	07/381,283	1/22/1991	4,987,088	SS
	omet one	cypired	LIGHTLY DOPED DRAIN	7/28/1989	07/386,189	3/5/1991	4,997,782	ន

PATENT

Exhibit A - US Issued Patents

S	5,786,272	7/28/1998	08/423,397	4/18/1995	METALLIZATION OVER TUNGSTEN PLUGS	Issued	Utility - CON	MINES-1139,01/US
5 8	5,407,861		08/068,139	5/26/1993	METALLIZATION OVER TUNGSTEN PLUGS	Issued	Utility - ORG	NNIX5-1139.00/US
5	5,355,333	1	08/135,842	10/12/1993	DYNAMIC REFERENCE SYSTEM FOR SENSE AMPLIFIER	Issued	Utility - CON	SO/TO'8517-SYMIN
55	5,663,080		08/524,080	9/6/1995	PROCESS FOR MANUFACTURING MOS-TYPE INTEGRATED CIRCUITS	Issued	Utility - CON	MMXS-1130 016 15
7	905 909 S	12/9/1997	08/475.555	6/7/1995	PROCESS FOR MANUFACTURING MOS-TYPE INTEGRATED CIRCUITS	issued	Utility - DIV	NMXS-1137.01/US
LS	6,350,676	2/26/2002	08/411,385	3/28/1995	METHOD OF FORMING HIGH-STABILITY METALLIC CONTACTS IN AN INTEGRATED CIRCUIT WITH ONE OR MORE METALLIZED LAYERS	Issued	Utility - CON	NMXS-1136.01/US
E	5,347,493	9/13/1994	07/938,731	8/31/1992	ROW DECODER FOR NAND-TYPE ROM	Issued	Utility - ORG	NMXS-1135.00/US
7	5 321 317	6/14/1994	07/936.857	8/27/1992	ZERO-CONSUMPTION POWER-ON RESET CIRCUIT	Issued	Utility - ORG	NMXS-1134.00/US
SS	5,408,148	4/18/1995	07/919,606	7/24/1992	SENSE AMPLIFIER FOR PROGRAMMABLE MEMORIES WITH A VIRTUALLY ENHANCED SOURCE OF SIGNAL	Issued	Utility - ORG	NMXS-1133.00/US
SS	5,461,713	10/24/1995	08/270,498	7/5/1994	CURRENT OFFSET SENSE AMPLIFIER OF A MODULATED CURRENT OR CURRENT UNBALANCE TYPE FOR PROGRAMMABLE MEMORIES	Issued	Utility - CIP	NMXS-1132.01/US
S	5,327,379	7/5/1994	07/878,823	5/4/1992	CURRENT OFFSET SENSE AMPLIFIER OF A MODULATED CURRENT OR CURRENT UNBALANCE TYPE FOR PROGRAMMABLE MEMORIES	Issued	Utility - ORG	NMXS-1132.00/US
S S	5,258,959	11/2/1993	07/810,480	12/19/1991	MEMORY CELL READING CIRCUIT	Expired	Utility - ORG	NMXS-1131.00/US
S.	5.283.478	2/1/1994	07/811,323	12/20/1991	FAST CAPACITIVE-LOAD DRIVING CIRCUIT PARTICULARLY MEMORIES	Expired	Utility - ORG	NMXS-1130.00/US
US.	5,270,590	12/14/1993	07/806,118	12/12/1991	SENSE CIRCUIT FOR STORAGE DEVICES SUCH A NON-VOLATILE MEMORIES, WITH ENHANCED SENSING DISCRIMINATION	Expired	Utility - ORG	NMXS-1129.00/US
8	5,276,644	1/4/1994	07/791,453	. 11/13/1991	SENSE CIRCUIT FOR STORAGE DEVICES SUCH AS NON-VOLATILE MEMORIES, WITH COMPENSATED OFFSET CURRENT	Expired	Utility - ORG	NMXS-1128.00/US
S	5,282,169	1/25/1994	07/791,973	11/13/1991	COMPENSATED SENSE CIRCUIT FOR STORAGE DEVICES	Expired	Utility - ORG	NMXS-1127.00/US
ĸ	RE36,292	7/6/1993	08/876,130	6/23/1997	OPERATIONAL ANALYSIS DEVICE OF THE SCAN PATH TYPE HAVING A SINGLE SCANNING CLOCK AND A SINGLE OUTPUT PHASE FOR AN INTEGRATED CIRCUIT	Expired	Utility - REIS	NMXS-1126.01/RE
হ্ল	5,225,724	7/6/1993	07/781,360	10/22/1991	TWO PHASES SCAN PATH WITH SINGLECLOCK.	Abandoned	Utility - ORG	NMXS-1126.00/US
US.	5,274,282	12/28/1993	07/970,609	10/30/1992	MONOSTABILIZED DYNAMIC PROGRAMMABLE LOGIC ARRAY IN CMOS TECHNOLOGY	Expired	Utility - CON	NMXS-1125.01/US
હ	5,231,051	7/27/1993	07/769,600	10/1/1991	METHOD FOR FORMATION OF CONTACT PLUGS UTILIZING ETCHBACK	Expired	Utility - ORG	NMXS-1124.00/US
US	5,267,202	11/30/1993	07/725,987	7/5/1991	READING DEVICE FOR EPROM MEMORY CELLS WITH THE OPERATIONAL FIELD INDEPENDENT OF THE THRESHOLD JUMP OF THE WRITTEN CELLS WITH RESPECT TO THE VIRGIN CELLS	Expired	Utility - ORG	NMXS-1123.00/US
S	5,179,300	1/12/1993	07/691,768	4/26/1991	DATA OUTPUT STAGE HAVING FEEDBACK LOOPS TO PRECHARGE THE OUTPUT NODE	Expired	Utility - ORG	NMXS-1122.00/US
us	5,657,484	8/12/1997	08/364,505	12/27/1994	METHOD FOR CARRYING OUT A BOOLEAN OPERATION BETWEEN ANY TWO BITS OF ANY TWO REGISTERS	Issued	Utility - CON	NMXS-1121.02/US
ß	5,486,487	1/23/1996	08/139,800	10/19/1993	METHOD FOR ADJUSTING THE THRESHOLD OF A READ-ONLY MEMORY TO ACHIEVE LOW CAPACITANCE AND HIGH BREAKDOWN VOLTAGE	Issued	Utility - CIP	NMX5-1120.01/US
US	5,218,570	6/8/1993	07/657,083	2/19/1991	L	Abandoned	Utility - ORG	NMXS-1119.00/US
S	RE36,579	6/8/1993	08/488,718	6/8/1995	SENSE CIRCUIT FOR READING DATA STORED IN NONVOLATILE MEMORY CELLS	Expired	Utility - REIS	NMXS-1119.00/RE
SS	5,097,226	3/17/1992	07/655,049	2/14/1991	VOLTAGE-BOOSTED PHASE OSCILLATOR FOR DRIVING A VOLTAGE MULTIPLIER	Expired	Utility - ORG	SD/00'8111-5XWN
S.	5,075,246	12/24/1991	07/625,764	12/13/1990	METHOD OF MANUFACTURING INTEGRATED CIRCUITS HAVING ELECTRONIC COMPONENTS OF TWO DIFFERENT TYPES EACH HAVING PAIRS OF ELECTRODES OBTAINED FROM THE SAME POLYCRYSTALLINE SILICON LAYERS AND SEPARATED BY DIFFERENT DIELECTRIC MATERIALS	Expíred	Utility - ORG	NMXS-1117.00/US
ĸ	4,992,680	2/12/1991	07/456,782	12/27/1989	PROGRAMIMABLE LOGIC DEVICE HAVING A PLURALITY OF PROGRAMIMABLE LOGIC ARRAYS ARRANGED IN A MOSAIC LAYOUT TOGETHER WITH A PLURALITY OF INTERMINGLINGLY ARRANGED INTERFACING BLOCKS	Expired	Utility - ORG	NMXS-1116.00/US
SS	ã	10/8/1991	07/446,196	12/5/1989	GRIPPER FOR THE ADVANTAGEOUSLY ROBOTIZED HANDLING OF ONE OR MORE SILICON WAFERS AND/OR OF A SUPPORT FOR SUCH WAFERS	Expired	Utility - ORG	NMXS-1115.00/US
Country	322	1swebate ParemNo	SerialNo	FileDate	S. Hitte	MatterStatus	Matterlype	MITECHANO - Mattentype

•
Ξ.
-
7.
,>
•
~
-
Ś
v
S
_
=
(D
Ω.
_
~77
44
w.
•
æ
-
~
S

2,463,492				COLLEGE OF AGE O	issued	Utility - ORG	SO/OU'8CTT-CYMIN
	1/9/1996 5,48	08/075,543	10/9/1992	SUBDITY OF AN ERASABLE SUBDITY OF AN EXPENSION OF AN ERASABLE SUBDITY OF AN EXPENSION OF AN ERASABLE SUBDITY OF AN EXPENSION OF AN EXPENS	Issued	Othry - NSPCT	NIMANA TATES ON CO.
5,712,816 US	1/27/1998 5,73	08/685,782	7/24/1996	AND FLASH-EEPROM MEMORIES METHOD AND ABBABILS CORESIDENTES METHOD ABBABILS CORESIDENTES METHOD ABBABILS CORESIDENTES METHOD ABBABILS CORESIDENTES METHOD ABBABILS CORESIDENTES METHOD ABBABILS CORESIDENTES METHOD ABBABILS CORESIDENTES METHOD ABBABILS CORESIDENTES METHOD ABBABILS CORESIDENTES METHOD ABBABILS CORESIDENTES METHOD ABBABILS CORESIDENTES METHOD ABBABILS CORESIDENTES METHOD ABBABILS CORESID	issued	Utility - CON	NINX5-1155,02/85
5,604,699 US	2/18/1997 5,60	08/454,854	5/31/1995	AND FLASH-EEPROM, MEMORIES MATHOR COR BYALLIATURE THE BUT STATES MATHOR COR BYALLIATURE THE BUT STATES MATHOR COR BYALLIATURE THE BUT STATES MATHOR STATES THE BUT STATES MATHOR STATES THE BUT STATES THE BUT STATES MATHOR STATES THE BUT STATES THE BUT STATES MATHOR STATES THE BUT STAT	Issued	Utility - DIV	NIVIXS-1155.01/US
5,469,389 US	11/21/1995 5,44	08/219,204	3/29/1994	COLUMNS ASSOCIATED WITH SINGLE MATRIX SECTORS AMETICO.	Issued	Otility - ORG	NMXS-1154.00/US
5,633,822 US	5/27/1997 5,63	08/458,346	6/2/1995	USING SOURCE LINE SWITCHING TRANSISTORS	issued	Utility - DIV	NMXS-1153.01/US
5,587,946 US	12/24/1996 5,58	08/212,907	3/15/1994	EEPROM MEMORY ARRAY USING SOURCE LINE SWITCHING TRANSISTORS	Issued	Utility - ORG	NMXS-1153.00/US
5,508,956 US	4/16/1996 5,50	08/214,049	3/15/1994	NONVOLATILE FLASH-EEPROM MEMORY ARRAY WITH SOURCE CONTROL TRANSISTORS	Issued	Utility - ORG	NMXS-1152.00/US
5,497,345 US	3/5/1996 5,49	08/196,572	2/15/1994	PROTECTION EPROM OF FLASH-EEPROM MEMORY WITH TUNNEL OXIDE PROTECTION	Issued	Utility - ORG	NMXS-1151.00/US
5,913,120 US	6/15/1999 5,9:	08/502,329	7/13/1995	PROCESS FOR FABRICATING INTEGRATED DEVICES INCLUDING NONVOLATILE INCREMORIES AND TRANSISTORS WITH TUNNEL OXIDE PROTECTION	issued	Utility - CON	NMXS-1150.01/US
5,466,622 US	11/14/1995 5,4	08/196,634	2/15/1994	PROCESS FOR FABRICATING INTEGRATED DEVICES INCLUDING NONVOLATILE MEMORIES AND TRANSISTORS WITH TUNNEL OXIDE PROTECTION	Abandoned	Utility - ORG	NMXS-1150.00/US
		08/195,369	2/10/1994	MEMORIES AND TRANSISTORS	Issued	Utility - ORG	NMX>1149.00/US
5,724,395 US	3/3/1998 5,7.	08/188,569	1/28/1994	METHOU AND APPARATUS FOR FILTERING DIGITAL SIGNALS	Issued	Ourity - ONG	1110.000 DE
5,594,677 US	1/14/1997 5,59	08/189,271	1/28/1994	METHOD AND APPARATUS FOR FILTERING HIGH RESOLUTION DIGITAL SIGNALS	Issued	Utility - ORG	NMXS-1147,00/US
5,372,956 US	12/13/1994 5,3	08/153,620	11/17/1993	METHOD FOR MAKING DIRECT CONTACTS IN HIGH DENSITY MOS/CMOS PROCESSES	Issued	Utility - ORG	NMXS-1146.00/US
5,793,675 US	8/11/1998 5,7:	08/829,935	4/1/1997	METHOD OF EVALUATING THE GATE OXIDE OF NON-VOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES	Issued	Urility - CON	NMXS-1145.02/US
		08/460,540	6/2/1995	METHOU OF EVALUATING THE GATE OXIDE OF NON-VOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES	issued	Utility - DIV	NMXS-1145.01/US
5.793.086 US		08/772,301	12/23/1996	NOR-TYPE ROM WITH LDD CELLS AND PROCESS OF FABRICATION	Issued	Othrty - CON	MINI-CY1018
T	4/18/1995 54	08/084.971	6/28/1993	METHOD OF MAKING NOR-TYPE ROM WITH LDD CELLS	Issued	Utility - ORG	NMXS-1144.00/US
		08/469,431	6/6/1995	METHOD OF FABRICATING NON-VOLATILE MEMORIES WITH OVERLAPPING LAYERS	Issued	Utility - CON	NMXS-1143.02/US
5,568,418 US		08/447,772	5/23/1995	A NON-VOLATILE MEMORY IN AN INTEGRATED CIRCUIT	Issued	OBIRY - DIV	CO/TO:CHTT-CVIAIN
		08/615,727	3/13/1996	VOLTAGE REGULATOR FOR MEMORY DEVICE	Issued	Othry - CON	SOLZHTT-CVINIAL
5 440 510		08/086,342	6/30/1993	INTEGRATED CIRCUIT ENTIRELY PROTECTED AGAINST ULTRAVIOLET RAYS	Issued	Utility - ORG	SOLOOTTATT-CYLINI
25.	007 Sebt./08/5	08/084.727	6/28/1993	LOW SWITCHING NOISE OUTPUT BUFFER	Issued	Utility - ORG	NMXS-1140.00/US

08/365,284 US 08/056,301 US	2001/20/0	THE PROPERTY OF THE PROPERTY O	Aparadoried		
08/365,284	CEET INC IN	DIRECT CURRENT SUM BANDGAP VOI TAGE COMPARATOR	> トゥッカーコウム	Utility - CON	NNIX5-0112.01/US
08/365,155	45CT /07/7*	DIRECT CURRENT SUM BANDGAP VOLTAGE COMPARATOR	Abandoned	Utility - ORG	NNXS-0112.00/US
	17/20/100/	VOLTAGE BOOSTER WITH AN ACCELERATION CIRCUIT	Abandoned	Utility - ORG	NMXS-0091.00/US
	10/10/1004	COUNT UNIT FOR NONVOLATILE MEMORIES	Abandoned	Utility - ORG	NMXS-0089.00/US
08/391,146	2/21/1995	LOAD SIGNAL GENERATING METHOD AND CIRCUIT FOR NONVOLATILE MEMORIES	Abandoned	Utility - ORG	NMXS-0088.00/US
08/347,267	11/30/1994	INTEGRATED CIRCUIT FOR THE PROGRAMMING OF A MEMORY CELL IN A NON-VOLATILE MEMORY REGISTER	Abandoned	Utility - ORG	NMXS-0081.00/US
08/235,173 US	4/28/1994	AN INTEGRATED CIRCUIT MANUFACTURE	Abandoned	Utility - ORG	NMXS-0074.00/US
08/319,799	10/7/1994	LEADFRAME FOR INTEGRATED CIRCUITS	Abandoned	DUIRY - DIV	10005.0Z/US
- 1	8/31/1992	LEADFRAME FOR INTEGRATED CIRCUITS	Abandoned	Utility - ORG	MMXS-0063.00/US
07/336,401 03	12/22/1992	MULTIPLE CLOCKED DYNAMIC SENSE AMPLIFIER	Abandoned	Utility - ORG	NWIXS-0061.00/US
	8/31/1992	INTEGRATED CIRCUIT OUTPUT DRIVER	Abandoned	Utility - ORG	NMXS-0059.00/US
08/240,091 US	5/9/1994	INPUT BUFFER CIRCUIT IMMUNE TO COMMON MODE POWER SUPPLY FLUCTUATIONS	Abandoned	Utility - CON	NMXS-0057.01/US
	11/2/1992	INPUT BUFFER CIRCUIT IMMUNE TO COMMON MODE POWER SUPPLY FLUCTUATIONS	Abandoned	Utility - ORG	NMXS-0057.00/US
- 1	3/31/1992	PARALLELIZED BORROW LOOK AHEAD SUBTRACTOR	Abandoned	Ounty - Ono	Treated Contraction
- 1	12/17/1991	TRISTATABLE DRIVER FOR INTERNAL DATA BUS LINES	Abandoned	Utility - ORG	NMXS-0042.00/03
08/307,519 US	9/16/1994	VIRTUAL GROUND READ ONLY MEMORY CIRCUIT	Abandoned	Othry - DIV	NIMPS-0040.01/03
	1/21/1992	SIGNAL LINE PULSE ENHANCING CIRCUIT FOR INTEGRATED CIRCUITS	Abandoned	Other - ORG	NIMAS-0059.00/05
07/627,823 US	12/14/1990	SEMICONDUCTOR MEMORY WITH MULTIPLEXED REDUNDANCY	Abandoned	Utility - ORG	NMX5 0030 00/US
07/834,632 US	2/12/1992	SEMICONDUCTOR MEMORY WITH POWER-ON RESET CONTROLLED LATCHED ROW LINE REPEATERS	Abandoned	Utility - DIV	NMXS-0026.01/US
07/570,148 US	8/17/1990	SEMICONDUCTOR MEMORY WITH INHIBITED TEST MODE ENTRY DURING POWER-UP	Abandoned	Utility - ORG	NMXS-0021.00/US
07/964,103 US	10/20/1992	SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY	Abandoned	Utility - CON	NMXS-0020.01/US
08/101,281 US	8/2/1993	DIFFERENCE COMPARISON BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	Abandoned	Utility - CON	NMXS-0014.02/US
	4/20/1992	DIFFERENCE COMPARISON BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	Abandoned	Utility - CON	NMXS-0014.01/US
	12/6/1994	CONTENT ADDRESSABLE MEMORY	Abandoned	Utility - CON	SO/201109-CVIAIN
1	3/15/1994	CONTENT ADDRESSABLE MEMORY	Abandoned	Utility - CON	NMX5-0011.01/US
07/531,011 US	5/31/1990	CONTENT ADDRESSABLE MEMORY	Abandoned	Utility - ORG	NMXS-0011.00/US
08/166,970 US	12/14/1993	POWER-ON-RESET CIRCUIT PROVIDING PROTECTION AGAINST POWER SUPPLY CUTS FOR INTEGRATED CIRCUIT	Abandoned	Utility - ORG	NMXS-0007.00/US
07/912,867 US	7/13/1992	METHOD FOR FIXING AN ELECTRONIC COMPONENT AND ITS CONTACTS TO A SUPPORT	Abandoned	Utility - REIS	NMXS-0002.00/RE

	SS	10/165,010	6/6/2002	NONVOLATILE FLOATING-GATE MEMORY DEVICES, AND PROCESS OF FABRICATION	Abandoned	Utility - DIV	NMXS-0256.02/US
	S	08/792,621	1/31/1997	NONVOLATILE FLOATING-GATE MEMORY DEVICES, AND PROCESS OF FABRICATION	Abandoned	Utility - ORG	NMXS-0256.00/US
	US	09/210,179	12/11/1998	ANALOG VOLTAGE-SIGNAL SELECTOR DEVICE	Abandoned	Utility - CON	NMXS-0249.01/US
	15/3	08/775 109	12/30/1996		Abandoned	Utility - ORG	NMXS-0244.00/US
	US	08/625.895	4/1/1996	READING CIRCUIT FOR MULTILEVEL NON VOLATILE MEMORY CELL DEVICES	Abandoned	Utility - ORG	NMXS-0224.00/US
	S	08/388,755	2/15/1995	CLOCK PULSE EXTENDER MODE FOR CLOCKED MEMORY DEVICES HAVING PRECHARGED DATA PATHS	Abandoned	Utility - ORG	NMXS-0212.00/US
l,	SU	08/826,269	3/26/1997	METHOD AND STRUCTURE FOR RECOVERING SMALLER DENSITY MEMORIES FROM LARGER DENSITY MEMORIES	Abandoned	Utility - CON	NMXS-0188.03/US
	SU	08/518,959	8/24/1995	METHOD AND STRUCTURE FOR RECOVERING SMALLER DENSITY MEMORIES FROM LARGER DENSITY MEMORIES	Abandoned	Utility - CON	NMXS-0188.02/US
	S	08/450,087	5/25/1995	METHOD AND STRUCTURE FOR RECOVERING SMALLER DENSITY MEMORIES FROM LARGER DENSITY MEMORIES	Abandoned	Utility - DIV	NMXS-0188.01/US
	SU	08/202,827	2/28/1994	METHOD AND STRUCTURE FOR RECOVERING SMALLER DENSITY MEMORIES FROM LARGER DENSITY MEMORIES	Abandoned	Utility - ORG	NMXS-0188.00/US
	Sn	09/123,295	7/28/1998	PROCESS FOR FORMING AN INTEGRATED CIRCUIT COMPRISING NON-VOLATILE MEMORY CELLS AND SIDE TRANSISTORS OF AT LEAST TWO DIFFERENT TYPES, AND CORRESPONDING IC	Abandoned	Utility - DIV	NMXS-0181.01/US
	SU	09/347,905	7/6/1999	PROCESS FOR FORMING AN INTEGRATED CIRCUIT COMPRISING NON VOLATILE MEMORY CELLS AND SIDE TRANSISTORS AND CORRESPONDING IC	Abandoned	Utility - DIV	NMX5-0180.02/US
	us	08/561,840	11/22/1995	TWIN-WELL MANUFACTURING PROCESS FOR AN EEPROM INTEGRATED DEVICE WITH REDUCED BODY EFFECT	Abandoned	Utility - ORG	NMXS-0175.00/US
1	SU	08/563,758	11/29/1995	MONOLITHICALLY INTEGRATED GENERATOR OF A PLURALITY OF VOLTAGE VALUES	Abandoned	Utility - ORG	NMXS-0166.00/US
	SN	09/670,723	9/27/2000	PROCESS FOR THE PRODUCTION OF A SEMICONDUCTOR DEVICE HAVING BETTER INTERFACE ADHESION BETWEEN DIELECTRIC LAYERS	Abandoned	Utility - DIV	NMXS-0161.02/US
	SU	08/419,826	4/11/1995	HIGHLY-PLANAR INTERLAYER DIELECTRIC THIN FILMS IN INTEGRATED CIRCUITS	Abandoned	Utility - ORG	NMXS-0160.00/US
<u></u> l	US	1 1	3/31/1995	PROGRAMIVABLE MEMORY ELEMENT	Abandoned	Utility - ORG	NMXS-0158.00/US
	S		7/1/1996	BIAS CIRCUIT FOR TRANSISTOR OF A STORAGE CELL	Abandoned	Utility - CON	NMXS-0144.01/US
	SS	08/393,463	2/27/1995	BIAS CIRCUIT FOR TRANSISTOR OF A STORAGE CELL	Abandoned	Utility - ORG	NMXS-0144.00/US
D A 7	SU		11/1/1993	STRUCTURE TO UTILIZE A PARTIALLY FUNCTIONAL CACHE MEMORY BY INVALIDATION OF FAULTY CACHE MEMORY LOCATIONS	Abandoned	Utility - ORG	NMXS-0129.00/US
	S	2	9/30/1993	REDUNDANT LINE DECODER MASTER ENABLE	Abandoned	Utility - ORG	NMXS-0128.00/US
	55	08/507,023	7/25/1995	VARIABLE IMPEDANCE DELAY ELEMENTS	Abandoned	Utility - CON	NMXS-0124.01/US
l.	SI		7/30/1993	VARIABLE IMPEDANCE DELAY ELEMENTS	Abandoned	Utility - ORG	NMXS-0124.00/US
	S	J	6/30/1993	CLOCK GENERATION CIRCUIT HAVING COMPENSATION FOR SEMICONDUCTOR MANUFACTURING PROCESS VARIATIONS	Abandoned	Utility - ORG	NMXS-0118.00/US
	US	80	6/30/1993	METHOD AND APPARATUS FOR PARALLEL TESTING OF MEMORY	Abandoned	Utility - ORG	NMXS-0117.00/US
200	Country	SerialNo	FileDate	TITLE	MatterStatus	MatterType	N/TEDektNo/

	SS	09/107,535	6/30/1998	DEVICES	Abandoned	Utility - ORG	NIVIA3-0353.00/OS
ш	SN	08/900,328	7/25/1997	MOS CAPACITOR WITH WIDE VOLTAGE AND FREQUENCY OPERATING RANGES DEPOSITION METHOD OF A DIFFECTRIC STRUCTURE CON DIAMABUTING AGAINST.	Abandoned	Onliny - OKG	NIMAS-0335.00/US
	SU	11/083,367	3/17/2005	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	Abandoned	Utility - CON	NMXS-0321.07/US
	Sn	10/939,960	9/13/2004	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	Abandoned	Utility - CON	NMXS-0321.06/US
	US	10/796,635	3/8/2004	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	Abandoned	utility - CON	NMXS-0321.05/US
L	S	10/645,344	8/21/2003	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	Abandoned	Utility - CON	NMXS-0321.04/US
	SO	10/385,189	3/10/2003	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	Abandoned	Utility - CON	NMXS-0321.03/US
l	Sn	10/222,940	8/16/2002	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	Abandoned	Utility - CON	NMXS-0321.02/US
	US	10/078,169	2/19/2002	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	Abandoned	Utility - CON	NMXS-0321.01/US
	Sn		9/7/2001	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	Abandoned	Utility - REIS	NMXS-0321.00/RE
1	US		1/19/1996	DEVICE AND METHOD FOR DRIVING A CONDUCTIVE PATH WITH A SIGNAL	Abandoned	Utility - ORG	NMXS-0313.00/US
	US	- 1	1/19/1996	MEMORY-ROW SELECTOR HAVING A TEST FUNCTION	Abandoned	Utility - ORG	NMXS-0310.00/US
	S	08/588,737	1/19/1996	CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL	Abandoned	Utility - ORG	NMXS-0308.00/US
	SU	08/589,139	1/19/1996	CIRCUIT AND METHOD FOR TRACKING THE START OF A WRITE TO A MEMORY CELL	Abandoned	Utility - ORG	NMXS-0307.00/US
L!	US	l I	12/3/1999	TEST MODE ACTIVATION AND DATA OVERRIDE	Abandoned	Utility - DIV	NMXS-0300.01/US
	US	08/466,107	6/6/1995	METHOD AND APPARATUS FOR TEST MODE ENTRY DURING POWER UP	Abandoned	Utility - ORG	NMXS-0295.00/US
	SU		7/31/1995	INTEGRATED MEMORY CIRCUIT WITH SEQUENCED BITLINES FOR STRESS TEST	Abandoned	Utility - ORG	NMXS-0294.00/US
CEN	S	08/399,079	3/8/1995	CONSTANT CURRENT SOURCE WITH REDUCED SENSITIVITY TO SUPPLY VOLTAGE AND PROCESS VARIATION	Abandoned	Utility - CIP	NMXS-0287.00/US
	Sn	08/775,110	12/30/1996	METHOD TO PREVENT DISTURBS DURING THE PROGRAMMING AND ERASING PHASES IN A NON-VOLATILE MEMORY DEVICE	Abandoned	Utility - ORG	NMXS-0270.00/US
	Sn	09/614,955	7/12/2000	HIGH CAPACITY CAPACITOR AND CORRESPONDING MANUFACTURINGPROCESS	Abandoned	Utility - DIV	NMXS-0257.01/US
(N)	Country	SerialNo	FileDate	inje # 200 miles #	MatterStatus	MTI-DicktNo MatterType WatterStatus	Will-Daktivo

PATENT

5	10/360,515 US	2/1/2003	S. MENICOL DEVICE			
		2 (2 (2000	MEMORY DEVICE AND METHOD FOR READING SEQUENTIALLY GROUPS OF BITS FROM	Abandoned	Utility - ORG	NMXS-0795.00/US
	11/294 763	12/6/2005	METHOD FOR MANUFACTURING ELECTRONIC CIRCUITS INTEGRATED ON A SEMICONDUCTOR SUBSTRATE	Abandoned	Utility - CON	NMXS-0789.01/US
VI	13/158,291 US	6/10/2011	MINITRENCHES MINITRENCHES	Pending	Other CON	Many -0/00.02/03
ν ₁	11/201,790 US	8/11/2005	ELEMENT INCLUDING THIS RESISTOR			NWX5-0780 07 /: 15
S	11/294,044 US	12/5/2005	PROCESS FOR MANUFACTUING INTEGRATED RESISTOR AND PHASE-CHANGE MEMORY	Abandoned	Utility - DIV	NMXS-0775.01/US
			Design failure mode effect analysis (DEMFA)	Abandoned	Utility - DIV	NMX5-0/58.01/US
7	11/564.864	11/30/2006	CONTACT LESS IC CARD WITH OPERATING SYSTEM USED IN CONTACT TYPE CARDS AND READER FOR SUCH CONTACTLESS CARDS	Abandoned	Utility - CON	NMXS-0753.01/US
S	11/476,361 US	6/27/2006	VOLATILE SEMICONDUCTOR INTEGRATED MEMORIES	Abandoned	Utility - DIV	NWXS-0/32.01/US
s	10/033,358 US	12/28/2001	MEMORY DURING READING	Abandoned	ounty - Ong	
· S	09/001,918 US	T0/31/2001	METHOD AND DEVICE FOR REDIGING AVERAGE ACCESS TAKES		1485-000	NMXS-0719.00/115
		10/31/2001	PROCESS FOR PRODUCING OPTICALLY ACTIVE TITANIUM AI KOXIDE COMBI EYES	Abandoned	Utility - ORG	NMXS-0704.00/US
S	09/737,842 US	12/14/2000	INTEGRATED MOS TRANSISTOR WITH A HIGH THRESHOLD VOLTAGE AND LOW MULTIPLICATION COEFFICIENT	Abandoned	Utility - ORG	NMXS-0634.00/US
(vi	1	1/11/2001	LOW RATE REMOVAL ETCH PROCESS IN THE MANUFACTURE OF SEMICONDUCTOR INTEGRATED DEVICES USING A DIELECTRIC FILM DEPOSITION CHAMBER	Abandoned	Utility - ORG	NMXS-0616.00/US
Š	09/731,065 US	12/6/2000	THEREOF			
<i>(</i> 7	05/619/20	1/20/2000	NONLYOLATILE MEMORY DELICE AND ASSAULTS	Abandoned	Utility - ORG	NMXS-0609.00/US
		7/20/2000	BIPOLAR TRANSISTOR PRODUCED USING PROCESSES COMPATIBLE WITH THOSE	Abandoned	Utility - ORG	NMXS-0608.00/US
S	09/627,876 US	7/28/2000	ESD PROTECTION DEVICE FOR SEMICONDUCTOR INTEGRATED CIRCUIT STRUCTURE	Abandoned	Utility - ORG	NMXS-0568.00/US
Š	09/342,318 US	6/29/1999	METHOU FOR ENHANCING SELECTIVITY BETWEEN A FILM OF A LIGHT-SENSITIVE MATERIAL AND A LAYER TO BE ETCHED IN ELECTRONIC SEMICONDUCTOR DEVICE FABRICATION PROCESSES	Abandoned	Utility - ORG	NMXS-0527.00/US
S	09/408,157 US	9/29/1999	CIRCUIT STRUCTURE FOR PROVIDING A HIERARCHICAL DECODING IN SEMICONDUCTOR MEMORY DEVICES	Abandoned	Utility - ORG	NMXS-0523.00/US
	08/962,977 US	10/31/1997	VSS SWITCHING SCHEME FOR BATTERY BACKED-UP SEMICONDUCTOR DEVICES	Abandoned	Utility - ORG	NIVIXS-0492.00/US
SU	09/862,665 U	5/21/2001	IME I HOU FOR EVALUATING AN INTEGRATED ELECTRONIC DEVICE	Apailabiled	County Cold	
		4/19/2001	METHOD FOR EVALUATING AN INTEGRATED ELECTRONIC DEVICE	Abandoned	Utility - CON	NMXS-0479.02/US
JS	09/186,504 US	11/4/1998	HIGH VOLTAGE REGULATOR AND CORRESPONDING VOLTAGE REGULATION METHOD	Abandoned	Utility - ORG	NMYS-0466.00/US
us	09/365,355 U	7/30/1999	FROCESS OF HINAL PASSIVATION OF AN INTEGRATED CIRCUIT DEVICE	Controlled	o many one	
S		4/14/1998	PROCESS OF FINAL PASSIVATION OF AN INTEGRATED CIRCUIT DEVICE	Ahandanad	Utility - DIV	NMXS-0432.01/US
SU		10/22/1998	BBOCESS OF TWA SACRUMING A FLASH EPROM-TYPE FOR MEMORY	Abandoned	Utility - ORG	NMXS-0432.00/US
Country	SenalNo	FileDate	WITH THE PROPERTY OF THE PROPE	Abandanad	Hillity - CON	NMXS-0430.01/US
			- Compile to a Applications	Watte	MatterType	MTFDcktNo

PATENT

us	11/169,497	6/29/2005	METHOD AND SYSTEM FOR CORRECTING ERRORS IN ELECTRONIC MEMORY DEVICES	Abandoned	Utility - ORG	SO/OO/2260-CVIMIN
Sn	13/219,491	8/26/2011	MEMORY DEVICE WITH IMPROVED CAPACITIVE COUPLING AND DEVICE THUS OBTAINED	Pending	Utility - CON	NMXS-0919.01/US
us	12/785,346	5/21/2010	FILM BETWEEN ADJACENT MEMORY CELLS METHOD OF MAKING A FLOATING FILM SETTING OF MAKING CONDUCTIVE	Abandoned	Utility - DIV	NMXS-0918.01/US
SU	11/592,020	11/2/2006	NONVOLATILE MEMORY HAVING CONDUCTIVE FILM BETWEEN ADJACENT MEMORY CELLS	Abandoned	Utility - ORG	NMXS-0918.00/US
US	11/173,896	6/30/2005	METHOD AND SYSTEM FOR CORRECTING LOW LATENCY ERRORS IN READ AND WRITE NON VOLATILE MEMORIES, PARTICULARLY OF THE FLASH TYPE	Abandoned	Utility - ORG	NMXS-0915.00/US
US	11/280,186	11/16/2005	PROCESS FOR DEFINING INTEGRATED CIRCUITS IN SEMICONDUCTOR ELECTRONIC DEVICES	Abandoned	Utility - ORG	NMXS-0909.00/US
us	11/317,679	12/22/2005	MEIHOD OF MAKING A FLOATING-GATE NON-VOLATILE MOS SEMICONDUCTOR MEMORY DEVICE WITH IMPROVED CAPACITIVE COUPLING	Pending	Utility - ORG	NMXS-0907.00/US
US	11/457,948	7/17/2006	SEMICONDUCTOR SUBSTRATE AND CORRESPONDING CIRCUIT STRUCTURE	Abandoned	Utility - CIP	NMXS-0903.01/US
Sn	12/001,294	12/10/2007	METHOD FOR PERFORMING ERROR CORRECTIONS OF DIGITAL INFORMATION CODIFIED AS A SYMBOL SEQUENCE	Pending	Utility - DIV	NMXS-0899.01/US
US	11/855,229	9/14/2007	DEVICES	Pending	Utility - DIV	NMXS-0898.01/US
US	11/479,369	6/29/2006	POLYSILICON LAYER TECHNOLOGY WITH SIDE CONTACT	Abandoned	Utility - DIV	NMXS-0870.01/US
US	10/574,868	10/6/2004	ELEKTONENSPEKTROSKOP MIT EMISSION, DIE DURCH EINEN MONOCHROMATISCHEN ELEKTRONENSTRAHL INDUZIERT WIRD	Abandoned	Utility - NSPCT	NIMXS-0867.00/US
US	10/749,130	12/30/2003	NON-VOLATILE MEMORY CELL COMPRISING DIELECTRICLAYERS HAVING A LOW DIELECTRIC CONSTANT AND CORRESPONDING MANUFACTURING PROCESS	Abandoned	Utility - ORG	NMXS-0852.00/US
us	12/014,883	1/16/2008	PROCESS FOR THE FORMATION OF DIELECTRIC ISOLATION STRUCTURES IN SEMICONDUCTOR DEVICES	Abandoned	Utility - DIV	NMXS-0848.01/US
SU	10/853,565	5/25/2004	PROCESS FOR THE FORMATION OF DIELECTRIC ISOLATION STRUCTURES IN SEMICONDUCTOR DEVICES	Abandoned	Utility - ORG	NMXS-0848.00/US
us	10/836,651	4/30/2004	PROCESS FOR MANUFACTURING A MEMORY DEVICE HAVING SELECTOR TRANSISTORS FOR STORAGE ELEMENTS AND MEMORY DEVICE FABRICATED THEREBY	Abandoned	Utility - ORG	NMXS-0846.00/US
SU	10/652,862	8/29/2003	METHOD AND APPARATUS FOR DETECTING A LEAK OF EXTERNAL AIR INTO A PLASMA REACTOR	Abandoned	Utility - ORG	NMXS-0841.00/US
Sn	11/449,129	6/7/2006	ION-IMPLANTATION MACHINE, CONTROL METHOD THEREOF, AND PROCESS FOR MANUFACTURING INTEGRATED DEVICES	Abandoned	Utility - DIV	NMXS-0824.01/US
US	Ğ	6/27/2003	PROCESS FOR FORMING TRENCHES WITH OBLIQUE PROFILE AND ROUNDED TOP CORNERS	Abandoned	Utility - ORG	NMXS-0814.00/US
Country	SerialNo	FileDate		ManeiStatus	MTI DodNO Mattertype MatterStatus	MTI-DelaNg

11/677,411	2/21/2007	MEMORY DEVICE AND RELATIVE CONTROL METHOD	Abandoned	Other ORG	CO/00:coot-colum
	8/4/2011	METHOD OF MANAGING FAILS IN A NON-VOLATILE MEMORY DEVICE AND RELATIVE MEMORY DEVICE	Pending	Utility - REIS	NMXS-0996.00/RE
	12/15/2005	NON VOLATILE MEMORY DEVICE SUPPORTING HIGH-PARALLELISM TEST AT WAFER LEVEL	Abandoned	Utility - ORG	NMXS-0994.00/US
	8/24/2010	VERTICAL MOSFET TRANSISTOR, IN PARTICULAR OPERATING AS A SELECTOR IN NONVOLATILE MEMORY DEVICES	Pending	Utility - CON	NMXS-0988.01/US
	12/30/2005	LOW-RIPPLE BOOSTED VOLTAGE GENERATOR	Abandoned	Utility - ORG	NMX5-0982.00/US
T	4/5/2006	PROCESS FOR PHYSICAL VAPOR DEPOSITION OF A CHALCOGENIDE MATERIAL LAYER AND CHAMBER FOR PHYSICAL VAPOR DEPOSITION OF A CHALCOGENIDE MATERIAL LAYER OF A PHASE CHANGE MEMORY DEVICE	Abandoned	Utility - ORG	NWXS-0981.00/US
	12/28/2010	METHOD THEREOF	Pending	Utility - DIV	NMXS-0979.01/US
	1/12/2006	BETWEEN THE SOURCE LINE AND THE WELL	Abandoned	Utility - ORG	MMX5-09/3.00/US
	12/28/2006	PROCESS EOB MANUEL CONTROL DEVICE	Abandoned	Other - One	11 N/C 2272 22 (V)
	8/5/2011	MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR	Pending	Utility - CON	NMXS-0962-01/US
	4/11/2006	MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR	Pending	Utility - ORG	NMXS-096Z.00/US
	8/16/2005	AND STORAGE SYSTEM INCORPORATING IT	Abandoned	Utility - ORG	NMXS-0960.00/US
Ī	1/23/2006	PHASE CHANGE MEMORY DEVICE AND MANUFACTURING PROCESS THEREOF	Abandoned	Otility - ORG	SO /OOCCEO-CYIAIN
	6/14/2005	DEVICE, AND NONVOLATILE-MEMORY BLOCKS IN A NONVOLATILE-MEMORY DEVICE IMPLEMENTING THE MANAGEMENT METHOD	Abandoned	Utility - ORG	NMXS-0943.00/US
	6/4/2004	MASS MEMORY DEVICE BASED ON A FLASH MEMORY WITH MULTIPLE BUFFERS	Abandoned	Utility - ORG	NMXS-0942.00/US
\prod	1/23/2009	SENSE AMPLIFIER FOR READING A CELL OF A NON-VOLATILE MEMORY DEVICE	Abandoned	Utility - REIS	NNIX3-0939.00/RE
T	12/18/2003	RESET CIRCUIT	Abandoned	Prov - ORG	NIMYS 0938.00/PK
Ī	12/18/2003	VOLTAGE TRANSLATING CONTROL STRUCTURE	Abandoned	Prov - ORG	NMX5-0937.00/PR
T	17/18/2003	ESD BONDING PAD	Abandoned	Prov - ORG	NMX5-0936.00/PR
T	17/18/7003	RESET RAMP CONTROL	Completed	Prov - ORG	NMXS-0935.00/PR
T	1/8/2000	TAMPER MEMORY CELL	Abandoned	Prov - ORG	NMXS-0934.00/PR
	17/18/2003	RESET INITIALIZATION	Abandoned	Prov - ORG	NMX5-0933.00/PR
	5/13/2010	PROCESS FOR MANUFACTURING A NON-VOLATILE MEMORY ELECTRONIC DEVICE INTEGRATED ON A SEMICONDUCTOR SUBSTRATE AND CORRESPONDING DEVICE	Pending	Utility - DIV	NMXS-0927.01/US
	12/29/2006	PROCESS FOR MANUFACTURING A NON-VOLATILE MEMORY ELECTRONIC DEVICE INTEGRATED ON A SEMICONDUCTOR SUBSTRATE AND CORRESPONDING DEVICE	Abandoned	Utility - ORG	NMXS-0927.00/US
灦	FileDate	Hile	MatterStatus	MatterType MatterStatus	MTF-DektNo

PATENT

	65	14/1/4/1/21	2000	The second section of Cl			
L	5	- 1	3/5/2000	Process for manufacturing integrated circuits formed on a semiconductor substrate and comprising tungston lawer.	Abandoned	Utility - ORG	NMXS-1065.00/US
	SS	11/899,275 U	9/4/2007	MANUHACI URING METHOD OF AN INTEGRATED CIRCUIT FORMED ON A SEMICONDUCTOR SUBSTRATE	Abandoned	Utility - ORG	NWXS-1061.00/US
	Sn	11/774,416 U	7/6/2007	SEMICONDUCTOR-INTEGRATED ELECTRONIC DEVICE HAVING A PLURALITY OF LEADS	Abandoned	Utility - ORG	NMXS-1060.00/US
	SU	12/070,175	2/14/2008	comprising non volatile floating gate memories and an associated circuitry and corresponding electronic device	Abandoned	Utility - ORG	MINISTED STORY
	US	13/155,347	6/7/2011	Process for manufacturing an electronic device integrated on semiconductor substants	Pending	Ounty - DIV	NING 1000 00 ha
	Sn	13/047,678	3/14/2011	READING METHOD OF A MEMORY DEVICE WITH EMBEDDED ERROR-CORRECTING CODE AND MEMORY DEVICE WITH EMBEDDED ERROR-CORRECTING CODE	Pending	Utility - CON	NMXS-1054.01/US
	SU		8/3/2011	STATE TO THE MEMORY ACCESS METHOD AND DEVICE	Ó		
	SU	- 1	2/27/2007	METHOD FOR LOCALLY SUPPRESSING A DISTURBANCE OF A REFERENCE LINE	Abandoned	Utility - CON	NMXS-1050.01/US
	SS		12/27/2006	SEMICONDUCTOR SUBSTRATE	Abandoned	Utility - ORG	NMXS-1045.00/US
	SU	11/961,266	12/20/2007	TEST CARTRIDGE WITH INTERNAL GENERATION OF THE TEST SIGNALS	Abandoned	OBIRY - ORG	11000 101100/03
	S	- 1	12/23/2009	SEMICONDUCTOR FIELD-EFFECT TRANSISTOR, MEMORY CELL AND MEMORY DEVICE	Pending	Utility - NSPCT	NIMXS-1041.00/US
	US	11/528,500 t	9/27/2006	FROCESS FOR MANUFACTURING A NON-VOLATILE MEMORY DEVICE	Charles and the	, ,	NIMEYE 1047 COLIC
	SU	11/787,220	4/12/2007	IMPLEMENTED WITH LOW VOLTAGE TRANSISTORS	Abandoned	Utility - ORG	NMXS-1039.00/US
Ш	SN		3/21/2007	COLUMN DECODING SYSTEM FOR SEMICONDUCTOR MEMORY DEVICE		Helber One	NWX-1037 OO/IS
	Sn	1	3/21/2007	ROW SELECTOR FOR A SEMICONINICTOR VERYOR CO.	Abandoned	Utility - ORG	NMXS-1036.00/US
\perp	us	11/605,193	11/27/2006	VOI TAGE SWITCHING CIRCLIUTS AND METHODS	Abandoned	Utility - ORG	NMXS-1035.00/US
	Sn	11/754,494	5/29/2007	NON-ACTIVE ELECTRICALLY STRUCTURES OF INTEGRATED ELECTRONIC CIRCUIT	Abandoned	Utility - ORG	NMXS-1032.00/US
	Sn	11/684,052	3/9/2007	METHOD FOR PROGRAMMING/ERASING A NON VOLATILE MEMORY CELL DEVICE, IN PARTICULAR FOR FLASH TYPE MEMORIES	Abandoned	Utility - ORG	NMXS-1031.00/US
	SN	11/753,368	5/24/2007	DEVICE AND OF A NON-VOLATILE ELECTRONIC DEVICE AND CORRESPONDING	Abandoned	Utility - ORG	NMXS-1025.00/US
'ΑΤ	STI	11/261,131	10/28/2005	FLASH MEMORY DEVICE WITH A LOW PIN COUNT (LPC) COMMUNICATION INTERFACE	Pending	Utility - ORG	NMXS-1020.00/US
	Sn	· 11/455,896	6/19/2006	PROCESS VARIATIONS	Abandoned	Utility - ORG	NMXS-1015.00/US
	US	11/337,085	1/19/2006	ENHANCED SECURITY MEMORY ACCESS METHOD AND ARCHITECTURE	Pending	Othery - ORG	CO/OCTOT-CAMPIN
	SN	11	1/19/2006	METHOD AND ARCHITECTURE FOR RESTRICTING ACCESS TO A MEMORY DEVICE	Abandoned	Utility - ORG	NMXS-1012-00/US
¥.	Country	SegalNo	FileDate	itle and the second second second second second second second second second second second second second second			27 LAN LAN LAN LAN LAN LAN LAN LAN LAN LAN

SN	1 1	9/22/1992	TO INPUMIE REFERENCE SYS JEM FOR SENSE AMPLIFIER	rwandondo		
SU	- 1	11/23/1992	DVKAAAIC BEEESCHILD URING MOS-1 YPE INTEGRATED CIRCUITS	Abandoned	Utility - ORG	NMXS-1138.00/US
SU	07/980,550	11/23/1992	DBOCESS FOR MAKE IS CONTROL A SANDWICH OF LUNGSTEN AND ALUMINIUM.	Ahandoned	Utility - ORG	NIMXS-1137.00/US
S		10/26/1995	PI ANARIZED CONTACT WITH A SANDWICK OF THE COLOR	Abandoned	Utility - ORG	NMXS-1136.00/US
US	08/498,830	1) 0/ 1000	ROW DECODER FOR NAND-TYPE BOM	Abandoned	Utility - DIV	NMXS-1135.01/US
5	- 1	7/6/1995	OPERATIONAL ANALYSIS DEVICE OF THE SCAN PATH TYPE HAVING A SINGLE	Abandoned	Utility - REIS	NMXS-1126.00/RE
Sn	07/767,141	9/27/1991	MONOSTABILIZED DYNAMIC PROGRAMMABLE LOGIC ARRAY IN CMOS TECHNOLOGY	Abandoned	Utility - ORG	O/OCZTT-SZIMINI
US		1/16/1997	INCLINED FOR FORMALION OF CONTACT PLUGS UTILIZING ETCHBACK	- Spanwolled	11111	NAVE 1176 OOM
S	08/507,545 L	7/26/1995	METHOD FOR FORMATION OF CONTACT PLUGS UTILIZING ETCHBACK	Abandoned	Utility - CON	NMXS-1124.01/US
SU	08/015,307	2/9/1993	ANY TWO REGISTERS ANY TWO REGISTERS	Abandoned	Utility - CON	NMXS-1121.01/US
SU	07/690,495	4/24/1991	ANY TWO REGISTERS ANY TWO REGISTERS	Abandoned	Utility - ORG	NMXS-1121.00/US
SU	07/678,557	3/29/1991	METHOD FOR ADJUSTING THE THRESHOLD OF A READ-ONLY MEMORY TO ACHIEVE LOW CAPACITANCE AND HIGH BREAKDOWN VOLTAGE	Abandoned	Utility - ORG	NMXS-1120.00/US
SU	06/940,501	12/11/1986	INCLUDING SILICIDE AND POLYSILICON PATTERNING ATTERS FOR METHOD FOR MANUFACTURING MOS/CMOS MONOLITHIC INTEGRATED CIRCUITS	Abandoned	Utility - ORG	NMXS-1105.00/US
SS	06/784,324	10/4/1985	COMPONENTS	Abandoned	Utility - ORG	NWAS-LIO4.00/OS
S	1	4/17/2008	REDITCED-REAK BLANDY BENCESS FOR THE CONTACTOR OF THE CON	0		NAVE 1104 OF THE
US	11/895,609	8/24/2007	NONLYOI ATHE MEMORY CIRCUIT SYSTEM AND ACTION	Pending	Utility - ORG	NMXS-1097.00/US
			MEMORY DEVICE	Abandoned	Utility - ORG	NMXS-1086.00/US
US S	- 1	4/13/2007	MANUFACTURING PROCESS OF AN ORGANIC MASK FOR MICROELECTRONIC	Abandoned	Utility - ORG	NMXS-1080.00/US
<u> </u>		2/22/2010	PHASE CHANGE MEMORY DEVICE	Pending	Utility - NSPCT	NMXS-10/8.00/US
	11/0// 701	11/26/2007	PLASMA DEPOSITION PROCESS WITH VARIABLE PROCESS PARAMETERS	Abandoned	Utility - ORG	NMXS-1077.00/US
Sn	11/854,713	9/13/2007	METHOD OF FIXING READ EVALUATION TIME IN A NON VOLATILE NAND TYPE MEMORY DEVICE	Abandoned	Utility - ORG	NMXS-1076.00/US
US	13/053,723	3/22/2011	PROGRAMMING AND CORRESPONDING PROGRAMMING METHOD	Pending	Utility - CON	NMXS-1075.02/US
Sn		2/19/2009	PROGRAMMING AND CORRESPONDING PROGRAMMING METHOD	Pending	Utility - CON	NMXS-1075.01/US
ા	12/551,383	8/31/2009	METHOD OF PROGRAMINING A MULTI-LEVEL MEMORY DEVICE	Pending	Utility - DIV	NMIX5-10/4.01/US
Б AT		7/28/2006	PAGE BUFFER	Abandoned	Utility - ORG	NMXS-1074.00/US
SU	11/949,517	12/3/2007	VOLTAGE REGULATOR MADE OF HIGH VOLTAGE TRANSISTORS	Abandoned	Cality - ORG	COTON TOTAL
	- 1	3/15/2011	CONFIGURATION OF A MULTILEVEL FLASH MEMORY DEVICE	Pending	Utility - CON	SO/TOT/OF
Sn	11/693,360	3/29/2007	PROTECTION INFORMATION OF A NON-VOLATILE MEMORY STORED IN AN ON BOARD VOLATILE MEMORY ARRAY AT POWER-ON	Allowed	Uniny - ORG	NIVIX-TOBS.00/US
COULTY	(CHANCA)		METHOD AND DEVICE FOR DETECTING POSSIBLE CORRUPTION OF SECTOR		F. OJ	NIMAYS. 1050 00 ft is
	Southern	FIIeDate	THE	MatterStatus	MatterType Matte(Status	Mil-BektNo

ı	_
ŀ	-37
ŧ	=.
ļ	-
ı	Ō,
ı	iibit
ı	•
ı	8
ı	w
ı	
ı	
i	S
ŀ	_
ŀ	S
ı	٠.
ı	•
ı	,,,,
ı	73
ı	
ı	8
ı	-
ı	≖.
ı	a
	n.
	=.
	tions
	J
	-3
	=
	S

	NMXS-1158.01/US Utility - CON	NMXS-1155.00/US Utility - ORG	NMXS-1153.02/US Utility - DIV	NMXS-1145.00/US Utility - ORG	NMXS-1144.01/US Utility - DIV	NMXS-1143.00/US Utility - ORG	NMXS-1142.01/US Utility - CON	NMXS-1142.00/US Utility - ORG	MH DCKING MatterType	
	Pending	Abandoned	Abandoned	Abandoned	Abandoned	Abandoned	Abandoned	Abandoned	MatterStatus	
The second secon	SUPPLY VOLTAGE DISTRIBUTION SYSTEM WITH REDUCED RESISTANCE FOR SEMICONDUCTOR DEVICES	MIGHOD FOR EVALUATING THE DIELECTRIC LAYER OF NONVOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES	METHOD OF PROGRAMMING A NONVOLATILE FLASH-EEPROM MEMORY ARRAY USING SOURCE LINE SWITCHING TRANSISTORS	METHOD OF EVALUATING THE GATE OXIDE OF NON-VOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES	NOR-TYPE ROM WITH LDD CELLS AND PROCESS OF FABRICATION	METHOD OF FABRICATING NON-VOLATILE MEMORIES WITH OVERLAPPING LAYERS	VOLTAGE REGULATOR FOR MEMORY DEVICE	VOLTAGE REGULATOR FOR MEMORY DEVICE		Exhibit B - US Applications
	9/26/2011	10/21/1993	6/2/1995	10/21/1993	1/3/1995	9/30/1993	5/23/1995	6/28/1993	FileDate	
	13/245,392 US	08/140,628	08/460,227 US	08/140,629	08/367,830 US	08/129,776	08/447,736 US	08/083,377 US	SenalNo	
	ડ	S	us P	S ATE	US EN	ਲ T	US	SU	Country	

REEL: 033282 FRAME: 0388

Page 9 of 9